TEST PRODUCT QUALIFICATION REPORT

TITLE:

LT86xx Test Site Transfer from Analog Devices Singapore to UTAC Thailand

PCN Number:

PCN

REVISION:

А

DATE:

31 Aug, 2020

CONTENTS:

Summary

Table 1 – LT86xx Test Details
Table 2 - Qualification Activities and Acceptance Criteria
Table 3 – Correlation Device Run Results
Table 4 – Product Site Transfer Correlation
Table 5 – Manufacturing Validation Lot Run
Table 6 - Untrimmed/Fresh unit verification using QA program
Table 7 - GR&R Result

PROJECT BACKGROUND:

The LT86xx family is currently undergoing production testing at the Analog Devices Singapore (ADSG). As ADSG is closing in Apr2021, it is a business strategic decision to qualify UTAC Thailand (UTL) to be test site to ensure continuity in supply.

SUMMARY:

The LT86xx step-down regulator features Silent Switcher architecture designed to minimize EMI emissions while delivering high efficiency at frequencies up to 3MHz. Assembled in a 3mm \cdot 4mm QFN, the monolithic construction with integrated power switches and inclusion of all necessary circuitry yields a solution with a minimal PCB footprint. An ultralow 2.5µA quiescent current—with the output in full regulation— enables applications requiring highest efficiency at very small load currents.

This report documents the successful completion of the product test transfer requirements for the release of LT86xx family in UTAC Thailand.

TEST AND PRODUCT INFORMATION:

Device:	LT8614 / LT8640 / LT8641
Package:	QFN (3mm x 4mm)
Leads:	18 leads

Affected products:

Generics	FGs
	LT8614IUDC#PBF
LT8614	LT8614IUDC#TRPBF
L18014	LT8614HUDC#PBF
	LT8614HUDC#TRPBF
	LT8640IUDC#PBF
178640	LT8640IUDC#TRPBF
L10040	LT8640HUDC#PBF
	LT8640HUDC#TRPBF
	LT8641IUDC#PBF
LT8641	LT8641IUDC#TRPBF
	LT8641HUDC#PBF
	LT8641HUDC#TRPBF

Tester Platform:	ETS364B
Handler:	RASCO1000

The LT86xx is planned to be tested in UTAC Thailand using exactly same test design as ADSG, details shown in the Table 1 below:

Parameters ADSG		UTL	Remarks	
Tester Platform	ETS364B	ETS364B	No change	
Handler	RASCO1000	RASCO1000	No Change	
Test Flow	FT – QAR – QAH - QAC	FT – QAR – QAH - QAC	No Change	
Contactor	18L JTI socket D#9037	18L JTI socket D#9037	No Change	
Performance Board	LT8614/LT8640 DIB	LT8614/LT8640 DIB	No change	
Test Program	LT8614_03	LT8614_03	No change	
	LT8640_01	LT8640_01		
	LT8641_00	LT8641_00		

There is no change to the form, fit and function of the product.

DESCRIPTION AND TEST RESULTS:

Below tables provide description of the qualification tests conducted and corresponding test results for LT86xx family, among which LT8614 is selected to be representative of performing detailed parametric correlation analysis and GR&R analysis. All the units have undergone electrical tests on both the sending and receiving sites on the same test platform. Any device that will not meet the electrical qualification requirements will mean failure of the qualification and require solid corrective actions and a repeat of the qualification process. Qualification activities performed, and acceptance criteria is shown on Table 2 below:

Table 2: Qualification Activities and Acceptance Criteria

Qualification Activity	Sample Quantity	Accept Criteria
Correlation device run	5 correlation device units	*100% Passing correlation devices
Parametric Correlation	Minimum of 300 known Bin1 units tested in full product test flow (ALL temperature passes) in Sending site (ADSG) and Receiving site (UTL).	*CpK≥1.67 * For tightened limits, Mean Shift Criteria and sigma-spread criteria to apply - Mean Shift Criteria (ABS (SS_mean - RS_Mean) / Limit Range) x 100 ≤ 5% - Sigma-spread criteria (RS_Sigma / SS_Sigma) ≤ 1.3
Validation Lot Run	Minimum of 2,500 fresh units in full product test flow (ALL temperature passes)	yield between receiving site vs. historical yield of sending site should be comparable
Untrimmed/Fresh unit verification using QA program	5 Fresh (Untrimmed) unit tested in QA Program.	QC program must detect untrimmed or fresh parts
GR&R	10 Bin 1 units tested on 1 board and 3 testers	R&R % =<10%

SS = Sending Site

• RS = Receiving Site

To validate full set-up functionality such as hardware, software, test paraphernalia and tester platform, 5 correlation devices of LT86xx were tested both in ADSG and UTL. Data between sites were analyzed and summarized in Table 3.

Table 3: Correlation	Device Run result
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Generic	Package	No. of correlation device	ALL correlation devices passed?
LT8614	18L QFN	5 units	YES
LT8640	18L QFN	5 units	YES
LT8641	18L QFN	5 units	YES

The LT8614 was further analyzed by testing a sample of minimum 300 known-good-units in both ADSG and UTL. This is to capture variation in tester and set-up condition thru mean shift and sigma spread analysis, to ensure the parameter measurement are still within the accepted range of variations. Data between sites were analyzed and summarized in Table 4.

Temperature	Generic	Package	Lot Number	Lot Size	Sending Site	Receiving Site	Total No. of Correlation Parameters	Result
Ambient	LT8614	18L QFN	1012692.1	310	ADSG	UTL	153	ALL PASSED
Hot	LT8614	18L QFN	1012692.1	310	ADSG	UTL	153	ALL PASSED
Cold	LT8614	18L QFN	1012692.1	310	ADSG	UTL	153	ALL PASSED

The LT86xx was qualified by running a validation lot with minimum 2,500 units in UTL and was compared to ADSG historical yield. Comparison result is summarized in Table 5.

 Table 5: Manufacturing Validation Lot Run

Generic	Package	FT lot number	Lot Size	Test Site	lot yield comparison between ADSG and UTL
LT8614	18L QFN	1061103.1	26716	UTL	
LT8640	18L QFN	1055316.1	21273	UTL	MATCHED
LT8641	18L QFN	1022523.1	11504	UTL	

To ensure QA Program does not trim untrimmed/fresh parts, samples of untrimmed or fresh parts were tested using QA Program. Results were analyzed and summarized in Table 6.

Table 6: Untrimmed/Fresh unit verification using QA program

Generic	Package	Lot Number	No. of Untrimmed/Fresh units tested on QC	QA Program detected untrimmed or fresh parts?
			program	
LT8614	18L QFN	1012692.1	5	YES
LT8640	18L QFN	Z46713.1	5	YES
LT8641	18L QFN	1019270.1	5	YES

GR&R was performed on LT8614 to confirm ATE repeatability and reproducibility performance, 10 serialized units were repeatedly tested on 1 test board and 3 test systems. GR&R result was analyzed and summarized in Table 7.

Table 7: GR&R Result

Generic	Package	Lot Number	No. of	No. of Test	No. of Testers	All parameters passed R&R %
			Units	Boards		=<10%?
LT8614	18L QFN	1012692.1	10	1	3	Yes – ALL PASSED

APPROVALS:

Technical Review Board No. <u>TRB-61507</u> - ADSG to UTL Test Transfer

ADDITIONAL INFORMATION:

Homepage: <u>https://www.analog.com/en/index.html</u>

Customer Service: <u>https://www.analog.com/en/support/technical-support.html</u>

TEST PRODUCT QUALIFICATION REPORT

TITLE:

LT8611 Test Site Transfer from Analog Devices Singapore to UTAC Thailand

PCN Number:

PCN

REVISION:

А

DATE:

04 Sep, 2020

CONTENTS:

Summary

Table 1 – LT8611 Test Details
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Table 7 - GR&R Result

PROJECT BACKGROUND:

The LT8611 is currently undergoing production testing at the Analog Devices Singapore (ADSG). As ADSG is closing in Apr2021, it is a business strategic decision to qualify UTAC Thailand (UTL) to be test site to ensure continuity in supply.

SUMMARY:

The LT8611 is a compact, high efficiency, high speed synchronous monolithic step-down switching regulator that consumes only 2.5μ A of quiescent current. Top and bottom power switches are included with all necessary circuitry to minimize the need for external components. The built-in current sense amplifier with monitor and control pins allows accurate input or output current regulation and limiting. Low ripple Burst Mode operation enables high efficiency down to very low output currents while keeping the output ripple below 10mVP-P. A SYNC pin allows synchronization to an external clock. Internal compensation with peak current mode topology allows the use of small inductors and results in fast transient response and good loop stability. The EN/UV pin has an accurate 1V threshold and can be used to program VIN undervoltage lockout or to shut down the LT8611 reducing the input supply current to 1µA. A capacitor on the TR/SS pin programs the output voltage ramp rate during start-up. The PG flag signals when VOUT is within ±9% of the programmed output voltage as well as fault conditions.

This report documents the successful completion of the product test transfer requirements for the release of LT8611 in UTAC Thailand.

TEST AND PRODUCT INFORMATION:

Device:	LT8611
Package:	QFN (3mm x 5mm)

Leads: 24 leads

Affected products:

Generics	FGs
	LT8611EUDD#TRPBF
LT8611	LT8611EUDD#PBF
L19011	LT8611IUDD#TRPBF
	LT8611IUDD#PBF

Tester Platform: ETS364B

Handler: RASCO1000

The LT8611 is planned to be tested in UTAC Thailand using exactly same test design as ADSG, details shown in the Table 1 below:

Table 1: LT8611 Test Details

Parameters	ADSG	UTL	Remarks
Tester Platform	ETS364B	ETS364B	No change
Handler	RASCO1000	RASCO1000	No Change
Test Flow	FT – QAR – QAH - QAC	FT – QAR – QAH - QAC	No Change
Contactor	24L JTI socket D#5701	18L JTI socket D#5701	No Change
Performance Board	LT8611 DIB	LT8611 DIB	No change
Test Program	LT8611_03	LT8611_03	No change

There is no change to the form, fit and function of the product.

DESCRIPTION AND TEST RESULTS:

Below tables provide description of the qualification tests conducted and corresponding test results for LT8611. All the units have undergone electrical tests on both the sending and receiving sites on the same test platform. Any device that will not meet the electrical qualification requirements will mean failure of the qualification and require solid corrective actions and a repeat of the qualification process. Qualification activities performed, and acceptance criteria is shown on Table 2 below:

Qualification Activity	Sample Quantity	Accept Criteria						
Correlation device run	5 correlation device units	*100% Passing correlation devices						
Parametric Correlation	Minimum of 300 known Bin1 units tested in full product test flow (ALL temperature passes) in Sending site (ADSG) and Receiving site (UTL).	*CpK≥1.67 * For tightened limits, Mean Shift Criteria and sigma-spread criteria to apply - Mean Shift Criteria (ABS (SS_mean - RS_Mean) / Limit Range) x 100 ≤ 5% - Sigma-spread criteria (RS_Sigma / SS_Sigma) ≤ 1.3						
Validation Lot Run	Minimum of 2,500 fresh units in full product test flow (ALL temperature passes)	yield between receiving site vs. historical yield of sending site should be comparable						
Untrimmed/Fresh unit verification using QA program	5 Fresh (Untrimmed) unit tested in QA Program.	QC program must detect untrimmed or fresh parts						
GR&R	10 Bin 1 units tested on 1 board and 3 testers	R&R % =<10%						

*SS = Sending Site * RS = Receiving Site

To validate full set-up functionality such as hardware, software, test paraphernalia and tester platform, 5 correlation devices of LT8611 were tested both in ADSG and UTL. Data between sites were analyzed and summarized in Table 3.

Table 3: Correlation Device Run result

Generic	Package	No. of correlation device	ALL correlation devices passed?
LT8611	24L QFN	5 units	YES

The LT8611 was further analyzed by testing a sample of minimum 300 known-good-units in both ADSG and UTL. This is to capture variation in tester and set-up condition thru mean shift and sigma spread analysis, to ensure the parameter measurement are still within the accepted range of variations. Data between sites were analyzed and summarized in Table 4.

Table 4: Product Site Transfer Correlation

Temperature	Generic	Package	Lot Number	Lot Size	Sending Site	Receiving Site	Total No. of Correlation Parameters	Result
Ambient	LT8611	24L QFN	1000536.1	310	ADSG	UTL	206	ALL PASSED
Hot	LT8611	24L QFN	1000536.1	310	ADSG	UTL	206	ALL PASSED
Cold	LT8611	24L QFN	1000536.1	310	ADSG	UTL	206	ALL PASSED

The LT8611 was qualified by running a validation lot with minimum 2,500 units in UTL and was compared to ADSG historical yield. Comparison result is summarized in Table 5.

Table 5: Manufacturing Validation Lot Run

Generic	Package	FT lot number	Lot Size	Test Site	lot yield comparison between ADSG and UTL
LT8611	24L QFN	5004130.1	12574	UTL	Matched

To ensure QA Program does not trim untrimmed/fresh parts, samples of untrimmed or fresh parts were tested using QA Program. Results were analyzed and summarized in Table 6.

 Table 6: Untrimmed/Fresh unit verification using QA program

Generic	Package	Lot Number	No. of Untrimmed/Fresh units tested on QC program	QA Program detected untrimmed or fresh parts?
LT8611	24L QFN	1000536.1	5	YES

GR&R was performed on UTL ETS364 ATEs using a switcher product representative LT8614 to confirm tester repeatability and reproducibility performance, 10 serialized units were repeatedly tested on 1 test board and 3 test systems. GR&R result was analyzed and summarized in Table 7.

Table 7: GR&R Result

Generic	Package	Lot Number	No. of	No. of Test	No. of Testers	All parameters passed R&R %
			Units	Boards		=<10%?
LT8614	18L QFN	1012692.1	10	1	3	Yes – ALL PASSED

APPROVALS:

Technical Review Board No. TRB-61507- ADSG to UTL Test Transfer

ADDITIONAL INFORMATION:

Homepage: <u>https://www.analog.com/en/index.html</u>

Customer Service: <u>https://www.analog.com/en/support/technical-support.html</u>

Worked on: (Name, Function)	Jason Hu																								
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	Assessment of Impact on Supply Chain regarding following aspects	Remain risks wi	ing		Evaluation leve A / B / C	Further applicable conditions	as site check)		imidity Bilas orbitas od HAST Marcal HLGT	ti azod HVG T cilng Line Cy cilng	re Sonage Life re Operating Life	a Roke A. Data Rokenton, and Operation		stats ar	2 Dielectric Brashdown	dan Amparatura Instability	n Itage Atobi	arge Model	udan	: Compatblity and defaults		ge Test	, da c	2, JEDEC.ES0001)	
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SEM-AN-01	Any change with impact on agreed upon technical contractual agreements	Р	P applicable but the change affects agreed technical contractual acreaments. Any change which is not covered in the matrix below, but risk assessment at customer is mocommended.		•		-																	-	-
SEM-AN-02	Any change with impact on processability/manufacturability at customer, which is not covered in the matrix below.	Р	P below, but risk assessment at customer is recommended.		в		-											-						-	
SEM-DS-01	DATA SHEET Drange of databast parameters/electrical specification (min.imax.hyp. values) and/or ACDC secondarition	Р	 Update of data sheet because of technical change 	e.g. recommendations for pull-up/pull-down or NC	A	,			.																
52M-DS-02	excilication	1	In the product, process or feat. No technical change of product, process or feat. New description of behavior which was not specificated before or which is different from initial specification. Please include dearly, that infonces contains this type of change!	pina, MSL. a.g. Errata	A		•		-															-	
SEM-DS-03	Specification of additional parameters	•	Description of a new not previously covered parameter. No technical change of the product. 9 (2): Definition of new parameter which was not decumented before. 99%: Not known as allegie change. City in combination with other changes.	(f): e.g. adding new tested parameter.	A		-											-						-	•
			Any device relevant changes in design / layout of elements with effect on data sheet																				T		
SEM-DE-01	Design changes in active elements. ¹)	Р	elements with effect on data sheet P ¹) Not included: Modification to adjust product parameter within specified process window and design rules.	e.g. change of ESD structure e.g. add / remove a transistor in layout	A	Please check if data sheet is affected (SEM-DS-01).		•		• • м	•	• D,J			- D D	D D	D •	•	• • •	•••	• •	- F		-	•
SEM-DE-02	Design changes in routing . *)	P	Any change of wiring between elements in chip design / layout with effect on data sheet. P 1 Not included: Modification to adjust product parameter within specified design rules.	e.g. mask changes in metal fix for corrective action (based on external 8D report)	c	A: Impact on EMC behavior cannot be evaluated / excluded on component level. A: If impact on electrical function is not excluded on component level. Please check if data sheet is affected (SEM-DS-01).	-	•		- а м								•	• • •	• •				-	•
SEM-DE-03	Die shtrik ²)	Р	P Shrink of active area.) Not included: saving street/kert/scribe line	Typical shrink of die.	A	Please check if change in process technology (SEM-PW-60) is also affected.	-	•	•	• · M		• D,J				•••	•••	•	•••	•••	•			-	•
SEM-DE-04	Provers modification		Integrated software by design or memory as defined by suppler. (#): Firmware modification or update without effect of the software modification or update with effect of functional performance at the customer (hug fig). (#): Firmware modification or update with effect of functional performance at the customer.	(i): e.g. addition of Firmware opportunities (P): e.g. bug fix with impact on functional performance	A		-											-						-	
	PROCESS - WAFER PRODUCTION	1		e.g. different water material to currently released					1			1				1							11		
SEM-PW-01	New / change of wafer substrate material	Р		e.g. different water material to currently released material (Rice change from EPI material into non- EPI material)	c		-											-	• • •		• •			-	Qualification effort acc. AEC-Q100: see diffusion/doping
SEM-PW-02	New water diameter	Р	P Change of water diameter resulting in equipment and process changes.		с	Impact on changes in SEM-FW-99 and/or SEM-EQ-91.	•	•		• E M	• •	•	EE-			•	- Е	E	E • -					-	AEC-Q100: "For broad charges that involve multiple attributes (e.g., site, material processes), refer to section AI 3 of this appendix and section 23 of Q100, which for the selection of wont-case test whiches to cover all the possible permutations.
SEM-PW-03	New final water thickness	Р	P Change in final water thickness.	e.g. charge in final chipidie thickness	с	At it method conductivity is amone (see MUSHE 1) Rush, BLAA package, standard dise, At it impact on EMC or ESD behavior cannot be evaluated / excluded on component level.	÷.	•		- Е М	• •	•	EE-			•	· E	E	е • •	• •				-	•
SEM-PW-04	Charge of electrically active doping/implantation element	Р	P Change in electrically active doping / implantation element resulting in a new technology.		A		1	•	-	м	- •	# -						•	• • •					-	•
SEM-PW-05	Charge of gate material / dielectrics	Р	P Change of gate material and / or gate delectric material.		A			•		• • M	- •	- D,J					· •	•	•••					-	•
SEM-PW-06	New / change of backaide openation (grinding / metallization)	Р	P Change of bottom layer of die (between die and leadframe). Change in process, material, or dimensions necessary. Atternative area SEAN-PW-09	e.g. change from Cr/NV/Au to Cr/NIV/Ag	с	A: If thermal conductivity is affected (like MOSFET; KDRT, BGA package, stacked dies,) A: If impact on EMC or ESD behavior cannot be evaluated / excluded on component level.				м							- м	м	• • •			н	- н -	-	AEQ-Q100: Applicable to all smart power devices
SEM-PW-07	New / change of metallization / vias / contacts	Р	Paternarve sale Scho-PV-39 Change in metalization of bondpads, material, layer hickness specifically for chip frontaide and internal layers.	e. g. change from ASICu to AICu e. g. change in over pad metallization	с		•		•	• • M			• • •				•							-	•
SEM-PW-08	New / charge of passivation or dis coating (without bare dis)	Р		e. g. addition of polyimide	с	A: Emergen at a consultativity is attended (see MUGPET: AuD.), BUK package, stacked dies,) A: Empact on EMC or ESD behavior cannot be evaluated /	-		•	••м	- • •	,N D,J	• • •			•••	•••	•	•••					-	•
SEM-PW-09	Change in process technology not covered by any other type of change	-	P (-): If the change in process technology does not influence the integrity of the final product. (P): If the change in process technology can influence the integrity of the final product.		A	Please also check changes described under EQUIPMENT. Please check if change is described by specific type of change is this matrix.	•		-									-						-	Qualification effort depends on type of change.
SEM-PW-10	Process integrity: turing within specification	-	Variation within process specification (-)-: It turing within process specification does not influence the integrity of the first product. (P): If semaining rak on product specification is anticipated.	(): «.g. pracess control	с	Please check if DATA SMEET is affected. Please check if SEM-PW-03 is affected.												-							
SEM-PW-11	Charge et water napples.	-	(-): If no remaining risk in supply chain exist P (P): If the change of water supplier can influence the integrity of the final product.		с	Not on component, tested on test sincuture (hypical for IC), interaction on component level for discrete components in case of SOI substates HP properties have to be qualified. Please check if SEM-PW-01 and SEM-DS-01 is affected.													· @• ·					-	Qualification for C2 sp-Controller difficult on product level. Characterisation on only on list structure. Supplier how displayment and assessment if there is a technology dependent of 46C-0100. The bread charges that involve multiple stributes (eq. set, material processes), while the section 4.2 of the approximat desides 2.2 def00, which for the selection of wost-case test vehicles to cover all the possible permutation in the selection.
SEM-PW-12	Change of specified water process sequence (deletion and/or additional process step)	-	Any change which is not covered by another type of change. Risk is to be assessed. P (-): No Risk for Supply chain. (P): Risk for Supply chain (influence on product integrity)	(-): e.g. change of cleaning process in wafer production (P): e.g. additional sinker implantation after standard implantation (to protect circuit against interference impulses).	с													-						-	•
SEM-PW-13	Move all or parts of production to a different water tab site.	Р	P (described above). (described above).	e.g. dual source / fab strategy	A	Check if any other type of process change is applicable due to the transfer	•	•	•	• • M		• J	• • •			•••	•••	•	• •			н	- н -	-	 AEC-Q100: "For broad changes that involve multiple attributes (e.g., site, material processes), refer to section A1.3 of this appendix and section 2.3 of Q100, which for the selection of wont-case test vehicles to cover all the possible permutation
SEM-PW-14	Libography	-	Change in process technique for tithographic process and material (-): Five change in process technology does not influence the integrity of the final product. (#):: Five change in process technology can influence the integrity of the final product.	(-): e.g. exchange of defect mask (P): e.g. change from E-beam process to X-ray process e.g. change from contact into projection mode	с	Please also check changes described under EQUIPMENT.	•	•	•	• м		# -	• • •												•

		Change in process technique for colde / intertays	r l																						
SEM-PW-15	Oxide / Interlayer Dielectric	 P Charge in process technique for oxide / interlays delector process technique for oxide / interlays delector process technology does no refluence he integrity of the final product. P I: Hite charge in process technology can refluence he integrity of the final product. 	d.	A	Please also check changes described under EQUIPMENT.	-	•	-	•	м -	• #,	N D,J	•		· · •	• •	· ·	•	•••						•
SEM-BD-01	BARE DIE New final water thickness	P P Charge in final water thickness.	Change in final chip/die thickness	A				•			•						. Е	Е	Е.						ELTR can only be performed on packaged leat vehicles. NBTI was removed in deviation from the AEC-QHO Maths because there it is a combined type of change (Wafer Dimension/Thickness). NBTI is applicable for wafer dimension
SEM-BD-02	Change of top metallization or bond pad stack	P P Change in bondpads (incl. stack below), materia pad pitch, surface changes, layer thickness	I, e.g. change from ASICu to ACu	в							•														- change only.
SEM-BD-03	New / change of backaide metallization	P P Charge of bottom layer of dis (between dis and disadtrame). Charge in process, material, or dimensions.	e. g. change from CrNV/Au to CrNV/Ag	A							•						- M	м	• • •						•
SEM-BD-04	Change of water setup or number of possible good dies on water.	I P Readed information for pick & place machine. I P R: amount of possible good des or water (P): influence on water setup and water mapping		В			• •	•	• •									-					••••	• •	•
SEM-BD-05	Change of optical appearance of wafer edge region (like Imide coverage or edge exclusion)	I P Selection of dies in wafer edge region which have full electrical functionality. (P): in case of wafer edge is affected only (P): in case of angle die is affected	instead of square) (P): e.g. polyimide as new coating on die	В		-											• •							• •	•
SEM-BD-05	Die solbe or separation	Needed information for sawing and pick & place machine. I P (i): If the change in sawing process does not influence the integrity of the final product. (P): In case if product is delivered on water	(in tape and reel) (P)c e.g. information change for pick & place machine. e.g. information change for saving machine.	в	Please check if SEM-BD-04 is affected.			-										-							•
SEM-BD-07	Die Preparation / Clean	Change in process technique for dis preparation dearing P P: If the change in process does not influence the integrity of the intal product. @? I impert on product integrity is anticipated.	/ (-): e.g. change of cleaning time. (P): e.g. change in cleaning procedure after change of sawing equipment.	в	Please check if SEM-BD-O5 is affected.			-			•														•
SEM-BD-08	New / change of pasa/vation or die coating	P P Change of top layer on dis.	e.g. addition of polyimide e.g. change of polyimide thickness	в				-			• #.	N D,J				• • •	•••	•	••						•
SEM-PA-01	PROCESS - ASSEMBLY Change in critical dimensions of package	P P Change in dimensions of existing package.	e.g. changes in package dimensions (further	в				•	• •	м •		1		• T	•			•	• •		- L	н.	- н	н	
SEM-PA02	Change of leadhaire base material	P P New leadhame material in new composition.	development). e. g. change from alloy42 to copper e. g. change between two different copper alloys	в					_	м			_	•								н			
sed-Phul									1	•											-		11	-	
SEM-PA-03	Change in leadframe dimensions	Charge in leadframe dimensions which has imp to the specified electrical parameter acc, data wheet or approximations (as, phase tails), pin dimensions, die padde size,) Not included: Variation within specification.		в	ESD investigations are only necessary il internal ground and power apply connection of lead/mare is affected. At il impact of BMC behavior cannot be evaluated / excluded on component level.	÷	• •	-	•••	м -				•	•			-		•	·L	н -			•
SEM-PA-04	Ohanga of lead frame finishing material / area (internal)	P P Change of surface material of die attach pad and second bond area (e.g. influence in adhesion to mold compound, wedge bond reliability)	6 e. g. change from Ag faah to NP protection layer e. g. change from Ag spot to Au spot e. g. increase of silver plating area	c		•	• •	•	• •	м •			- c •		• • •			-			· L	н	- н		 For wire bond attempt test: Pre-& Post-process change comparison to evaluate process change robustness (AEC-Q101).
SEM-PA-05	Change of lead and heat skip plating material/plating thickness (external)	P P Change in material and / or process resulting in a new technology (e.g. pure tin).	e.g. charge in heat alug stack e.g. charge from Sn into NiPGNu e.g. charge of layer thickness	в			• •	•	• •	м •			- с		•						· L	н	- н		•
SEM-PA-05	Bump Material / Metal System (riternal)	P P Stack de or de to substrate (1ip chip)	e.g. change to Pb-free material e.g. change to Pb-free material e.g. change of copper piltars	с			• •	•	• •	м •	•			••				-			• L				•
SEM-PA-07	Die attach material	P P Change of die attach material and / or process neutring in a new technology (e.g. soft solder, spoor, etc.)		с	A: If impact on EMC behavior cannot be evaluated / excluded on component livel (If die attach has impact on electrical conductivity).	•	• •	•	• •	м •	•							-			+ L	н -	- н	н -	•
SEM-PA-08	Change of wite bonding	P P p Material, dameter, change in bonding dagram and / or change in process resulting in a new achinology.	e.g. charge from Au to Co material e.g. charge from 20µm to 20µm diameter e.g. charge from airgle to double bond e.g. charge from airch bond to aitch on bail bond.	c	A: In case of bond diagram change and EMC cannot be evaluated on component level. Please also check changes described under SEM-CO-01.	•	• •	•		۹.			• • •					-	- м			н.			Parameter Analysis, Strictly required only for Power devices, In person: Else all the remaining durings with impacts on transformass (e.g. born Au to Ca) ACCC102 To broad charges that incolven multiple ability of the case of the appendix processes), wher to assord charges and incolven should ability of the appendix of the appendi
SEM-PA-09	Substrate / Interpreter	P P Charge of BGA substrate	e.g. changes in routing	в	A: Impact on EMC behavior cannot be evaluated / excluded on component level. A: If impact on electrical function is not excluded on component level.			•	•••	м •	•		• •	- т						@• -	- L	н	- н	н -	•
SEM-PA-10	Die Owroot / Underfit	 Bupporting layers for complex packages like lip chips and / or change in process resulting in a ne andmology. P drange does not inhance the integrity of the find product. P is impact on product integrity is anticipated. 	w (): e.g. change of dispensing speed (P): e.g. change of undefill material	c				•	• •	м.	•							-			• .			н -	•
SEM-PA-11	Charge of mold compound / encepsulation material	p p Change of mald compound / encapsulation material.	e.g. charge to green mold compound e.g. charge of filer particles		B: Inspect on Hermo-mechanical stress caused by minimatch of mold compound, inferencementing technology and carrier is anticipated (pace) for Phone Pacinca). B: for wave soldmad division A: maar of high sequency sign pack () - 20Hz () schoold be A: maar of high sequency sign pack () -20Hz () schoold be A: maar of high sequency sign pack () -20Hz () schoold be A: maar of high sequence sign pack () -20Hz () schoold be A: maar of high sequence sign pack () -20Hz () schoold be A: maar of high sequence sign pack () -20Hz () schoold be A: maar of high sequence sign at the sequence sign of the A: maar of high sequence sign at the sequence sign of the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence sign at the sequence sign at the A: maar of high sequence sign at the sequence s			•	•	м •	•	•		•	•			-			• L				
SEM-PA-12	Change of hermetic sealing	P P Affected areas are material and process of hermetic (e.g. ceramic) packages, capped die a sealed devices (e.g. pressure sensors)	nd e.g. change of sealing material for RoHS	в	A: impact on EMC behavior cannot be evaluated / excluded on component level (if encapsulation / sealing has impact on electrical conductivity).	•	• •		• •	•				•	•			-				•	• •	• •	•
SEM-PA-13	Change of product marking	Change of marking on device and / or change in process resulting in a new technology () P (): I change does not influence the integrity of it final product. (P): If impact on product integrity is anticipated.	(R): e.g. change of appearance (additional marking) e. (P): e.g. change from inked marking to baser marking e.g. marking of pin 1	в			•						E												•
SEM-PA-14	Change in process technology (e.g. trim and form, leadframe preparation)	 P (-): If the change in process technology does no influence the integrity of the final product. P): If the change in process technology can influence the integrity of the final product. 	f (P): e.g. change from punched to sawn QFN	в	Please also check changes described under SEM-EQ-01. Please check if change is described by specific type of change in this matrix.	÷																			•
SEM-PA-15	Process integrity: tuning within specification	 Yanistion within process specification (-): it tuning within process specification does n (-): it tuning within process specification does n (#)uncos the integrity of the final product. (#): It impact on product specification is anticipated. 	st (): «.g. process control	с				-										-							•
SEM-PA-16	Change of direct material supplier		(-): e.g. change of wire material supplier. (P): e.g. change to new mold compound supplier e.g. additional leadmine supplier with specific leadmane manufacturing technology	c	Please check if material is changed	•												-							- Sea change of material.
SEM-PA-17	Charge of specified-assembly process sequence (deletion and/or additional process step)	P P	(-): e.g. additional cleaning step e.g. deletion of optical impection of (P): e.g. change lead triabing pre trim & form to post trim & form	с				-																	Qualification depands on specific change.
SEM-PA-18	Move all or parts of production to a different assembly site.	P P Assembly transfer or relocation. Includes transfer as well as additional site.	e.g. dual source / fab strategy	c	A or B: impact on other type of changes described under PROCESS ASSEMBLY and SEM-EQ-41. Check if any other type of process change is applicable due to the transfer	ŀ	•	•	•••	м -	•	•	•••	• т	•			-	•		• L	н.	- н	н •	Whisker tests have to be done on monitoring basis! EC-C100: "For toroad charges that involve multiple attributes (s.g., ste, materials, processes, refer to action 1/3 of the apprechanges of section 2/3 of 0100, which allows for the selection of worst-case test vehicles to cover all the possible permutations."
SEM-PA-19	Die sofbe or separation	 Separation process from single value to des. (-): If the change in process does not influence the integrity of the final product. (P): If impact on product integrity is anticipated. 		c		ŀ	•	•	•••	м .															•
SEM-PA-20	Die Preparation / Clean	Charge in process technique for die preparation desning P (-): If the change in process does not influence the integrity of the final product. (P): If impact on product integrity is anticipated.	/ (): e.g. change of cleaning time.	с			•	•	• •	м •	•		• • •										- н		•
SEM-PA-21	Malding / Encapsulation process	 Charge in process technique for molding / encapsulation. P (-): E the strings in process does not influence the integrity of the final product. (P): E impact on product integrity is anticipated. 		c			•	•	• •	м •	•			•	•						۰L				•

	PACKING/SHIPPING																			
SEM-PS-01	Packing/shipping specification change	Р	P Packing/shipping specification change.		•			· ·		 	 	 		 	· ·		 	 	 -	
SEM-PS-02		Ρ	P Change of dry pack requirements (e.g. change of MSL)	1	•		1.1			 	 	 		 			 -	 	 -	
SEM-PS-03	Change of carrier (tray, reel)	P	P Change of carrier (tray, reel)		В					 	 	 	1.00				 	 	 -	•
SEM-PS-04	Change of labeling	-	Charge of labeling site on reel. Ø: Charge of material label without impact on barcode. ØP: Charges of material label information which affects data processing at customer.	(I) e.g. additional information (RoHS stamp) (P) e.g. change of defined nomenclature for data processing	в			-		 	 	 		 	-		 -	 	 -	
	EQUIPMENT																			
SEM-EQ-01	Production from a new equipment/lool which uses a different basic technology or which due to its unique form or function can be expected to influence the integrity of the final product.	P	P Change in process technique which is not alread covered above.	Change from single wafer to batch process (e.g. over pad metalization) e.g. dambar cutting (mechanical to laser cutting)	A					 	 	 		 			 -	 		- Affected process change is to check.
SEM-EQ-02	Production from a new equipment/hod which uses the same basic technology (replacement equipment or extension of existing equipment pool) without charge of process.	1	PCN required for dedicated equipment for sensitive component production. (-): If change does not influence the integrity of the final product. (P): If impact on product integrity is anticipated.	(-): e.g. extension of existing equipment pool (P): e.g. extension of declarated equipment in case basic technology still need to be proven	c			•		 	 	 		 			 	 		•
SEM-EQ-03	Change in final test equipment type leading to a different test concept.	Ρ	P Change of tester platform with differences in HM or SW that makes a change in test concept necessary (only in case of bare de: final test means water bas).		с		· ·	•		 	 	 		 	-		 -	 	 -	Gage R&R / delta correlation
	TEST FLOW			·						 	 	 					 	 		
× SEM-TF-01	Move of all or part of electrical water test and/or final test to a different test site.	р	P Check impact on SEM-AN-01 Includes transfer as well as additional site	Dual source strategy	с	Check if any other type of process change is applicable due to the transfer	•	-	- e - e	 	 	 		 	1.0	· • ·	 	 	 ÷.,	Gage R&R / delta correlation
	Q-GATE																			
SEM-QG-01	Charge of the test convergeteeting process flow used by the supplier to ensure data sheet compliance (e.g. simulation) addees of electrical measurementuum flow flow block, electronic testing and the strategy processor or surgiving testing and the strategy processor or surgiving testing and the strategy processor or surgiving testing and testing processor or surgiving testing and testing test	1	 e.g. test flow block, reduction from three temperature measurements to teo temperature measurements, change in born in / non in process (-): If change does not influence the integrity of the final product. (P): If impact on product integrity is anticipated. 	(-): s.g. last implemented without customer requirement (PP): e.g. reduction from three temperature measurements to two temperature measurements e.g. change in burn in / nun in process.	c		•	•		 	 	 		 		• • .	 -	 	 -	Persmater Analysis: Data correlation * For them in changes ELVP recommended
	Tests, which should be considered for the appropriate process change.				~															•

Tests, which should be considered for the appropriate process change.	C	
Tests, which should be considered for the appropriate process change after selection of condition table.		• • • • • • • • • • • • • • • • • • •
Suppliers performed tests (mark with an 'X' for done or 'G' for generic)		
Reason for exception of tests and/or usage of generic data:		

-	Not required.	
_	Information Note required.	
P	PCN required.	
letter or "	* indicates that performance of that stress test should be considered for the	
poropriate	e process change.	
@ recom	rmended additionally by ZVEI	
-		lo
A	Only for peripheral routing	
в	For symbol rework, new cure time, temp	
С	If bond to leadlinger	
D	Design rule change	
E	Thickness only	
F	MEMS element only	
н	Hermetic only	
J	EPROM or EEPROM	
E.	Lead free	
M	For devices requiring PTC	
N	Passivation and gate oxide	
P	Passivation and interlevel dielectric	
Q	Wire diameter decrease	
T	Only for Solder Ball SMD	
- -	Only from non-100% burned-in parts	
	For "burn in" changes IOL or ELFR recommended	
	=> Please mark 'NO' with X, default is 'YES'	_

Worked on: (Name, Function) Date:		-																										
																Devic	e evalu	ation										
Signature:	0.000												MATERIA	L PERF	ORMANCE				s of AEC Q	02 – Revisi	on March15,	2017)						
		1			level (
	Assessment of Impact on Supply Chain regarding following sepects	Remaining			Evituation Inv A/ B/C		A market of the Constant	an the		Operating LF+	Contro d	o Human Doop Mada	. COM			(cum)											and the second sector	Remarks
charge an X	 contractual agreements softracti affree of processed/lip/meru/acturate/lip/ of castomer form, IX, function, quality performance, reliability 	riaka within Supply Chain?	Understanding of semiconductors experts	Examples to explain	A Ageloster lead B Boardend C Comperent lead	Parther applicable conditions	ve reduzio an tervisirello dal co AEC 0102 sect of specification	(e na ministred) 11 hga Terqena a O	E Tengenson Cjobe	readen võring.	S. Pare Tengoraue	ECO Characteristic	ESO Charlothéa le	Phy size (Dimension	Tarriel Drag h	K. Variation Variation F.	E Meximal Shock	Le feat a blicerite Discertalia	Hydrogen Saly No	And And And And	Contra Contra	Mine Manual Cam	The error file side an co	at Netleot Na	the fixed thear	De Dear Bailer Groe	Parameter Analysis Comparison of over	
LED-AN-01	ARY Any change with impact on agreed upon technical contractual agreements	p p	triended to be used if no other type of change i applicable by the change affects acreed technical contractual acreements.	4	•	1		- 4 						ч			-											
LED-AN-02			Site processability on board level technical interface means component terminals			Check if LED-0541 is affected Processability should be assessed.	• • •		т			-					-	S,T -						-	-			
	DATA SHEET Change of databased parameters/rectrical specification (nin-Joan, byp. values) and/or Pulse/DC				1	1			1	1	1		1					1			1	1	1	1 1		1	-	
LED-05-01	Drange of designed parameters/electrical specification (min.imax.hyp. values) and/or Pulse/BC specification	p p	Change of application relevant information (e.g. maximum pu summt) due to a technical product or process change.	e.g. change of die substrate naterial.	*		· · ·	. Е	E	E	-	E	E	1		-	-	s .		E			E		-		E	
Libeses	Correction of data above or insure of wrates		Change of application revealed internation (e.g., maximum pu- current), due to a scholarial product or process of hear. No instruction damage of poduct, process or text. New description of tensorium/scholar application or whice distances too instructional application or explicit distances too instructional application or explicit distances too instructional application required.		*		• • •	•	-	•	+	-		-	-	-	-			-	-	-	-	-	-			
Libeses	Specification of additional parameters		E Definition of an additional parameter which was not specifie before P. If there is a risk on supply chain where at least one addition of the PCM-relevant change category will apply.		*		• • •	•	-	-	-	-	-		-	-	-	•	-		-	-	-	•	-		•	Formatian since this is not a product change, ony additional information Cases/Formation: C
LED-DE-01	Design dhanges in epitasy.	p p	Any device relevant dharges in design I layout of optical injurys for landaed. Changes within design stars and angle optication without attending specified functions, parameter and initiating in sing design / layout. New foregoint of design / layout. New foregoint of the design relevant and angle the foregoint of the design relevant and angle with initiation micro and peopled functions, parameters and another relevant	e.g. change from Double-Intens to Quantum wells e.g. change of barrier thickness	c	A change from Double herers to Quantum webs spectrum is affected	•	•	-	•	•	•	•	-	-	-	•		-	•	н	-	-	•			•	
LED-06-02	Design changes in souting layout.	p p	Not included. Changes while design rules and design specification which a design specified functions, parameters and reliability.	e.g. change in layout of current spreader; thickness of current spreader e.g. reduction of bond pad size	c	A change in layout of current spreader radiation pattern changes	• • •	•	•	•	•		-	1			-	• •	м	•	м	м		в	в	о,м -	•	TR might be considered for complex die band technologies
LED-06-03	Die skrink	p p	Not included: using street/writisribe ine	Typical shrink of die.		Pease check if change is process technology (LED-PW-08) is also affected.	•	•			•	•	•		-	-	-	•	-	•	-				в		•	
LED-DE-04	LED package (eccept leadform)	p p	any change in housing thickness any change in turn-or dimensions.	e.g. change of dimensions e.g. change of x, y, or 2 dimension of the package		Check if LED-05-02 is affected which leads to a change of the elchooptic parameters or distributions.		•	•	•	•	1.1	-	٠		v	v	• 1	D		D	D	L	в	в	D -		
ut-0646	Design of HeadTame PROCESS - WARE PROCECTON	P P	any change of leadhane / carrier dimensions. any change of outer dimensions	e.g. change in leadTarke / cartier dimensions in $\chi_{\rm F}$ or 2 direction. e.g. change inner design of the leadbarke not affecting the sic performance & reliability of the device.		Check if LED-05-02 is affected which leads to a charge of the elchooptic parameters or distributions.	• • •	• •		•	•	•	•	•	-	v	v	• •			-		•	в		D 2	•	
LED-PW-01	New/ change of water substrate or carrier material	p p	New water substrate material.	e.g. different water material to currently released naterial (change from Sapphire to Silicon)	c	Check if LED-05-02 is affected which leads to a change of the elchooptic parameters or distributions.		• •	Р	Р	•	Р	Р			-	-	•	Ρ	•	Р	Р	•			• •	•	
LED-PW-02	Vilder diamater		change of water diameter resulting in equipment and process changes.		c	It case other type of changes are affected i.e equipment/process technology - they need to be identified in addition	• • •	• •		•	1	Ρ	Ρ	+	-	-	-	•		•	-	-	•	-	-	-	•	
LED-PW-03	New final author thickness	P P	Change in final water thickness	e.g. charge in final chipide thickness	c	Check if LED-0540 is affected which leads to a change of the elchooptic parameters or distributions.	• • •	• •	•	Р	•	Ρ	Р	+		-	-			•		-	•	в	в	• •	•	
LED-PW-04	Change of electrically active-disping/implantation element	p p	Change in electrically active doping / implantation element resulting in a new technology.	e.g. change from ite to C as dopart	c			•		с	с	•	•	+			-		-	•		-	•		-		•	
LED-PW-05	Change of stacking		change in layer sequence or thickness	e.g. change of isolation layer thickness between n- and p- material	A	dustomer application needs to be checked due to potential system voltage differences	• • •	•	F	•	•	•	•			-	-			•	F	-	-				•	
LED-PW-06	New/ change of metalization (specifically chip formulae)	p p	Change in metallization of bondpads, material, layer thickness	s e.g. change in bond pad metalization thickness	c		• • •		•	•	•	M,B	M,B			-	-			•	м	м	-	•	•		•	
LED-PW-07	New/ change of metallization (specifically chip backside)	p p	Change of bottom layer of die (betwees die and likadhame/carlier). Change is process, material, or dimension tecessary.	is e.g. change from Aa to AurGe	c	A customer application needs to be checked due to potential system voltage differences B chaose here CVD den to an mar den for	. • I	• •	•	•	•	D,M	D,M	+	-		-	•	D,A	•	D,M	D,M	D,M	-	-	• •	•	
LED-PW-08	Change in process technique (e.g. significant process changes like lithography, esch, celde deposition, de tack surface preparation/backgrind,)		Change from wet to dry estilling, change from horizontal to vertical own fair oxidation, change from consuct time into shipper little,		c	differences Bi change trum CVD dep to aputer dep for backside/furnicies metalization. In case of new equipment please sheck? UD-PA-14 is also affected.				-		-		+	-	-	-				-	-	-		-			Qualification effort depends on type of change.
LED-PW-09	Prozess trengely. Tuning within specification Change at namelal supplier within to impact on agreed specifications	- P	Variation within process specification Change of water supplier. Change of supplier for chemicals seeded for water production.	e.g. process control e.g. Change of water supplier.	c									1.1					-				-		-		-	Qualification effort decends on type of chance.
LED-PW-11	Change of specified water process sequence (deletion and/or additional process step)	- P	needed for water production. Any change which is not covered by another type of change. Rak is to be assessed.		с												-				-	-						Qualification effort depends on type of change.
LED-PW-12	Change in die coating or passivation	P P	Change in material, thickness, and process for stating and passivation	e.g. change from SIC2 to SIMI	c					-	Ρ	Ρ	Ρ	÷	+	-	-		Р		Р	Р		Р				
LED-PW-13	New walker production faction or transfer of walker production to a different not previously released location/ultimutocomposition	P P	New water proposition location or transfer of water productio with possible additional changes.	<u> </u>	c	A or B: Impact on other type of changes described under PROCESS - WHER PRODUCTION and EQUIPMENT categories of this DeQUIA	• • •	•	•	•	-	•	•		-			•		•	· ·	-	J	•	•	•		
LED-RD-61	BARE DE DELVERES New/ change of front side metalization	p p	Change in bondpads, nuterial, pad pitch, surface changes, Byer Bickness	e.g. change from As to Au alloy e.g. change in over cad metalization				•	•	•	•	M,B	M,B				- 1		•	•	•	•	•	•	•			
180-80-62	New/ change of backside metalization		Change of bottom layer of die (between die and Readformercamer). Change in process, material, or dimension			Check if LED-05-02 is affected which leads to a change of the elchooptic parameters or dimension		• •			•	D,M	D,M		-		-	• •	•		•	•	•			• •		Curclomer application needs to be checked due to potential system votage differences
LED-RD-03	Change of water samp or number of dies on water.	1 P	Needed information for pick & place machine. 5. only additional number of drips Pt change in spacing between chips and form of water	e.g. information change for pick & place machine.																		-						
LED-RD-EX	New final autor thickness	p p	P: change in spacing between chips and Some d water Changes in final Chip height (including same); very take and exactly combined with a material change (change of carrier listenia)	e.g. change on converse thickness		Check if LED-05-01 is also affected.		• •		Р	•	Ρ	Р	•			- I	• •				-		в	в	• •		
LED-RD-65	Change in die coating or passivation	p p	Insterial Change in material, thickness, and process for stating and passivation	e.g. change from SIC2 to SMI		Check if LED-05-01 is also affected.				•	Ρ	Р	Р					• •	Р		Р	Р		Р				
LED-PA-01	PROCESS - ASSEMBLY Change of Inadianny Lander Date motorial		New leadBamelcanier material (new in composition)	e.g. change from copper alky to bare copper	8	Check if LED-09-03 is affected which leads to a change of the electocopic parameters			1.						3				A		A	A			•		· .	Explanation should be provided in case H25 test is not applicable Regarding applicable number pieces refer to the Whisker standard.
LED-PA-02			Change of ourface material of die attach pad and second bor	id a c change from #s fight to Nikt contection lawsr	•	or distributions.		P		_	•			-		-		•			A	A .	P,1			•		Regarding applicable manetals please refer to the thibiter standard. MSI text should be considered for automotive extension applications, explanation should be provided in case HOR test is not applicable
LED-PA-43	Change of load and heat thig plating materialiplating filicitness (edemal)	p p	Imaging a limitance in advection to make compound, wedge soon installing. Change in material and process technique to their pin- emination (in-g, pare to), Neero-Catago, processibility an establity on board level can be writfied by generic data. Classification depend on impact of datage. Stock die or die to advection	a.g. change in hear slug stack e.g. change from Sn into NéPatka e.g. change of leger thickness	8		-		•	к	+	-	-	1	-	-		• •	A		A	A	P,1		-	- в		Explanation should be provided in case HBS text is not applicable Regarding applicable manifalt please refer to the Whisker standard.
LED-PAGE	kump Material / Metall System (internal)	p p	Stack die or die to substrute Phanese of die structure possibilities and and de anover and	e.g. change to Pt-free material	A 8			• •			•		-			- N	N	• •	w		W	w	<u>.</u>	-		•		
LEDPARE	Die attach material Change of bond wite material	P P	Change of die attach namelal (e.g. soft salder, epole, etc). Thermat management must be respected. Material, wire diameter, change in process technique	e.g. change of Ag glue to Au glue; e.g. change from 30µ to 21µ	в А											N	N D		Q 9,9			Q P,D		•		•		Site audit for material change with impact on bondprocess (e.g. from Au to Cu) recommanded.
LED-PA47	Change in naterial for sub-components (excluding LED chip & LED package related berris) with impact on agreed specifications	- P	Wateriar, wire claimeter, change in process technique Change of sub-component supplier using different technology/materials Note: Jung start tect of CRMs might be necessary	e.g. change trom 30y to 28p e.g. using a different ESD-dode intechnology and material than previously		Check if LED-09-01 is also affected.													P.4									to Cu) recommended. Qualification effort depends on type of change.
LEDPAGE	on agreed specifications De Oversoar / Underfil	<u> </u>	Note: Junp start test at Olifits night be recessary Supporting layers for complex packages like flip chip.	Pas previously P. e.g. change of underfit with change of thermal insultance		Check if LED-05-01 is also affected.				P							P	•	P			Р	U			υ.		and address of the second
LEDPAGE	Die Develouit / statemit Change of multi compoundercopsusticit/sealing material	P P P	Supporting types the complex packages like flip clip. - No change is productively by the clip clip clip. P: change can influence the strength of Snat product. Change of relation populations, or can show the clip clip clip clip clip clip clip clip		*	Check if LED-0941 is also affected.				•	•			D	3	D.		• •	P		P	P	P	-				
LED-PA-10	Change of convension material	p p	has to be assessed. Mit, might be changed. Change of material class.	e.g. change from granues to nitrides	с	Check it LED-05-01 is affected for optical/photometric parameters			Y	•	•	-				Y	Y	•	Р	Р	Р	Р	Y					
LED-PA-11	Dhange of direct supplier for converter material	P	New supplier with same material specification		c			• •	Р		•					Ρ	Р		Ρ	Р	_	Р	Р	-				
LED-PA-12	Change of converter process technology		new technology for converter production E no influence on e/u performance of product Pr in case of impact on product integrity	e.g. change from volume convension to bayer conversion; e.g. change from stamping to printing of bayer	c	Check if any change in electro-optical characteristics results in change of data thest LSD-05-61		•	Y	•	•	-	-			Y	Y	• •	z	z	z	z	Y					
LED-PA-13	Change of product marking		Maning on device. E change in appearance, readability not affected P: change of content or change of appearance of data matic sode	e.g. making of cathoda;	8		• • •	•	0	-		-		-	-	-	-	тт	-	-	-	-	-	•	-			
LED-PA-15	Change in process technique (e.g., die attach, bonding, musiding, plating, trim and form,] Process theyalty: Turing within specification		Any change in assembly process technique Variation within process specification	e.g. change die attached hom gluing to saldering: e.g. process control	B C	A or it: Peake check if EQUIPMENT and other type of changes of material (EED-PA- BERGIONTTREMING) are affected	• • •						-		-	-		• •			-		-		-			Qualification effort depends on type of change.
		· · ·			-														-				_			_		

LED-PA16	Change of direct material suppler with na impact on specification	-	P Change of suppliers e.g. for lead transes, wire material, die attach, electronical components	Change of suppliers e.g. for lead frames, who material, ESD- diade	c	Assumption that change material specification remains unchanged. Otherwise see change of material.	• • •	-				-	-						-				-			(\cdot, \cdot)	See change of material.
LED-PA-17	Change of specified-essentially process sequence (additional and/or deletion of process step)	ı.	Addition or deletion of a process step in assentity process adquerce with generitably egisticant inpact on the product participation of the product itsephy is no influence on product itsephy in influence on product itsephy espected.	e.g. additional or deletion plasma cleaning process	c	Single case assessment necessary to identify possible interactions or risk.		-			-	-		-			+		-	-	-	-	-			1	Qualification effort depends on type of change.
LED-PA-18	location reference on a dar	Р	P New assembly location, assembly transfer or relocation. Transfer of known technology and equipment.	e.g. Dual source strategy	c	A or its impact on-other type of changes described under PROCESS ASSEMBLY and EQUIPMENT	• • •	-				-	-				-	-	-	-		-	-			+	Qualification effort depends on type of change.
	PACKING/SHIPPING																										í l
LED-P3-01	triver Packing Misping law officiation change	P	P dimension chance of direct product packing	e.o. SMT pocket in tape changes	B		. P				P	P	1.1				T										
Labyardi	Iner Packing Milpong specification change	v	· · · · · · · · · · · · · · · · · · ·	a.g. SMIT pocket in tipe changes							P	r										-					
LED-PS-62	Outer Packing Mipping specification change	1	dimension changes indirect product packing P & small changes in dimension or appearance P: number of mets in the packing are changing	eg pittebox				-		· ·	-	-	+	1.1			1.1		-				-		1.1	1.0	1
LED-P543	Change of labeling	r.	Change of labeling also on reel. P It additional information no change of previous information P) change in content of previous information	(b) e.g. additional information (RoHd) stamp) (P) e.g. shange of customer specific information	8	Check if LED-05-01 is also affected.		-					-					-	-	-	-	-	-			+	
LED-PS-01	Dry pack requirement change	р	P Change of dry pack requirements (change in MSL)	e.g. change from Mill.3 to Mill.1		Check if LED-05-02 is also affected.	2 . A . A . A .	1.1																		÷	í.
	EQUIPMENT																										(
LED-EQ-61	Production trum a new equipment/boot which uses a different basic technology	р	Change in process technique which is not already covered stores. Note: Major changes affecting the product not covered by the latter mount also a PCN.	e g change tromisingle water to batch process e.g. over pad metalikation e.g. dantbar cutting (mechanical to baser cutting	8	Check if LED-05-01 is also affected. Consistent stability should be assessed.	• • •	-	-				+	-	-		-	-	-	-	-		-			-	Qualification effort depends on type of change.
160-60-62	Production from a new equipment/box which uses the same basic technology (replacement equipment or extension of existing equipment pool) without change of process.	-	PCN required for dedicated equipment for sensitive component production.	e.g. change from single site to multi site handler.	c		• • •				-	-			1		1		-		-	1.1	÷.,		1.1	1	Qualification effort depends on type of change.
LED-60-63	Change in final test equipment type that uses a different technology		Change of tester platform(e.g. region test program changes, test tester interface,) E-product specification is not attested P-product specification is affected	e.g. change in text method from of to lumen	8		. • •	-			•	•	-	-	-		т	-	-		-		-		-	•	diage Ritik / deta correlation
	TEAT FLOW																										í .
LED-19-41	Nove of all or part of electrical wafer test and/or final test to a different location/she/subcontractor	р	P Tester transfer or relacation.	e.g. Dual source strategy	c		• • •	в	•	• B	•	•				•	т	-	в		-	-	в	в в		•	Gage RdR / deta correlation; additional specification check It should be considered for Water testing
	0-GATE																										
LED-03-01	Charge of the text soverage testing process flow used by the supplier to ensure data sheet compliance (e.g. elimination/addition of electrical measurementheit flow block, initiaation/enhancement of mentaring procedure or sampling)	-	P Reduction or additional southof steps, test coverage within the process flow	e.g. test flow block like Final test / final clearance	c			-				-	+	-			+	-	-		-	-	-		-	•	
Tests which a	hould be considered for the appropriate process change.							_											_			_	_		_	_	-
read, which a	nous an community of the appropriate process charge.				_				-			-	-	-	-		-				-	-	-		-	-	
Tests, which s	hould be considered for the appropriate process change after selection of condition tal	ble.											1					÷		÷							
Suppliers peri	ormed tests (mark with an 'X' for done or 'G' for generic)																										
Reason for exc	ception of texts and/or usage of generic data:					1		-					1 1				-		-				-			-	



Worked on: (Name, Function)]																																					
Date: PCN number:	12/06/2020 PCN 20, 0171		Form provided by 2VEI - Revision 4.1 - November 2019													D	evice	evalu	ation																				
Signature:												МА	TERIAL	PERFOR	MANCE 1	EST RESI	ULTS on I	the basi	s of AEC	-Q104 Re	vision -S	eptemb	er 14, 20	117								addition AEC-Q	al to 10x						
	Assessment of Impact on Supply Chain reporting following supersa - entranal of personal - entranal supersonal assessibly menufactuality of costment - term, fit, function, quarky parliamences, whitelity	Remaining risks withi Supply Chain?	Dedentanding of sentembershore segurin Examples to explain	Lovel Evaluation lovel Lovel A/B/C	Further applicable conditions	ydde orauthonsected) evision September 14, 2017	f uub component) Toucontain thereigt a film with and table	Autoclave or Urbin red HVST	Temperature Cycling Power Temperature Cycling	High Temperature Storage Life High Temperature Operating Life	Fair I to Bit to Bate	cary Lie Failor More MrM.Endurance, Data Reinin fan , and Coartsboal Lie	Wire Bond Shear	WireBond Put Soldentidity	Physicial Clime resizes Solder Bail Sh ear	Lan dirtagity Xray / CSMA	Biocranic Discriming in Human Body Model	Electronic Discharge Changed Device Model	Latch up	Electrical Celebration Fault Grading	Characterisation	Electromagnetic Compatibility Soft Error Parts	Harrotic Package Tast	ჩაძადი Drop	LidTarque	Dia Sina ar Internal Vitaor Vapor	Board Lavel Relationly. Low Temperature Stange Life	Start Up and Temperature Steps MCM Dino Teat	Destructive Physical Analysis	Xeny	Acoustic Microscopy	Whiteke Mut (000 00006612406, JE DE C. JEST DOVI) Distribution A valuation	Comparison for a survey with the changed days as Comparison, electrical of initial on			Re	marks		
ın a	Type of change	No Yes		A: Application I B: B conditivel C: Con ponent "Not relevant		C-0104 R		9	2 2	frsu) frau)	a a a a a a a a a a a a		MBS V	VBP V	0 88	0 AND	Wa	was	3	a g	CHAR 0	BMC R	NECH N	000	1	g ¥	BLR E	STEP 1	Ye0	OBAY)	10								
MCM-AN-01	ANY Any change with impact on agreed upon technical contractual agreements.	P P	Inunded to be used if no other type of change is applicable to a the change allocts agreed sechrical roomerchal innuments	•		VEX (cent		a AS							C4 C2		r E2 -							(GS -	G8 -	G7 G8	H1 H2	нз н	4 HS	нs -	H7 -							_	-
	Any change with impact on processability/manufacturability at customer, which is not covered in the matrix below.	РР	Any change which is not covered in the matrix below, but fait assessment at customer is recommended.	в		1.		•	•		•		-						-	•	-					• •	• •	•		+			•						
MCM-DS-01	Charge of datasheet parameters/electrical specification (min/max/kgs.values) and/or ACIDC specification	P P	Lipide of the thet is based if why call charge of the second seco				-	•		• •	-		•			•		•	•		-		-	•	•	• •	• •		-	•	•	•	•					_	_
MCM-DS-02	Correction of data sheet / errola		specification specification Please indicase clearly, that Mo note contains this type of changel Assessment in antification serviced	*							•						-	•	•											1	1		1						
MCM-DS-03	Specification of additional parameters	1 P	Security for a new not previously rowshown as the product, the product of the pr	A		19 (A)	•			• •				• •		-	-				•				•					•	•		•						
MCM-DE-01	DEBON	1 1	In goald subsets by decigo or heartory as defined by e.g. addison of Firmann opportunities the control of the star effect of p_{1} e.g. addison of Firmann opportunities the control of the star effect of the star effect of the star effect of the control of the star effect of the control of the star effect of the starters of the control of the starters of the control of the starters of the star	A		· .	•														•									•									
MCM-DE-62	Charge that adds or subtracts sub-components from the module BOM	P P	n.g. addition of paralee elements in filter circuit	A		•	•	•	• @•	۰.	•	•	•				•	•	•	• •	$ \cdot $	• •		D .		8F -							·						
MCM-PA-01	PROCESS - Assessment + MATERIALS	РР	Change from an AEC Dualified sub-component to a NonAEC Dualified sub-component or Change from a Nan-AEC Dualified sub-component is another NonAEC Dualified sub-component	A		•		• • •	• •	• •	•	• •					•	•	•	• •	•	• •	(@•,I	D @•		@ F ·				@•	۰.		•						
MCM-PA-02	Replacement of any sub-component by an AEC qualified sub-component	p p	Is a worker Nex-AEC Calable dat-component Collenge hom cark AEC Calable dat-component In andere AEC Calable dat-component Collenge from a NexAE C Calable dat-component en ga with impact an existencia charamente (ESD, lateh e.g) electical territorially stat comenge	A	Requires additional evidence that new sub-component is AEC qualified	•	•				•						•	•	•		•	• •	e @•.1	D @•		8 F ·			6.	ϥ	۰.		•						
	Replacement of any sub-component by an AEC qualified sub-component Critical characteristics of sub-component are <u>not</u> affected		e.g. with so impact on electrical robustness (FSD, listch up,) electrical functionality, test coverage	с	Requires additional evidence that new sub-component is AEC qualified	•	•			· @	•	· @	•													@ F ·	• •		6	ϥ	@•		·						
	Change within a sub-component that has been requilified Critical characteristics of sub-component are affected		e.g. with impact on-electrical robustness (ESD, bath $(\mu,)$ electrical functionality, test coverage		Requires additional use of the appropriate ZVETDeQuilts (e.g. active, passive component) for qualification of the changed sub- component Previous additional use of the averand set ZVETDaQuilta is o	•	•					•	_				-			• •			_	_		@ F ·						-	•						
MCM-PA-05	Charge within a sub-component that been requilified Ortical characteristics of sub-component are not affected	1 P	e.g. with <u>and</u> impact on electrical solutions (ESD, latch-up,) electrical functionality, test coverage Design changes and reading Design changes and reading	c	Requires additional use of the appropriate ZVETDeQuilta (e.g. active, passive component) for qualification of the changed sub- component	•	•					• @	•				@•	@•	@•	• @•		• @	M @•,I	D -		@ F ·						-	·						-
MCM-PA-06	Salatana changa alfacing models schematic (Changes to the internal dimensions and / or schematicu)	P P	Interrupt - (characteristic statistic statistic) Disegis charage and charafing demonstrate with Disegis charage and statistic statistics of the statistic statistic statistic statistics of the distant state of specification is a plant statistic part distant statistic statistics and the statistics of distant statistics of the statistic statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the statistics of the distant statistics of the statistics of the statistics of the statistics of the statistics of the distant statistics of the statistics o	*		•	• @	•••	• ек		-	•	@•	@• ·			•	•	•	• •	•	• •	•	•	•		• •		6	-	-	•	•						
MCM-PA-07	Charge to the processes used in module assembly (a.g., pick & pison, die attach, bonding, millow, encapsulation, singulation, die owercaw, underfit, die preparation, die clear)	- P	(-) If the change is process technology does not influence the integrity of the final product. (-), if a g, tuning within process specification influence the integrity of the final product.	c		•		•	• @к	· @.	A -		•	• •	• •	•		•	- 0	≬н -	@•	• •		•	•		• •	• •	6	-	1	-	·						
MCM-PA-08	Process imagity string within specification	- P	Variation within process specification (−) I funing with process specification data not induces the integrity of the final product. P(r) I impact on product specification is anticipated.	c		19 (A)	•		-	• •	•		•			-	-				-				•		• •			•	•	•	-						
MCM-PA-09	Change to materiale used in models assembly (e.g., adhesive, underfit, encapsularie, subder, epoxy, bump material, die attach material, bond wire, die overcast, substanse, leadhane basie material)	P P	Change of used material (e.g. bump material, de s.g. Stack de or de to substrate (Bp.chip) s.g. changes InDe Neter material Change al Erode with material, dismeter, change in bording disgram e.g. change al Cooper Jahan e.g. change al Cooper e.g. change al C	c	B: impact on thermomechanical stress caused by mismatch of mold compound, interconnecting technology and carrier is anticipated B: estematilead finishing material is affected	·	•	•	• ек	@• ®I	E Ø	E -	•	•••	•••	•			-	•	@•		-		•		• •	•	6	•			•						
NCM-PA-10	Charge of direct material supplier	- Р	Change of suggisters the direct meansials which are given by the second	c	Please check il material is changed		•			• •				• •		-	-				•				•					-				se change of r					
MCM-PA-11	Charge to assembly location (Mow all or pasts of production to a different assembly sile)	P P	Assembly transfer or telocation e.g. dual source / fab strategy holdes transfer as well as additional site	c	A or B impact on other type of changes described under PROCESS ASSEMBLY and SEM-EQ-01. In case of Curwine product please consider AEC-0006.	• •	•	• •	• ек			•	•	•••	• @	•			-	•	@•								6.			٥.	• A6 pro	hiskertests ha EC-Q100: 'Fo ocesses), refe a selection of r	ve to be done broad change r to section A1 vorth-case test	e that involve 3 of this appre- vehicles to co	basis multiple attrib ndix and sec over all the po	ributes (e.g., si ection 2.3 of Q possible permu	oto Oto mutai
	Charge of product marking		Change of making on decise and for change in process realing in a new schrology. B: E change dass nei inflance the integrity of the four product. By E Impact on product integrity is anticipated.	8		19 (A)	•	•					•	. в		•					•	•		•	•					•	•	•	·						
	Packinghitoping specification change	P P P P	Packinghthisping specification change. Change of dry pack requirements (e.g. change of										-	 					-		-			-	-	 											_		Ē
MCMP548	Ounga of tanke (bay sud)	P P	MSL Charge of caster inter, mell Charge of caster inter, mell (), e.g. addronal internation/Ruli G tamp) Stander, e.g. of manual label information whom (), e.g. addronal internation/Ruli G tamp) P/S Charge of instanciable information whom (), e.g. addronal of tamp of defined international target of tamp Milesch dam proceeding of casteries. ()	8		· ·		· ·	 	· ·		· ·		· ·		•	•			 				-	-	· ·					•								
NCM-EQ-01	EdupletCNT Production from a mewequipmenthoid which uses a different basic inchroibgy or which due to its unique form or function can be expected to influence the imaginy of the final product		Change in process technique which is not already change in process technique which is not already covered above.	A															-	•	@•									-			• /4	fected proces	s change is to s	zheck.			
MCM-EQ-02	Production from a new equipmenthoal which uses the same basic technology (splacement equipment or essentiation of exaiting equipment pool without change of process.	. р	PCN required for dedicated equipment for sensitive component products. (F) If or the descent of hear case the integrity of the (F) If or the descent of hear case the integrity of the basis product. (F) If impediate on ponduct theory is anticipated. (F) If impediate on ponduct theory is anticipated.	c		1. A.															.																		
	Change to testing platform (Change is finalisat equipment type leading to a different test concept) TEST FLOW	P P	Change of tester platform with differences in HIV or 2W that makes a change in test concept recessary	c		•		·			•								-	•	۰.			•	•		• •			ŀ		•	• •	sge R&R / del	a correlation				

MCM-TF-	(Now of all or part of the final test to a different test site) P P Check in test	r transfer or milocation. k impact on MCB4-NH-01 busi source strategy as transfer as used as writikional site.	c	
	OGATE			
MCM-QG	Charge of the test coverage/setting process flow used by the supplier to ensure data sheet compliance 1 is a diministration/addition of electrcal measurementheat flow block, relaxation/entrancement of monitoring 1 procedure or sampling	nd loo kod, no ductor fan Thea kergenste uweren to hou fryskelen wijkeren to hou fryskelen wijkeren gelanste roop, do ker of kerke fer belagt of the roop of product hergefy is writegees.	c	
	Tests, which should be considered for the appropriate process change.			
	Tests, which should be considered for the appropriate process change after selection of condition to	table.		
	Suppliers performed tests (mark with an 'X' for done or 'G' for generic)			
	Reason for exception of tests and/or usage of generic data:			
	reason of exception of tests and/of dange of generic data.			

Not required. Information Note required. P IFCN required.

inge.	 Indicates that performance of that streas test should be considered for the appropriate process mended additionally by 2VEI.
	CONDITIONS No
A	die preparation and/or die clean
B	For symbol rework, new cure time, temp
с	If bond to leadfinger (requirement in Q100)
D	G1 - G3: no G4
E	only for bare die and change of mold compound
F	bare die sub-component only
н	represses for material in direct contact with dia surfaces
ĸ	For devices requiring PTC (requirement in Q100)
м	Applicable for subcomponents with > 1M SRAM or DRAM per AEC-Q100
T	Only for Solder Ball SMD (requirement in Q100)
	For "burn in" changes IOL or ELFR recommended

History of DeQuMa

Version	Remarks
2.0	Revised by ZVEI PCN Methodology Workgroup in March 2015
2.1	Released March 2015
2.1.1	Active Components - delete write protection in comments
2.2	Solved problems with some ActiveX configurations
2.2.2	Solved Problems in Active Components
2.2.3	Solved Problems ActiveX, Active Components SEM-DE-02 (Design changes in routing) error fixed
2.2.4	Minor fixes
3.0	General Revision by ZVEI PCN Methodology Workgroup in June 2016
	Changes are indicated by underlining in the read only version named Changes_DeQuMa_rev3_vs_rev2.xlsx
3.0.4	Expert Release
3.0.5	Fixing of macro bugs
3.1	Final Release (orthographic and punctuation corrections)
4.0	General Revision by ZVEI PCN Methodology Workgroup in July 2019.
	Muliti Chip Modules newly added to DeQuMa
	LED Components now based on the AEC Q102
	Further Changes see separate PDF's Excel-File, where changes are indicated by underlining
4.1	LED worksheet: Content of columns had been swapped due to rearrangement and omission of columns.

DeltaQualifikationsMatrix

Allgemeines

prozeß- und werkstofftechnischen Änderungen an Bauelementen, Leiterplatten, Verbindungstechnik und Schaltung, welche evaluiert werden müssen. Eine geeignete Methodik zur Handhabung von Änderungen an elektronischen Bauelementen beschreibt die ZVEI "Guideline for Customer Notifications of Product and /or Process Changes (PCN) of Electronic Components specified for Automotive Applications". Ein wesentlicher Teil dieser Guideline sind die hier vorliegenden Matrizen, welche sich als Empfehlungen für die Evaluierung von typischen Änderungen an elektronischen Bauelementen verstehen. Dies sollte Teil des offenen und risikobewussten Dialoges zwischen Lieferant und Kunden sein.

Diese DeltaQualifikationsMatrizen wurden durch den Industriearbeitskreis "PCN DeltaQualifikationsMatrix" und den Bauteilexperten des ZVEI Arbeitskreis "PCN-Methodik" erarbeitet. Der Inhalt wurde basierend auf dem aktuellen Stand der Technik erstellt und erhebt keinen Anspruch auf Vollständigkeit. Im Einzelfall ist ggf. ein abweichendes Vorgehen abzustimmen, da kundenspezifische Vereinbarungen zur Qualifikation zu berücksichtigen sind.

Anwendung der DeltaQualifikationsMatrix (auszufüllen durch den Bauelementehersteller)

- a) Diese Tabelle ist nur bei Änderungen anzuwenden. Neugualifikationen und Sondergualifikation (z.B. Verauß von Modulen) sowie Information Notes bleiben von diesen Matrizen unberührt. b) Ist eine Änderung in dieser Tabelle nicht aufgeführt, so ist der Qualifikationsumfang zwischen Kunde und Lieferant abzustimmen.
- c) Die Matrix der Aktiven Bauelemente ist so aufgebaut, dass zwischen integrierten Halbleitern (AEC-Q100 Rev. H) und diskreten Halbleitern (AEC-Q101 Rev. D1) auszuwählen ist (Zelle D4). Für passive Bauelemente gilt die AEC-Q200. Für LED's gilt die AEC-Q102. Für Multi-Chip-Module ailt die AEC-Q104.
- d) Alle Änderungen in der PCN sind in der Spalte B durch ein Kreuz (x) zu markieren und werden dadurch farblich hervorgehoben. Sofern dies geschehen ist, werden im Feld "Tests, which should be considered for the appropriate process change" alle in Betracht zu ziehenden Zuverlässigkeitstests angezeigt.
- e) In "Tests, which should be considered for the appropriate process change after selection of condition table" wird die Anpassung der in Betracht zu ziehenden Tests in Folge der Relevanz bezüglich der Änderung berücksichtigt
- Dazu ist die Tabelle "Conditions" entsprechend der Auswahl (A/B/C) mit einem (x) zu bewerten. In "Suppliers performed tests" dokumentiert der Bauelementehersteller die durchgeführten bzw. geplanten Tests.
- g) Falls von der Testempfehlung abgewichen wird, so sollten diese Abweichungen vom Bauelementehersteller angezeigt und kommentiert werden. Hierzu ist der Bereich "Reason for exception of tests" zu verwenden. Werden die in Betracht zu ziehenden Tests durch generische Daten (G) belegt, ist dies ebenfalls hier anzuzeigen und zu begründen.

Die Einstufung des Untersuchungslevel erfolgt in folgende Kategorien

- "C: Component level": Die Evaluierung der Änderung am Bauelement ist durch Untersuchungen ausschließlich am Bauelement beim Bauelementehersteller durchführbar. Zur Evaluierung der Änderung dürfen Ergebnisse aus bereits durchgeführten Untersuchungen herangezogen werden wenn diese zu einem ähnlichen Bauelement bereits vorliegen (Generische Daten)
- "B: Board level": Die beschriebene Änderung hat möglicherweise Finfluss auf die Verarbeitbarkeit des Bauelementes im Steuergerät. Die Evaluierung der Änderung wird wie unter C beim Bauelementehersteller durchgeführt. Zusätzlich ist durch den Kunden/Steuergerätehersteller die Verarbeitbarkeit zu prüfen, die z.B. abhängig von der Änderung, Zuverlässigkeitsuntersuchungen auf applikationsrelevanten Testbords erfordert.
- "A: Application level": Die beschriebene Änderung hat möglicherweise Einfluss auf die Applikation/ das Steuergerät. Die Evaluierung der Änderung wird wie unter C oder B durchgeführt. Zusätzlich ist vom Kunden/Steuergerätehersteller der Einfluss der Änderung im Steuergerät durch geeignete Untersuchungen zu bewerten. Dieses Vorgehen ist mit dem OEM abzustimmen. Hierbei ist zu berücksichtigen, ob die Steuergeräte- / Baugruppenanforderungen durch andere Qualifikationen bereits hinreichend abgesichert sind (applikationsspezifische Risikobetrachtung).
- " *: Not relevant for qualification matrix": Änderung(en), die nicht in A, B oder C eingestuft werden können und somit nicht relevant für die DeQuMa sind

Infomation Notes

Änderungen die nur eine Information Note benötigen (bei der Bewertung Risk on Supply Chain als "I" gekennzeichnet), dürfen nicht in der DeQuMa angekreuzt werden, da Sie ansonsten den erforderlichen Evaluierungslevel verfälschen. Für als "I" bewertete Änderungen ist das Information Note Formblatt zu

Wichtige Hinweise

- Zur formgerechten Anwendung der DeltaQualifikationsMatrizen steht auf der Homepage des ZVEI AK ein Tutorial bereit (ZVEI-Tutorial).
- ID Nummer: ist eine eindeutige Identifikationsnummer für jede angegebene Änderung, die in den ZVEI PCN DeltaQualifikatiosMatrizen identifiziert ist. Die gleiche ID Nummer wird zur Identifizierung der Änderung im PCN Form Sheet verwendet.
- Die mittels Matrix identifizierten Tests sind in Betracht zu ziehen, d.h. es ist zu pr
 üfen, ob der ieweilige Test für die spezifische Änderung in dieser Form notwendig ist. Abweichungen ode generische Daten sind im Detail zu begründen.
- Die Spalte "Further applicable conditions". Bemerkungen und Fußnoten sind unbedingt zu beachten, da sie wichtige Hinweise und Einschränkungen enthalten.
- Zur Nutzung aller Funktionen muss in Excel die Anwendung von Makros freigegeben sein

Form provided by ZVEI - Revision 4.1 - November 2019

DeltaQualificationMatrix

General Kurze Produkt- und Technologiezyklen elektronischer Bauelemente sowie neue Umweltauflagen führen häufig zu Short product and technology cycles as well as new environmental regulations frequently result in process and material changes of components, printed circuit boards, assembly techniques and circuit layout which have to be evaluated. The ZVEI "Guideline for Customer Notifications of Product and /or Process Changes (PCN) of Electronic Components specified for Automotive Applications" describes an appropriate methodology for dealing with changed electronic components. The gualification matrices in this guideline are recommendations for how to assess typical changes of electronic components. These recommendations promote an open risk-based discussion between supplier and customer regarding qualifications

> The DeltaQualificationMatrices were developed by the Industry Task Force Team "PCN DeltaQualificationMatrix" together with component experts from the ZVEI Working Group "PCN-Methodology", Actual content represents state-of-the-art technology and does not claim to be comprehensive. Deviation from proposed guideline should be mutually agreed as customer specific requirements have to be considered

DeltaQualificationMatrix Application (completion by component manufacturer)

- a) This table has to be used for changes only. The matrices are not applicable for new product. special qualifications (for instance for encapsulation of module) or Information Notes. b) If a change is not listed in this table, the qualification plan has to be defined and agreed
- between customer and supplier. c) The matrix for Active Components requires the user to choose between integrated circuits
- (AEC-Q100 Rev. H) and discrete semiconductors (AEC-Q101 Rev. D1) (cell D4) For Passive Components AEC-Q200 is used. For LED'S the AEC-Q102 is used For Multi-Chin-Modules the AEC-O104 is used
- d) All changes as listed in the PCN have to be marked, by a cross (x) in column B and will appear colored. The relevant reliability tests are then shown in "Tests, which should be considered for the appropriate process change".
- e) In "Tests, which should be considered for the appropriate process change after selection of condition table" is for modification of the found relevant tests under consideration of the weight of change
- Related table "Conditions" has to be assessed per proposed letters with an (x). f) In "Suppliers performed tests" the component manufacturer documents the planned and performed tests
- g) In case of deviations from tests, which should be considered this should be notified and commented by the component manufacturer in the area "Reason for exception of tests". Test results in form of generic data (G) are allowed when notified and justified.

Evaluation Levels are categorized as follows

- "C: Component level": The evaluation of a change at component level by the component manufacturer is sufficient. Generic data from other relevant evaluations can be used.
- "B: Board level": The intended change described in the PCN may influence processability / manufacturability of the component at hoard level. Therefore additional evaluation by customer may be necessary, for example reliability tests on application relevant testboards depending on change
- "A: Application level": The intended change described in the PCN may influence the properties of the application (e.g. Electronic Control Unit). In addition to the evaluation under C or B the influence of the change in the application is evaluated by suitable investigations by the customer. The scope of the evaluation has to be aligned with the OEM. It has to be considered whether the application / assembly requirements are already sufficiently safeguarded by other qualifications (application specific risk assessment).
- " *: Not relevant for qualification matrix": Changes which fulfill neither A,B nor C definitions

Infomation Notes

Changes indicated as "I" shall not be marked in the DeQuMa. For those changes the Information Note sheet shall be used. As the DeQuMa is desired for PCN only, a marking of "I"-changes would automatically influence evaluation level and test effort.

Important Notes

- To use the matrices in the right form the ZVEI working group provides a Tutorial on its homepage (7VEI-Tutorial)
- ID number: is a unique identification number for each indicated change defined in the ZVEI PCN DeltaQualificationMatrices. The same ID number is used in the PCN Form sheet to identify the change
- Tests identified by the matrix have to be considered and checked if they are necessary to assess the specific change. Test modifications or generic data have to be justified in detail.
- "Further applicable conditions", comments and notes need attention, as they provide important
- hints and limitations.
- In order to use all functions in EXCEL, macros have to be allowed

Worked on: (Name, Function)		Form provided by ZVE1 - Revision 4.1 - 1	iovember 2019																								
	2/06/2020																										
PCN number: p	PCN 20_0171														e evalua												
Signature:											MAT	ERIAL PERF	ORMANCE	TEST RES	ULTS (on t	he basis of a	AEC-Q200 F	levision D)							additional to A Q200	AEC-	
change			1	Evaluation lovel A/B/C	n sile chocky																				(10008	inbation	
	ssessmern of impact on Stupply Chain regarding following aspects R contractual agreements -schriezi andress of processabilitymenufacturability of customer -term, R, function, quality performance, reliability	emaining Ja within Supphy Understanding of component Chain? experts	Examples to explain	Further applicable conditions	olastion e estuated by dan or estro - Q200 Revision D or spatiestion entend only	High Temp Exposure (Storage	Tarpendue Cycling Destructive Physical Analysis	Moleure Roal dance Biesed Hunt day	Operational Life Ecolemati Visual	Proyated Dimension Terrainal Breesth (Landed)	Resistance to Schwerts	Mechanical Shack Vibration	Resistance to Soldering Heat	Thermal Shook Electronizatic Discharge (1550)	Soldwold By Electrical Chemican Landon	Florer of Ry	scarotrok Taménal Breegh (SAD)	Bears Load Test Flame Relardance	Rozadon Life	Surge Vidtage Sait Spray	Electrical Transient Conductio	Sheer Strength Fault Ourses Durability	Erd-d-LFe/Kode Verification	Arrip Start Endurance Load Durrp Endurance	Wit Her Text 0EC 60085 T2-82, JEDEC JE Parameter-Analysis	companiant or current with of the current of the	Remarks
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NORKS & RESISTORS	IETWORKS & RESISTORS		-1	1 1			_			r - 1																	
	ny change with impact on agreed upon technical contractual agreements	P Intended to be used if no other type of change is applicable but the change affects agreed technical contraction assessments		•	<u>.</u>																				· · ·	-	
BIS & RESISTORS			Technical interface means component terminals.	8			<u>·</u> ·																		@•		
PAS-RES-DS-01 0	hange of datasheet parameters/electrical specification (min./max./kp. values) and / or ACIDC secification	P Change of application relevant information Not included: Editorial changes.	e.g. tighten of electrical parameter distribution	A Risk assessment depending on change for each application.	<u>.</u>		· ·														•			1.	•	-	
PAS-RES-DS-02 Co	ALAGENT og of fabbielspennetenskelskol geoficien (miniselyp, vaker) ed / or ACOC of the analysis of the second sec			*	•																			• •		-	
PAS-RES-DS-CO Sp	pecification of additional parameters	Description of a new not previously covered parameter. P B technical change of the product. (b; no influence mathematical states of the product of the parameters of the product of the product of the mathematical states of the product of the product of the mathematical parameters (stat. evaluation)	n.g. adding new (issiled) perameter. for	A																							
	ATERIAL hange of material composition - ink/Wire material of Resistor element		e.g. resistor paste, NCr, resistor wire	c		•	•		• •	- v	v .			• F	- B	1.1		• R	1.1						- 6	Q	
		P Change of Ink / Wire material	e.g. AgPd paste, Ag paste, lead wire , NCr for side termination	8			•		•	. v				F	. в			- R							-	s• 8•	
IRIOS & RESISTORS	hange of material composition - Package/ Mold	P Change of Package	e.g. for chip res.: Tinal coaling, epoxy	в		•	•	•••		• •	• •			• •		•		• R								- Check	whether AOI at tier 1 car ad.
	hange of material composition - Passivation	P Change of Passivation /inner protection P P Change of substrate material	e.g. change of glass	с с		•	•	· ·			-		•	•	• •	•	• •	• R		- N						g•	
	hange of material composition - Substrate material hange of supplier of material	 P Change of substrate material Change to a new or additional material suppli- at component manufacturer. 	er e.g. for 2nd source purpose	c				•		•				• •		•		• R		- N							ption material specifical as unchanged. Otherwis
ROG & RESISTORS	ESIGN																			-					I	crange	.cf material.
ROS & RESISTORS PAS-RES-DE-02 O	hanges of termination, surface finish, shape, color, appearance or dimension structure hanges of Inner construction - Passialistics ROCESS	P Charge of package P Charge of passivationTrimer protection	e.g. change of glass, laquer, epoxy,	B C			<u> </u>	• •	•									- R		- N							
	ROLLAS	P Change of ink fire process	e.g. change of firing profile e.g. change from normal almospher to nitrogen atmospher	c			•		•	- F	ε.				- в										- 6	9•	
ING A RESISTORS PAS-RES-PR-02 C	hanges in process technology or manufacturing methods - Ink Print	P Charge of ink print process		c	•	•	•		•	- F	ε				- В		R R								- @	Q•	-
CS & RESISTORS PAS-RES-PR-04 O	hanges in process technology or manufacturing methods - Laad Form	P Charge of Irim process P Charge of lead form process	e.g. change from mill trimming to baser trimming e.g. change from bending to punching	8				•		•					. В • В					N						Q•	
IS & RESISTORS	hanges in process technology or manufacturing methods - Termination Attach	P Charge of termination attach process P Charge of marking process	e.g. chip resistors: electroplating process e.g. welding of leads for through put devices.	8	•			· •		• •			•		- в					- N						8•	
INS & RESISTORS PAS-RES-PR-07 C	hangas in process lechnology or manufacturing methods - Marking hangas in process lechnology or manufacturing methods - Molding	P Change of making process P Change of molding process P Variation within process specification.	e.g. change from tampon printing to laser marking	8 C		•		• •				•		• •		<u>++</u>										-	
S & RESISTORS	ACKING / SHIPPING - NEW MATERIAL, CRITICAL DIMENSIONS		e.g. process control																							-	
	acking / shipping specification change (lossening of tolerances)	P P Change of packing specification.	e.g. number of pieces on reel. e.g. change of MSL e.g. change in dry pack assurance (HIC, MBB)	8																							
IS & RESISTORS		P Charge of carrier	e.g. change in dry pack assurance (HC, Mass) e.g. change by material e.g. change by geometry.	в																							
	ACKING / SHIPPING - VISUAL INSPECTION	P Charge of labeling, also on reel.	() e.g. additional information (RoHS stamp) (P) e.g. change of customer specific information	8			+					_			<u> </u>	+ +		<u> </u>						<u> </u>	=		
KS & RESISTORS			(P) e.g. change of customer specific information e.g. change of content of marking e.g. change of method of marking			-																	-		——		
IS & RESISTORS		P Marking on device.		в																					<u> </u>		_
PAS-RES-PV-03 O	hange of packing/shipping specification	P P Change in packing specification which does not described a change of dimensions or material of the packing.	e.g. change of documentation in packing specification	•			· ·					1.					•								نے لئے	•	
PAS-RES-EQ-01 Pr	DOBSTICS / CAPACITY / TESTING - EDUPMEMENT roduction from a new exploymentified which uses a different inclinology or which due to its unique mice function can be expected to influence the inegrity of the final product	Drange in process technique which is not almady covered above. Note: Changes affecting the product not covered by the table require also a PCN.	s.g. new equipment supplier with different process concept	c	• • •	•	•	•	•					• •	- в	•									- 6	Perform process	flort depends on final s sment. mance least according as change.
PAS-RES-80-02 Pr	roduction from a new equipment/bol which uses the same basic technology (replacement pipment or extension of existing equipment pool)	PCN required for dedicated equipment for aenative component production.	e.g. additional equipment to increase production capacity e.g. replacement of same equipment	c	• • •		•	•	•	· · ·		· ·		• •	- в			1.1						· ·	- @	• Text off accord	flort depends on final ri sment. Performance ter ding to affected proces
PAS-RES-ED-03	hange in final test equipment type that uses a different technology	P P Change of final text equipment which use different technology. PCN required for dedicated equipment for technical parameters.	e.g. change of tester platform	c	•	-	· ·				-				· @8	3 -			•						- 6		R&R / delta correlation
PAS-RES.PT-01 MA	DOGSTICS / CAPACITY / TESTING - PROCESS FLOW Invlaching alls transfer or movement of a part of production process to a different location/site	P P Change of manufacturing site. Includes transfer as well as additional site. Note: Recognization inside one plantituite is not affected	e.g. movement or transfer of manufacturing site or process step(s) to a different location/site. e.g. dual source / tab strategy	8	• • •	•	•	•••	• •		• • •		•	• •	- в	1.	• •	• R		- N					@• @	8•	
CS & RESISTORS PAS-RES-PF-42 EX	inination or addison of a manufacturing process step	P Change of manufacturing process sequence	e.g. dual source / fab strategy e.g. veshing / cleaning process e.g. change of order of processes	c			· ·	· ·		•			•		· @8	3 -			•		•		•		- @	0 Otarac product	cterisation depends on ction flow.
PAS-RES-QG-01	DOBTIGE (LARACTLY TESTING - G-GATE Narge of test contrage, used by the supplier to impute data sheet compliance (e.g., or instantic contract one of a contract processing and contract on analysis) EXECUTORS	. P Charge of test coverage.	e.g. change from 100% to sample inspection e.g. test flow block, reduction from three to two temperature measurements e.g. change in burn in traces.	c	• • •	•		•	• •				•			·			•		•		•		·L	R (elec R (rela proces	cir. funct.): test coverag ability) only for change as.
xs //	NY	Intended to be used if no other type of chance	•	1 1		- T						-			-	1 1	_	-	1	-			1 1	-			
PAS-IND-AN-01 Ar	ny change with impact on agreed upon technical contractual agreements I ny change with impact on processability/manufacturability at customer, which is not covered in a matrix holinar.	P P Intended to be used if no other type of change is applicable but the change affects agreed inchoiral contractual assessments	Not relevant for technical evaluation. Technical interface means component terminals.	В																					@•	-	
5 5	ATADREET		recontrat memore means component terminals.																						· · ·		
PAS-IND-OS-01 D	hange of datasheet parameters/ielectrical specification (min./max/kp. values) and / or ACIDC pecification	P Charge of application relevant information Not included: Editorial charges. No included relation of product, process or	e.g. lighten of electrical parameter distribution	A Risk assessment depending on change for each application.		•	• •	• •		•			•		• •	•			•		-		•		•	-	
PAS-IND-05-02 Co	onnection of data sheet or issue of errate	No technical change of product, process or test. New description of behavior which was not specified ballow or which is different from I while specification. Please indicate clearly, bat infonde containe this type of change! Assessment in application required!	e.g. data sheet correction because of new information about component behavior	A		-					-												-	• •		-	

PAS-IND-DS-03	Specification of additional parameters	I P	Description of a new not previously convert parameter. No inchronic change of the product. (B): no influence (P): Risk assument depending on change for each application to provide evidence of additional parameters (stat. evaluation)	n.g. adding new (lealed) parameter.	A					-															-	-
PAS-IND-MA-01	Diarge of material composition - Bobbin Material	P P	Material without magnetic function ("Spulerkloper") typically made by plastic material	e.g. change from Thermoset to Thermoplastic	в			• • •		•	• @•		• •						-		-				- T	-
PAS-IND-MA-02	Change of material composition - Core Material	P P			A			• • -		· .	•					в •							+	—	+	@•
			ingene ration			• •				-									-		-		<u> </u>	<u> </u>	+	@•
PAS-IND-MA-03				e.g. wire insulation, insulation tepes, e.g. change from Polyurethane to Polyamide	c	· ·	•••	• • •	•		• -	· •		••		в •			•		-		<u> </u>		4 - 4	
PAS-IND-MA-OI	Change of material composition - Lead Material	P P	Change of lead material	e.g. change from tin coverd to non-coverd lead material	в	· ·				•	•	• •	•	• •	•		•••		-		-		· ·		@•	-
PAS-IND-MA-05	Change of material composition - Mold Compound	P P	Change of mold compound material	e.g. change to green mold	в	- •	• •	• •	•••	•	• -	- •	• •	- •		в •			-		-		-		-	@• Electrics mechanic changes board co MSL mp
PAS-IND-MA-06			connector.	e.g. change of SnAgCu composition	в	- •	•	• •		-	•	•	•••	@• •	•		•••		-		-		-		@•	-
PAS-IND-MA-07			Foiltor multilayer inductors (inner electrode).	e.g. change of Cu composition	в	• •	• @	•	••		• -				• -	в -	••		-		-			· ·		@•
PAS-IND-MA-08	Change of material composition - Gue			e.g. change from glue A into glue B	c	· ·	• •	@• ·	· @•	-	@• ·		- @•	@• ·	· @•	@В -			-		-		· ·	· ·	1 - 1	@• Consider the air ga
PAS-IND-MA-09	Change of supplier of material	. P	Change to a new or additional material supplier at component manufacturer.	e.g. for 2nd source purpose	c	- •	•	• •	• @•		• •	• •		· •		в -			-		-		- I I		1 - 1	@• Assumption
PAS-IND-MA-10	Charge of material composition - Poting Material	p p	Change of potting material	e.g. change from epoxy reain to allicon	C A: If influence on other connections on PCB or laquer expected.			@• -	- @•		@• @•		- @•	@• ·	- @•	@В -										@•
	DESIGN			the charge non-spory rear to accur	PCB or laquer expected.		_	6.	6.		8. 8.		6	8.	6.	65							4		╧┷┷┾	@+
PAS-IND-DE-01	Dhanges of termination, surface linish, shape, color, appearance or dimension shucture - Bobbin	I P	Material without magnetic function ("Sputerkörper") typically made by plastic	e.g. construction / dimension change of bobbin	в			• •			• •		• •		• •	в -			-						1.17	@•
PAS-IND-DE-02	Changes of termination, surface finish, shape, color, appearance or dimension shucture -			e.g. change from PTH terminals to SMD terminals	A									• -			•••								@•	
PAS-IND-CE-03	Lead Terrinals Diarges of lermination, surface finish, shape, color, appearance or dimension structure - Mold	I P	Charge of mold	e.g. new mold material with different color	в			• • •	• @•	-	• •					в -			-		-		•			Paramete component magnetic
PAS-IND-DE-04	Changes of Inner construction - Core Construction	. P	Change of core construction, which is material with magnetic function	e.g. change fromdrum core & shield core into pot core & cover plate core	A	• •		• •	· · ·	-	• •		•••	- •		в -			-		-		•			@•
PAS-IND-DE-05	Changes of inner construction - Insulation System		Charge of insulation system	e.g. wire insulation, insulation tapes, e.g. chance from Polyurathana to PTET (Taff	c		- @	•		•	• •			• •	Α -	в •					-		· · /			-
PAS-IND-CE-06	Changes of inner construction - Wite / Foil Construction		Change of wire / foil dimensions	e.g. wire insulation, insulation tapes, s.g. change free Polyarehane to PTPE (Tellon) s.g. change free Polyarehane to PTPE (Tellon) s.g. change free Polyarehane to Ez wire s.g. from single wire to Ez wire	в						• •		· @•			в -										@•
PAS-IND-DE-07	Unanges of inner construction - volte / Foi Construction Changes of termination, surface finish, shape, color, appearance or dimension structure - Polling Material	-																					4	4		
	Charges of termination, surface finish, shape, color, appearance or dimension structure - Poling Material PROCESS	I P	Change of polling dimension	e.g. change of potting (filling) height	C If data sheet is affected (PAS-ND-DS- 01)			@• •	1 • 1 •	1 .	@• @•		· @•	@• ·	• •	@B -	· · ·	• •		· ·	· ·	· · ·	يليك	<u></u>		@•
PAS-IND-PR-01	Changes in process technology or manufacturing methods - Insulation Sirip			e.g. change from mechanical removal to laser removal	в	• •			• .	-	• -	- •		• .	- @•				-		-		-		-	- Mechanic Impact or stripping area.
PAS-IND-PR-02	Changes in process technology or manufacturing methods - Lead Prep. / Plating	. P	Change of lead prep. / plating	e.g. change from hot dip timing to electroplating	в	• •		• •		-	•	•		•••	•		•••		-		-		· · 7		@•	- Influence
PAS-IND-PR-03	Ohanges in process lechnology or manufacturing methods - Terminal Atlach	. P	Connection of wire terminal and / or connection of termination to core/bobbin.	e.g. chanle from Manual winding to Semi-automtic winding (winding of wire on terminal)	c	• •		• •	• @•		•	• •		Α •					-		-				@•	- Increase
PAS-IND-PR-04	Changes in process technology or manufacturing methods - Marking	. P		e.g. change from ink marking to baser marking	8						•										-					-
PAS-IND-PR-05		- P	Charge of molding process	e.g. change from one component molding to two component molding (other technology needed)		• •		• • •	- •	•	• •	· · ·	• •	- •		в •					-					-
PAS-IND-PR-06	Changes in process technology or manufacturing methods - Soldering Internal Connections	- P	Charge of soldering internal connection		в	• •	- C	• •		-	•	• •	•	•	•		• •		-		-	÷ -	· .		-	-
PAS-IND-PR-07	Changes in process technology or manufacturing methods - Winding Insulation	- P	Change of winding - insulation	e.g. change from manual to automatic process	в	•		• • •						• •					-		-					-
PAS-IND-PR-08	Changes in process technology or manufacturing methods - Winding Wire	- P	Change of winding - wine	e.g. change from semi-automatic winding to full automatic winding	c	• •		• • •		•						в -			-		-	· ·	4-1-		-	@•
PAS-IND-PR-09	Process integrity: tuning within specification	- P	Variation within process specification.	e.g. process conitrol	c	1.0			· ·	- I			· ·	· ·				• •	-		-		434		4-1-	-
PAS-IND-PR-10	Changes is process technology or manufacturing methods - Poling PACKING / SHEPPING - NEW MATERIAL, CRITICAL DIMENSIONS	- P	Change of potting process	e.g. change from manual potting process to automatic potting process	c		•	@• -	· @•	1 - 1	@• @•	· ·		1 · 1 ·		· ·	· · ·	• •	· · ·	• •	-	• •		• •		-
PAS-IND-PN-01		P P	Charge of packing specification.	e.g. number of pieces on real.	в									· ·		· · ·			· · ·						1.1	-
PAS-IND-PN-02				e.g. change of MSL e.g. change in dry pack assurance (HIC, MBB)	в					1.1																
PAS-IND-PN-03							-																+	_	+++	
	Change of carrier (tay, ree) PACKING / SHEPPING - VISUAL INSPECTION	PP	Change of carrier	e.g. change by material e.g. change by geometry.	в								1 1 1										للغل	<u>. </u>	للغله	-
PAS-IND-PV-01		I P	Charge of labelling, also on reel.	(i) e.g. additional information (RoHS stamp) (P) e.g. change of customer specific information	в																				1.17	-
PAS-IND-PV-02	Change of product marking			e.g. change of content of marking e.g. change of method of marking	в																					
				e.g. change of appearance of marking																				-		
PAS-IND-PV-03	Change of packing/httpping specification LOGISTICS / CAPACITY / TESTING - EQUIPMEMENT		Change in packing specification which does not described a change of dimensions or material of the packing.	e.g. crange of documentation in packing specification	•	· ·	•	· ·			• •			· ·	• •		• •	•	· ·	•					ļ	-
PAS-IND-ED-01	Production from a new equipmentition which uses a different technology or which due to its unique form or function can be expected to influence the integrity of the final product	P P	Change in process technique which is not sheady covered above. Note: Changes affecting the product not covered by the table require also a PCN.	e.g. introduction of potting process	c	•	- ·			•						@в -		• •	-		-		•	· ·	•	@• Test effort sasessmer Performan process ch
PAS-IND-ED-02	Production from a new equipment/lool which uses the same basic technology (replacement equipment or extension of existing equipment pool)	. P	PCN required for dedicated equipment for sensitive component production.	e.g. duplication of existing winding machine	c	•	•			•									-		-		•		·	@• Test effort assessmen Performan process ch
PAS-IND-EQ-03	Change in Tinal test equipment type that uses a different technology LOGISTICS / CAPACITY / TESTING - PROCESS FLOW	P P	Change of final last equipment which use different technology. PCN required for dedicated equipment for senalities parameters.	e.g. change of tester platform	c	•	-			•						@В -			-		-		•	• •	$ \cdot $	@• Gage R&R
PAS-IND-PF-01		р р	Charge of manufacturing sile. Includes transfer as well as additional sile. Note: Reorganization inside one plantibile is	e.g. movement or transfer of manufacturing alle or process skep(s) to a different location/site.	в	• •		• • •	• @•	•	@• -	• .		•••		в -			-		-				@•	@•
PAS-IND-PT-02	Elimination or addition of a manufacturing process step		not alleriade too	e.e. dual access / fab strategy e.g. washing / cleaning process	c																					@• Characteri production
PAS-IND-PT-02 PAS-IND-PT-03	Elimination or addition of a manufacturing process step	. P	Change of manufacturing process sequence. Reduction of final testing. PCM required for dedicated final test reductions for sensitive parameters.	e.g. vashing / cleaning process e.g. change of order of processes e.g. elimination of High-voltage measurement	c																					e production Characteri final text fit
•	LOGISTICS / CAPACITY / TESTING - Q-GATE	<u> </u>	•																				+	+		
PAS-IND-QG-01	Charge of text coverage used by the supplier to amore data thest compliance (e.g., alimitation) data or of electrical measurementhat flow block, relaxation/enhancement of monitoring procedure or sampling CEERANKC / TANTALUM and	. Р	Change of test coverage.	e.g. change from 100% to sample inspection e.g. ptat flow block, reduction from three to two temperature measurements e.g. change in burn in/run in process.	c						• •													1		- R (electr. f R (reliabilit process.
PAS-CER-AN-01	ANY Any change with impact on agreed upon technical contractual agreements	P P	Intended to be used if no other type of change is applicable but the change affects agreed technical contects of assessments	Not relevant for technical evaluation.	•																				TIL	
PAS-CER-AN-02	Any change with impact on processability/manufacturability at customer, which is not covered in the methods	P P	terbeind coster-keil ansamerte	Technical Interface means component terminals.	в																				@•	
	DATASHEET																			-					Ť	
PAS-CER-OS-01	Ohange of datasheet parameters/electrical specification (min/max/kp. values) and / or AG/DC specification	P P	Change of application relevant information Not included: Ecitorial changes.	e.g. lighten of electrical parameter distribution	A Risk assessment depending on change for each application.	· ·	•			•									•		•		·			-
PAS-CER-OS-02	Connection of data sheet or issue of errate	1 1	Please indicate clearly, that infoncie contains this type of change! Assessment in application required!	e.g. data abeet correction because of new information about component behavior	A					-											-					-
PAS-CER-DS-03	Sectication of additional serventers	I P	Description of a new not previously covered parameter. No technical change of the product. (f):: no influence (P): Raik assessment depending on change for each application to provide evidences of additional parameters (tata: evaluation)	e.g. adding new (lealed) parameter.	A																					

,																
CERAMIC / TANTALUM CERAMIC / TANTALUM	PAS-CER-MA-01	MATERIAL Drange of material composition - Geramic Binder	P P	Binder material (ceramic)	1	c	• •		• • • • •							
CERAMIC / TANTALUM CERAMIC / TANTALUM	PAS-CER-MA-02 PAS-CER-MA-03	Chanos of material composition - Tartalum Binder Change of material composition - Dielectric	P P	Binder material (ceramic) Binder material (berbal) Dielectric change (ceramic only)	e.o. chance from wax 1 to wax 2	c c	• •		• • • B							
	PAS-CER-MA-04	Charge of material composition - Electrode Attach	P P	Dielectric change (ceramic only) Electrode attach (only tantal, glue, carbon, Ag)	e.g. change of Ag particle size in conductive	c		· · · · · · · · · · · · · · · · · · ·								
CERAMIC / TANTALUM		Change of material composition - Electrode Material	P P	Electrode Material (only cetamic, inner	e.g. change from spehric to fake shape (N paste)	c										
CERAMIC / TANTALUM	PAS-CER-MA-06	Change of material composition - Encapsulation	P P	Encapsulation	e.g. change from epoxy1 into epoxy2	c	• • •	•••••••••••••••••••••••••••••••••••••••								Check whether AOI at Tier 1 can be attented
CERAMIC / TANTALUM	PAS-CER-MA-07	Change of material composition - Lead material / Termination	P P	Lead material / Termination	e.o. change from SrPb to pure Sn	c	• •		- • B -							
CERAMIC / TANTALUM	PAS-CER-MA-08	Change of supplier of material	- P	Change to a new or additional material supplier at component manufacturer.	e.g. for 2nd source purpose	c		• • • · · • • • • •	• • • в - •	• c •		- A. (1997)			. @•	Assumption material specification remains unchanged. Otherwise see
CERAMIC / TANTALUM CERAMIC / TANTALUM		DESIGN				↓ ↓						1 1				Ichanos of material.
CERAMIC / TANTALUM	PAS-CER-DE-01	Changes of termination, surface finish, shape, color, appearance or dimension situcture - Lead Diameter	I P	Lead dameter	e.g. change from 0.8mm into 0.6mm	в	· · · · ·					- A. (1997)				
	PAS-CER-OE-02	Changes of lermination, surface finish, shape, color, appearance or dimension structure -		Termination area	e.g. change in width of termination from 0.1 -0.3mm into 0.2 - 0.4 mm	в		• • • • • • • • • • •		• • • •						
CERAMC / TANTALUM	PAS-CER-DE-03	Damelar Dianges of testination, surface links, shape, color, appearance or dimension structure - fummation Area Dianges of testination, surface links, shape, color, appearance or dimension structure - testination before the structure of the str		Terminal intertace	into 0.2 - 0.4 mm e.g. additional layer in termination	8			B -							
CERAMC / TANTALUM CERAMC / TANTALUM	PAS-CER-DE-04	Tantination Interface. Changes of Inner construction - Electrode Thickness	. P	Electrode Prickness (cenamic only)	e.g. N layer charge from 2.5µm into 3.5µm	c		· · · · · · · · · · · · ·	• • B •							
CERAMC / TANTALUM	PAS-CER-DE-05	Changes of inner construction - Layer Thickness	- P	Layer thickness (delectric thickness)	e.g. Ceramic layer thickness changes from 3µm into 5µm.	c	· • · · · ·	· · · · · · · · · · · · · · · · · · ·	• • - в	- c -				 • 		
	PAS-CER-DE-05	Changes of inner construction - Number of Layers		Number of layers (ceramic only). Always in combination with PAS-CER-DE-05.	see also layer thickness	с			СС- В,С-	- c -			1.1.1			
CERAMIC / TANTALUM CERAMIC / TANTALUM		PROCESS		combination with PAS-CER-DE-05.		5										
CERAMIC / TANTALUM	PAS-CER-PR-01	Danass is process lechnology or manufacturing methods - Dicing	- P		e.g. change from cutting to sawing	c	• • •		B -	· C ·						
CERAMIC / TANTALUM	PAS-CER-PR-02	Changes in process technology or manufacturing methods - Electrode apply	- P	Electrode apply (dielectric layer process)	e.g. change from wet to dry process	c	• • •	- c c c	C C - B,C - 0			1.1		· · ·	· ·	
	PAS-CER-PR-03	Changes in process lechnology or manufacturing methods - Firing	. P		e.g. seperation of decarbonization and firing profile.	c	•		• • - B - ·	- C -	1. A.	1. A.				
CERAMIC / TANTALUM CERAMIC / TANTALUM	PAS-CER-PR-04	Changes in process technology or manufacturing methods - Lamination		Change of lamination / press techinque	e.g. standard pressing to iso static pressing.	c	• •	· · · · · · · · · · · ·								
CERAMIC / TANTALIM	PAS-CER-PR-05	Changes in process technology or manufacturing methods - Particle Size	- P	Change of powder particle size. Always in combination with PAS-CER-MA-03.	e.g. change DS0 from 0.5µm into 0.4µm	c	• • •	· · · · · · · · · · · · · · · ·	• • в •			1.1		· · ·	· ·	
CERAMIC / TANTALUM	PAS-CER-PR-06	Changes in process technology or manufacturing methods - Screening Printing		Change of screening / printing	e.g. change from screen printing into offset printing	c	• • •	· · · · · · · · · · · ·	- C - B,C -	- c -						
CERMIC / IANIALDRI	PAS-CER-PR-07	Changes in process technology or manufacturing methods - Termination		Change for termination preparation like plating or apply of termination base layer.	e.g. change in plating technology (final termination) e.g. change from dip in paste to plating (apply)	в	• • •	• • • • • • • • • • • •		• • • •						
CERAMIC / TANTALUM	PAPERFINI		- P	or apply of termination base layer.			•									
CERAMIC / TANTALUM CERAMIC / TANTALUM	PRO-CEN-PR-08	Process integrity: tuning within specification PACKING / SHIPPING - NEW MATERIAL, CRITICAL DMENSIONS			e.g. process control	c				1 - 1 - 1 -						
CERAMIC / TANTALUM	PAS-CER-PN-01	Packing / shipping specification change (lossening of tolerances)	P P	Charge of packing specification.	e.g. number of pieces on reel.	в										
	PAS-CER-PN-02	Dry pack requirements change		Charge of drypack requirements.	e.g. change of MSL e.g. change in dry pack assurance (HIC, MBB)	в										
CERAMIC / TANTALUM															_	
CERAMIC / TANTALUM CERAMIC / TANTALUM	PAS-CER-PN-03	Change of carrier (tray, ree)	P P	Charge of carrier	e.g. change by material e.g. change by geometry.	в						1.1	1.1			
CERAMIC / TANTALUM		PACKING / SHIPPING - VISUAL INSPECTION		1						1 1 1			1 1		1	
CERAMC / TANTALUM	PAS-CER-PV-01	Change of labeling		Change of labelling, also on reel.	(i) e.g. additional information (RoHG stemp) (P) e.g. change of customer specific information	в							1 1			
CERAMIC / TANTALIM	PAS-CER-PV-02	Change of product marking	I P	Marking on device.	e.g. change of content of marking e.g. change of method of marking e.g. change of appearance of marking	в	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1									
GERMING / GANTALIUM	PAS-CER-PV-03			Change in packing specification which does												
CERAMIC / TANTALUM		Change of packing shipping specification	PP	Change in packing specification which does not described a change of dimensions or material of the packing.	e.g. change of documentation in packing specification			<u> </u>					1.1			
CERAMC / TANTALUM	_	LOGISTICS / CAPACITY / TESTING - EQUIPMEMENT											1		-	
	PAS-CER-ED-01	Production from a new equipmentitool which uses a different technology or which due to its unique form or function can be expected to influence the integrity of the final product	p p	Change in process technique which is not already covered above. Note: Changes affecting the product not covered by the table require also a PCN.	e.g. change from wet to dry technology.	c			в .	- c -					- @•	Test effort depends on final risk assessment. Performance test according to affected
CERAMIC / TANTALIM		form or function can be expected to influence the integrity of the final product		Note: Changes affecting the product not covered by the table require also a PCN.		-										Performance test according to affected process change.
CENNEC/ INTIGEN	PAS-CER-ED-02	Participation from a supervision of the later to supervise the state of the supervised state of the su						• • • · · · · · · · ·	в							Test effort depends on final risk
CERAMC / TANTALIM	PAS-CER-EQ-02	Production from a new equipmentitool which uses the same basic technology (replacement equipment or extension of existing equipment pool)	- P	PCN required for dedicated equipment for sensitive component production.	e.g. elimination of manual handling processes	c	• •	•••••••	• • в -	- c -					- @•	assessment. Performance test according to affected process change.
CEMMC/ MUDEUM				Change of final lest equipment which use different technology. PCN required for descated equipment for sensitive parameters.												
	PAS-CER-EQ-03	Change in final test equipment type that uses a different technology	P P	different technology. PCN required for dedicated equipment for	e.g. change of tester platform	c	 • 1 (1) 		· · · @B - ·						- @•	Gage R&R / delta correlation
CERAMC / TANTALUM CERAMC / TANTALUM		LOGISTICS / CAPACITY / TESTING - PROCESS FLOW		sensore parameters.												
	PAS-CER-PF-01	Manufacturing site transfer or movement of a part of production process to a different location/site		Change of manufacturing site. Includes transfer as well as additional site. Note: Reorganization inside one plantitite is not affected	e.g. movement or transfer of manufacturing site or process step(s) to a different location/site.	в			• • в							
CERAMC / TANTALUM	PAPERFICI	senuraciuming are stander or moviment of a part of production process to a dimensit location are	P P	Note: Reorganization inside one plantitite is not affected	e.g. dual source / fab strategy	•	· ·		• • • • •							
	PAS-CER-PF-02	Elimination or addition of a manufacturing process step	- P	Change of manufacturing process sequence.	e.g. washing / cleaning process	c	· · · · ·								- @•	Characterisation depends on impact of
CERAMIC / TANTALIJM	PAS-CER-PF-02	Elimination or addition of a manufacturing process step	- P	Charge of manufacturing process sequence.	e.g. washing / cleaning process e.g. change of order of processes	c	• • •								- @•	Characterisation depends on impact of production flow.
		LOGISTICS / CAPACITY / TESTING - Q-GATE	. Р	Charge of manufacturing process sequence.			• • •			· · ·					. @•	
CERAMIC / TANTALIJM	PAS-CER-PF-02 PAS-CER-QG-01		. р	Change of manufacturing process sequence. Change of test coverage.		c	• • • •	· ·	· · · · · ·		· · ·	· ·	· ·	 	· @•	Characterination depends on impact of production flow. R (electr. funct.): text coverage. R (velocity) only for change in burn in process.
CERAMIC / TANTALIJM		LOGISTICS / CAPACITY / TESTING - Q-GATE Durgs of test coarings used by the suppler to ensure data sheet compliance (e.g., elimitation/addition of electrical measurement/test flow block, relaxed/or/enhancement of monitoring processing or a sumpling)	. Р	Change of manufacturing process sequence.	 a, while / clambe process a, change if order of processes a, change item 100% to sample inspection a, g tell flow block, reduction from three to two temperature massurements. a, change in two inhum is process. 		• • •	· · <td>· · · · · ·</td> <td>· · · ·</td> <td>· · · ·</td> <td>· ·</td> <td>· ·</td> <td>· ·</td> <td>· @•</td> <td></td>	· · · · · ·	· · · ·	· · · ·	· ·	· ·	· ·	· @•	
CERAMC / TANTALUM	PAS-CER-QS-01	LOGISTICS / CAPACITY / TESTING - 0-GATE Chorpo Hai convego and Ly na capitar is amain data sheet compliance (r.g., restandarization ad device fram angelar is amain data sheet compliance in (r.g., restandarization ad device fram angelar is amain and the block, valuation/infra-center of restandarization angelar is angelar in (r.g., restandarization) FLIM CAPACITORS ANY	. Р	Charge of last coverage.	e.g. change from 500% to sample inspection e.g. (at Row block, eduction from three to two temporature measurement), e.g. change in burn is hun is process.	c	• • •				· · · ·	· ·	· ·	· ·	- @•	
CERAMC / TANTALUM	PAS-CER-QG-01	LOSTICS / CARACTLY TESTING - G-GATE Compared and comparison of the insume data that compares in a distribution of the data data data data data data data dat		Change of test coverage.	eg, change from 100% to sample inspection e.g. test flow block, reduction from three to how e.g. change in barn hinte in process. Rel release for technical evaluation.	c .					· · · ·	· ·	· ·	· ·	· ·	
CERNAIC / TANTALIM CERNAIC / TANTALIM Film capacitos Film capacitos Film capacitos	PAS-CER-QG-01 PAS-FLM-AN-01	LOSTICI LORADITY ISTING - GANT Comparison provide the first sector set on performance is a sector provide and the sector set of the sector provide istication (FAL OPERATIONS FILST CONTRACTORS Filst Sector (Sector Sector S	. Р . Р Р Р	Change of test coverage.	e.g. change from 500% to sample inspection e.g. (at Row block, eduction from three to two temporature measurement), e.g. change in burn is hun is process.	c				· · · ·	· ·	· ·	· ·	- @•	
CERAMC / TANTALUM	PAS-CER-QG-01 PAS-FLM-AN-01 PAS-FLM-AN-02	(destrict)(devery intrine - g.deff Chego of the compare the two-side abut complexes (s), means a second s	P P	Dange of lest coverage.	Age, change harn 50% in sample inspection a g and free block, deduction have to lead more than the block deduction have to lead more than the process. Point released for lactical evaluation. Technical indexteam mana composed terminals.	C							· · ·	· ·	· ·	
CERNAIC / TANTALIM CERNAIC / TANTALIM Film capacitos Film capacitos Film capacitos	PAS-CER-QG-01	LOOPICI (CAROTY) 15116 - GANT Constraints and the first set of the second set of the compression of the comparison of the comparison of the second set of the IFAN CONSTRAINTS of the second set of the Alternative second set of the second	P P	Diarge of text countrys. Diarge of text countrys. Insected to be used if no other type of charge text speed which of more and text speed which of more and executions. Diarge of speciation relevants. Diarge of speciation relevants.	eg, change from 100% to sample inspection e.g. test flow block, reduction from three to how e.g. change in barn hinte in process. Rel release for technical evaluation.	c .		· · <td>. </td> <td>· · · · · · · · · · · · · · · · · · · · · · · · · · ·</td> <td>· · · · · · · · · · · · · · · · · ·</td> <td></td> <td>· · ·</td> <td>· · ·</td> <td>· ·</td> <td></td>	· · · · · · · · · · · · · · · · · · · · · · · · · · ·	· · · · · · · · · · · · · · · · · ·		· · ·	· · ·	· ·	
CERVINC / TUNTALIAN CERVINC / TUNTALIAN CERVINC / TUNTALIAN Film capacitas Film capacitas	PAS-CER-QG-01 PAS-FLM-AN-01 PAS-FLM-AN-02	(destrict)(devery intrine - g.deff Chego of the compare the two-side abut complexes (s), means a second s	P P	Dange of test coverage.	Age, change harn 50% in sample inspection a g and free block, deduction have to lead more than the block deduction have to lead more than the process. Point released for lactical evaluation. Technical indexteam mana composed terminals.	C				· · · · · · · · · · · · · · ·			· · ·	· ·	
CERVINC / TUNTALIAN CERVINC / TUNTALIAN CERVINC / TUNTALIAN Film capacitas Film capacitas	PAS-CERIQG-01 PAS-FLM-AN-01 PAS-FLM-AN-02 PAS-FLM-DS-01	DeadSet Content I Terms - E ADT Compared (an imaginary terms in the same term in t	P P	Dange of test coverage.	es drange hore 102% to antiple trapector a g and tables, relative to the two produces tables, relative to the two produces tables that the two produces the two the two two two Ref releases for two two two two two two Ref releases to two two two two two two Ref relative mans composed two two. 4.5 Optims of electrical parameter distribution	C .		· · <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td>· ·</td> <td></td>							· ·	
CERVINC / TUNTALIAN CERVINC / TUNTALIAN CERVINC / TUNTALIAN Film capacitas Film capacitas	PAS-CER-QG-01 PAS-FLM-AN-01 PAS-FLM-AN-02	(destrict)(devery intrine - g.deff Chego of the compare the two-side abut complexes (s), means a second s	P P	Dange of test coverage.	Age, change harn 50% in sample inspection a g and free block, deduction have to lead more than the block deduction have to lead more than the process. Point released for lactical evaluation. Technical indexteam mana composed terminals.	C	• • • • • • • • • • • • • • • • • • • • • • • • • • •	· · <td>· ·</td> <td>. </td> <td>· · · · · · · · · · · · · · · · · · · ·</td> <td></td> <td>· · ·</td> <td></td> <td>· ·</td> <td></td>	· ·	· · · · · · · · · · · · · · · · · · · ·		· · ·		· ·	
CERVINC / TUNTALIAN CERVINC / TUNTALIAN CERVINC / TUNTALIAN Film capacitas Film capacitas	PAS-CERIQG-01 PAS-FLM-AN-01 PAS-FLM-AN-02 PAS-FLM-DS-01	DeadSet Content I Terms - E ADT Compared (an imaginary terms in the same term in t	P P	Dange of test coverage.	es drange hore 102% to antiple trapector a g and tables, relative to the two produces tables, relative to the two produces tables that the two produces the two the two two two Ref releases for two two two two two two Ref releases to two two two two two two Ref relative mans composed two two. 4.5 Optims of electrical parameter distribution	C .		· ·	· ·		· · · · · · · · · · · · · · · · · · · · · ·		· · ·	@ @	· ·	
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PAS-FLM-DE-06	Changes of inner construction - Insulation System	- P Change of inner insulation to protect winding element against housing.	e.g. change of poting material	с														. в											@•
PAS-FLM-DE-07		P element against housing. P Charge of packaging	(depending of insulation material bickness) e.g. change of dimension or shape e.g. change of surface	в				@•	. 0	3.	· ·	<i>m</i> • <i>m</i> •	- (n. n.	<i>@</i> •				@•										
	Process PROCESS							 				1						_		_								+ +	-
PAS-FLM-PR-01	Changes in process lechnology or manufacturing methods - Package	P Change of reals filling or hardening process (relevant for board types only)	e.g. change in reain filing process (mixing, sequences, poling,) e.g. change in hardening process (temperature, time)	с		•	•	•		•	•	• •	1.1	•		· .		÷			1.1				· .	· · ·			
PAS-FLM-PR-02	Changes in process technology or manufacturing methods - Terminal Attach	- P Change Terminal Attach Process to winding element for bosed and nacked types	e.g. spraying and / or galaanic process, e.g. welding / soldering	c	B: for naked SMD		1.1	•		•	•		•	•				- в		•••	1.1								Consider Solderabil
PAS-FLM-PR-03	Dhanges in process technology or manufacturing methods - Winding	- P Change of winding, flattening or tempering process	e.g. change of tempering temperature	с			•			· @•	•						•	- в											-
PAS-FLM-PR-04	Process integrity: tuning within specification		e.g. process control	с				•					1.1				•	÷		· ·		10 C					1.1	1.1	14 C
PAS-FLM-PN-01	PACKING / SHIPPING - NEW MATERIAL, CRITICAL DIMENSIONS Packing / shipping specification charge (loosening of tolerances)	P P Change of packing specification.	e.g. number of pieces on reel.	в																									
PAS-FLM-PN-02		P P Charge of drypack requirements.	e.g. change of MSL e.g. change in dry pack assurance (HC, MBB)	в																									
PAS-FLM-PN-03							-	-	-		-								-					-				-	-
	Change of carrier (Itay, ree) PACKING / SHEPPING - VISUAL INSPECTION	p p Change of carrier	e.g. change by material e.g. change by geometry.	в		1. A. 1.	1.1						1.1	· ·			1	· ·	· ·										
PAS-FLM-PV-01			L	в							ТТ																		
PAS-FLM-PV-01	Change of labeling	I P Change of labelling, also on reel.	(f) e.g. additional information (RoHS stamp) (P) e.g. change of customer specific information	в			1.1						1.1	· ·		· · ·	1.1	· ·			1.1	1.1					1.1		1
PAS-FLM-PV-02	Change of product marking	I P Marking on device.	e.g. change of content of marking e.g. change of method of marking e.g. change of appearance of marking	в																									
			e.g. change of appearance of marking				_				_															_			
PAS-FLM-PV-03	Change of packing/shipping specification	P P Change in packing specification which does not described a change of dmensions or material of the packing.	e.g. change of documentation in packing specification	•			1.1	1						· ·	1.1		1.1	· ·			1.1	1.1		1.1			1.1	1.1	1
	LOGISTICS / CAPACITY / TESTING - EQUIPEMEMENT									1	1 1				1 1				1 1					1 1					
PAS-FLM-EQ-01	Production from a new equipment/tool which uses a different technology or which due to its unique form or function can be expected to influence the integrity of the final product	P P P Change in process technique which is not already covered above. Note: Changes affecting the product not covered by the table require also a PCN.	e.g. implementation of new machines	с		• • •		•		• @•	•	@• @•	•				•	- в	-	- •									@• Test effort assessme Performan process of
<u> </u>									_																_				Text allow
PAS-FLM-DQ-02	Production from a new equipment/tool which uses the same basic technology (replacement equipment or extension of existing equipment pool)	P PCN required for dedicated equipment for aenative component production.	e.g. extension of existing machine capacity	с		• • •	-	•		• @•	•	@• @•	•		-	- •	•	- в	-	- •	-			-				-	@• Test effort assessme Performe
		Charge of final test equipment which use																											process o
PAS-FLM-EQ-03	Change in final test equipment type that uses a different technology	P P Change of final test equipment which use different technology. PCN required for dedicated equipment for assative parameters.	e.g. change of tester platform	c		•		-	-		-		-		-		-	- @B	-		-			-	•			-	@• Gage RM
	LOGISTICS / CAPACITY / TESTING - PROCESS FLOW																												
PAS-FLM-PF-01	Manufacturing site transfer or movement of a part of production process to a different location/site	P P P Includes transfer as well as additional site. Note: Recognization inside one plantitie is not affected	 e.g. movement or transfer of manufacturing site or process step(s) to a different location/site. e.e. dual energy / bib strategy 	в		• • •	•	•		• •	•	• •	•	• •	•	• •	•	• в	•	• •	1.1		- e - e		· .		1.1	@•	@•
PAS-FLM-PF-02	Elimination or addition of a manufacturing process step	P Change of manufacturing process sequence		с																									@• Character
L	LOGISTICS / CAPACITY / TESTING - Q-GATE		e.g. change of order of processes				_									_													Production
PAS-FLM-QG-01	Drange of test coverage used by the suppler to ensure data sheet compliance (e.g., elimination/addition of electrical measurement/last flow block, relaxation/enhancement of monitoring procedure or sampling)	. P Change of test coverage.	e.g. change from 100% to sample inspection e.g. test flow block, reduction from three to two temperature measurements e.g. change in barn in/um in process.	с																									 R (electr. R (reliabili process.
PART DIPUT		. P Charge of an coverage.	temperature measurements e.g. change in burn in/run in process.	č			1																						process.
<u> </u>	QUARTZ CRYSTAL / SAW																												
PAS-QUA-AN-01	Any change with impact on agreed upon technical contractual agreements	P P Intended to be used if no other type of change is applicable but the change affects agreed	Not relevant for technical evaluation.	•			1.0												-								1.0	-	
PAS-QUA-AN-02	Any change with impact on processability/manufacturability at customer, which is not covered in the metric below.	P P	Technical interface means component terminals.	в																								@•	-
	DATASHEET											-																	
PAS-QUA-OS-01	Drange of datasheet parameters/electrical specification (min./max/lyp. values) and / or ACIDC specification	P P Charge of application relevant information Not included: Editorial charges.	e.g. tighten of electrical parameter distribution	A	Risk assessment depending on change for each application.		1.1						1.1						-								1.1		
		No technical change of product, process or																											
PAS-QUA-OS-02	Connection of data sheet or issue of errats	New description of behavior which was not apecified before or which is different from	e.g. data sheet correction because of new information about component behavior	A																									-
		Please indicate clearly, that infonds contains this type of changel Assessment in application required!																											
PAS-QUA-DS-03	SpecTration of additional promotion	Re technical change of product, process or Non description of behave stucks use of and description of behave stucks use of and description of behave stucks and process forcing a description of the description Process forcing a description, and information Process forcing a description of the product Discription of a second product growth on Process forcing a description of the product Process for the product of the product of the product Process force and the product of the product Process for the product of the product of the product Process force and the product of th	n her e.g. adding new (tested) parameter.	A		· · ·	-																					-	-
PAS-QUA-OS-03		Description of a new not previously covered parameter. Not technical change of the preduct. (P) Fir hold assassment depending on change I wash application is provide edimonal additional parameters (stat. evaluation)	n for a siding new (webs) parameter.	*		· · · ·							•	• •	-													-	-
PAS-QUA-OS-03 PAS-QUA-MA-01	MATERIAL Charge of material composition - Cuerte Black	Description of a new not previously consent parenteries. In Instruction of the product. P PFR Assessment depending on changes and hepicitation to provide evidence of editional parentelies (size, evaluation) P Price and the provide evidence of editional parentelies (size, evaluation) P Price and Samt Samt Samt Samt Samt Samt Samt Samt	ng, adding new (lealed) parameter.	A .									· ·					- B					· ·				· ·	-	
PAS-QUA-05-03 PAS-QUA-MA-01 PAS-QUA-MA-02	MOTERNA. Drange of mainrist composition - Quarte Bank Drange of mainrist composition - Ruane	Description of a new not previously consent permeter. 1 P P Real Assessment depending on chargin and hepication to provide validance of excharge/cathone permeters (pint evaluation) P P A charge of Quarter Titlers is a way rank case. Many for SOV-Titler P P P Danging of the material of the base.	n « g. sóding new (keské) parameter.	A		• • •	-	•	- @	2• •	-	• •	-	• •	• @	2• @•	-		@•	• •	-	· ·	· ·		· ·		· ·	-	- CO may b Tempenating we chan
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NSG2AM61 NSG2AM62 NSG2AM63 NSG2AM63 NSG2AM63 NSG2AM64	WEMAL Orage of material sequestion: data that does Orage of material sequestion: back does, does experiment of material schedule: back does Orage of material sequestion: back does, does experiment of material schedule: back does Orage of material schedule, does, does experiment of material schedule: back does Orage of materials. After back have, experiment of material schedule: back does Orage of materials. After back have, experiment of material schedule: back does Orage of materis. After back	Image: Section of the end grand section of the end grand section of the predict section of the predict section of the predict section of the predict section of the end grand	Lease and search search and	A B A C B C B C B C B C B B B B B B B B B B B C C C C C C C		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		• •				• • • •		· · · · · · · · · · · · · · · · · · ·				· · · · · · · · · · · · · · · · · · ·				I I I I	· @• · @• · @• · @• · . · . · . · . · . · . · . · . · . · .					_	- X-Ray in a vian and
NS GJA MSG NS	NEMME Objary of standar stangulation. Salaw Takan Stangulation. Salaw Takana Stangulation	Image: Section of the sectio		A B A C B C B C B C B C B C B B B B B B B B B B C C C C C C C C C C C C		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1				30		• • • •						·					· @• · @• · @• · @• · . · . · . · . · . · . · . · . · . · .					_	- X-Ray in a vian mai vian mai - Vian mai - Vian mai - Not vian - Act, was - Act, was - Act, was - Act, was - Act chairs - Act chairs - Act chairs - Chair - Chairs - Chairs - Chairs - Chair - Chair - Chair -
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	Changes in process technology or manufacturing methods - Can / Cap Attaching		Change of Cap/Can attaching process	e.g. change of the sealing method e.g. change from batch oven to reliow oven	с		• •		•	@• @Y •	• •	• •		- ·	• •	•		в -	• •							-	
	Changes in process technology or manufacturing methods - Molding			e.g. change of overmold process parameter	с					@• • @						•		в •	• •							-	
PAS-QUA-PR-08			Change of Marking process	e.g. change from inked marking to laser marking e.g. marking of pin 1						-		• •									@						
PAS-QUA-PR-08	Changes in process technology or manufacturing methods - Marking			e.g. change of appearance (additional marking)	в		• •	1.1	-			• •		• •		-					@	2• • •		1.1.1	1.1	-	ADI check nece
PAS-QUA-PR-09	Changes in process technology or manufacturing methods - Aging		Change of Aging process. Typically no aging done on quartz crystals.	If aging is done: e.g. change of times or terroscolumn	с		• •	- @•	• •					•	•	•		в -	•					1.1	1.0	-	
PAS-QUA-PR-10	Process integrity: turing within specification	- 1	Variation within process specification.	e.g. process control	с		-	1.1	-									a								-	
	PACKING / SHIPPING - NEW MATERIAL, CRITICAL DIMENSIONS				-	1																			- 1		1
PAS-QUA-PN-01	Packing / shipping specification change (lossening of tolerances)	P	Charge of packing specification.	e.g. number of pieces on reel.	в			1.0																	1.1	-	
PAS-QUA-PN-02	Dry pack requirements change		Change of drypack requirements.	e.g. change of MSL e.g. change in dry pack assurance (HIC, MBB)	в			1.1						· · ·				1.1			1.1			1.1	1.1		
PAS-QUA-PN-03	Change of carrier (tray, reel)	P	Change of carrier	e.g. change by material e.g. change by geometry.	в			1.0											1.0					1.1	1.0	-	
-	PACKING / SHIPPING - VISUAL INSPECTION		+ -	e.g. crange by geometry.		1 1																					
	Change of labeling		P Change of labeling, also on reel.	(i) e.g. additional information (RoHG stamp) (P) e.g. change of customer specific information	в																						
PARAMITICI	Charge of adding				5												-			-					-		
PAS-QUA-PV-02	Change of product marking		Marking on device.	e.g. change of content of marking e.g. change of method of marking e.g. change of appearance of marking	в			1.0																			
													_	_		_											
PAS-QUA-PV-03	Change of packing/shipping specification	Р	Change in packing specification which does not described a change of dimensions or material of the packing.	e.g. change of documentation in packing specification				1.0																	1.1		
<u> </u>	LOGISTICS / CAPACITY / TESTING - EQUIPMEMENT		material of the packing.																								
		1 1	Channe in more surfacione which is not	1							<u> </u>	1		<u> </u>		1 1										1	Text effort dans
PAS-QUA-EQ-01	Production from a new equipment/tool which uses a different technology or which due to its unique form or function can be expected to influence the integrity of the final product	• P	Change in process technique which is not already covered above. Note: Changes affecting the product not covered by the table require also a PCN.	e. g. new equipment supplier with different process	с		•	1.0										@в -					-			@•	Test effort depe assessment. Performance te
			covered by the table require also a PCN.																								
4	Developing from a new environmentional which uses the same heat's technology (randomenent			e a additional environment to increase production														@В -								~	Test effort depe
PAS-QUA-EQ-02	Production from a new equipment/bod which uses the same basic technology (replacement equipment or extension of existing equipment pool)		PCN required for dedicated equipment for aenalities component production.	e.g. additional equipment to increase production capacity e.g. replacement of same equipment	с		•											@в -					-			@•	Test effort depe assessment. Performance te process change
			Change of final test equipment which use																								
PAS-QUA-EQ-03	Change in final test equipment type that uses a different technology	Р	Change of final test equipment which use different technology. PCN required for dedicated equipment for sensitive parameters.	e.g. change of tester platform	с		1	1.0						· ·	1.1		1 (A)	@В -					-			@•	Gage R&R / del
4			sensitive parameters.																								
	LOGISTICS / CAPACITY / TESTING - PROCESS FLOW	1 1		e.g. movement or transfer of menufacturing view			_		-													_			-		
PAS-QUA-PF-01	Manufacturing alle transfer or movement of a part of production process to a different location/site	Р	Change of manufacturing site. Includes transfer as well as additional site. Note: Reorganization inside one plantitite is not atflected	e.g. movement or transfer of manufacturing sile or process step(s) to a different location/sile.	в		• •		•		• •	• •	• •	• •	• •	•	· •	в •	• •					· ·	· @•	@•	
A		+ +	not affected	e.g. dual source / fab strategy																							Channel -
	Elimination or addition of a manufacturing process step	1 - 1	Change of manufacturing process sequence.	e.g. change of order of processes	с		•						· · · ·	5 C. S.			1.1	1.1		1.1	1.1	· · ·		· .	· ·	@•	Characterisation production flow
	LOGISTICS / CAPACITY / TESTING - Q-GATE							_	_						_		_	_	_								
QUA-05-01	Change of test coverage used by the supplier to ensure data sheet compliance (e.g., alterination/addition of electrical measurement/test flow block, netwation/enhancement of monitoring procedure or surgright()		Change of test coverage.	e.g. change from 100% to sample inspection e.g. test flow block, reduction from three to teo temperature measurements	с																						R (electr. funct.) R (reliability) on
	monitoring procedure or sampling)	ĽĽ		emperature measurements e.g. change in burn in/run in process.	, in the second se																						process.
	ALUMIUM ELECTROLYTIC CAPACITORS				_																						_
PAS-ALU-AN-01	AVY Any change with impact on agreed upon technical contractual agreements		Intended to be used if no other type of change is applicable but the change affects agreed	Not released for technical																							
																										-	
		Р	>	Technical interface means component terminals. See processability on board level.	В		1 A 1	1.1						5 C. S.			1 A A	1.1	1.1	1	1.0			1 . A.	· @•	-	
	DATASHEET	i i		1	-						- I - I			- r - r													r
PAS-ALU-DS-01	Ohange of datasheet parameters/electrical specification (min./max./kp. values) and / or ACIDC specification	Р	Change of application relevant information Not included: Editorial changes.	e.g. lighten of electrical parameter distribution	A	Risk assessment depending on change for each application.		1.0											- A. (1997)						- A - A - A - A - A - A - A - A - A - A	-	
			No technical channe of modert rencess or										+ +														
4			No technical change of product process or text. New description of behavior which was not appelled balone or which is different hom initial specification. Please indicate clearly, that infonds contains this type of change! Assessment in application required!																								
PAS-ALU-DS-02	Correction of data sheet or issue of errats	1.1	specified before or which is different from	e.g. data sheet correction because of new information about component behavior	A			1.0							1.0										1.1	-	
4			Please indicate clearly, that infoncie contains																								
			Assessment in application required!																								
-													_													-	
			Description of a new not previously covered																								
PAS-MULTS/D	Sour Restor of additional normation		Description of a new not previously covered parameter. No technical change of the product.	e a státos new lineira) normaliar	A																						
PAS-ALU-05-03	Specification of additional parameters		Description of a new not previously covered parameter. Not technical change of the product. (0): no influence (P): Risk assessment depending on change to each acebrication to convide evidence of	e.g. adding new (issited) parameter.	A																				• -	-	
			Description of a new not previously covered parameter. No technical change of the product. (Br: no influence (P): Risk samesument depending on change fo each application to provide evidence of additional parameters (stat. evaluation)	n.g. adding new (tested) parameter.	A		÷																		• -	-	
	MATERIAL		Description of a new not previously covered parameter. No technical change of the product. (1): no internet depending on change to such application to provide endence of additional parameters (stat. evaluation)	n.g. adding new (kesisd) parameter.		B: only if a cap holder holds the	- ·																			-	
			Description of a new not previously covered parameter. No technical change of the product. (1): no internet depending on change to such application to provide endence of additional parameters (stat. evaluation)	e.g. adding new (testind) parameter.		B: crip if a cap hobier hobit the Capacitor body by pressing.	· ·	•	•	· · ·				 - •		•	· ·	· ·					-	· ·	· .	•	
PAS-ALL-MA-01	INTERNE. Charge of material composition - Heating	P	Description of a new not presionally covered parameter. No inchronial change of the product. (B): no inflamment depending on change for meth replication to provide relations of additional parameters (stat. weakation)	e.g. adding new (lealed) parameter.	c		· ·		_								· ·		· ·	· ·	· ·		-	· ·	· ·	-	
	MATERIAL	P I	Description of a new of previously covered the individual sector of the product difference of the product of the product of the individual difference of the sector of end of the individual difference of the end of the individual difference of the individual difference of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the indinviolation difference of the individual diffe	e.g. adding new (keesu) parameter.	c	B: in case of external surface of sealing is changed. Evaluation only, if capacitor is glued	 	• •	•			• •	• •	• -	@• @:	s •			· ·	 	· ·	· · · ·	- -	· ·	· .	-	
PAS-ALLI-NR-01 PAS-ALLI-NR-02	INTERNE. Charge of material composition - Heating	P I	Description of a new of previously covered the individual sector of the product difference of the product of the product of the individual difference of the sector of end of the individual difference of the end of the individual difference of the individual difference of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the individual difference of the end of the individual difference of the indinviolation difference of the individual diffe	e.g. adding new (keesu) parameter.	c		 	• •	_		· · ·	• •	• •		@• @:		· ·		· ·	· · ·	· ·	· · · ·	· · ·		· .	-	Biased Hamidi
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PAS-ALU-PV-02	Change of product marking	1	P Marking on device.	e.g. change of content of marking e.g. change of method of marking e.g. change of appearance of marking	в			100	-	•	-										•		-		•	-			-	-	-		-	
PAS-ALU-PV-03	Change of packing/httpping specification	Ρ	P Charge in packing specification which does not described a charge of dimensions or material of the packing.	e.g. change of documentation in packing specification	•		1.0	1	-	1	1	1.	1		1		1.1	-	• •			-		1	1	-			-	1	-		-	•
	LOGISTICS / CAPACITY / TESTING - EQUIPEMENENT	TT	Change in process technique which is not	1		1			<u> </u>	ГТ							1							1	- T	Т	1	Т	1	ГI	Т		1	• Per
PAS-ALU-ED-01	Production from a new equipment/bol which uses a different technology or which due to its unique term or function can be expected to influence the integrity of the final product	а р	P Change in process technique which is not sheady covered above. Note: Changes affecting the product not covered by the table require also a PCN.	e. g. new equipment supplier with different process concept	с		• •	1.1	•	1	1	•	1	• •		• •	1		•	В			-	-		•		-	-		-		- @	Per pro
PAS-ALL-ED-02	Production from a new equipment/loci which uses the same basic technology (replacement equipment or extension of existing equipment pool)		P PCN required for dedicated equipment for sensitive component production.		с			1.									1			в													- @	Teo and
	equipment or exersion or existing equipment pool																		_	_			_				_	_	-					• Per pro
PAS-ALU-EQ-03	Change in final test equipment type that uses a different technology	Р	P Charge of final test equipment which use different technology. PCN required for dedicated equipment for sensitive parameters.	e.g. change of tester platform	с		•	$(\mathbf{x}_{i}) \in \mathcal{X}_{i}$				· .	1.1	· ·		· ·	1.1	-		@В	-		-	-				-	-		-		- @	• •
	LOGISTICS / CAPACITY / TESTING - PROCESS FLOW	+ +	Channe of months internal late	a a movement or involve of merchanismic site or		l I						_					_		_	-			-			_	_	-	-	1 1		_	_	_
PAS-ALU-PT-01	Manufacturing site transfer or movement of a part of production process to a different location/sit	• P	P Note Recognization inside one plantistic is rectarger and the rectarger in the rectarger in the rectarger inside one plantistic is restantistication	e.g. movement or transfer of manufacturing site or process step(s) to a different location/site.	в		• •	•	•	@•	•	• •	•	• •	•	• •	•	•	• •	в	•	•		-	1	•		1.1		1.1	-	· (8• 6	•
PAS-ALU-PF-02	Elimination or addition of a manufacturing process step		Note: Recrystization inside one plantistle is not effected P Change of manufacturing process sequence. Reduction of final leating. P PCN required for dedicated final leat	 e.g. washing / cleaning process e.g. change of order of processes 	с		•	1.0		•																-								9 8 9
PAS-ALU-PF-03	Elimination of final electrical measurement / set flow block LOGISTICS / CAPACITY / TESTING - G-GATE	1	P PCN required for dedicated final test surfactions for samalities rearrangeers	e.g. elemination of additional impedance control	с																					•							- @	• fra
	Change of test coverage used by the suppler to ensure data sheet compliance (e.g., alministion/addition of electrical measurement/lest flow block, relaxation/enhancement of monitoring procedure or sampling)		p Change of test coverage.	e.g. change from 100% to sample inspection e.g. test flow block, reduction from three to two temperature measurements e.g. change in burn in/run in process.	с			1.1															1.											RORO
	monitoring procedure or sampling) NTC			e.g. change in burn in/sun in process.																														pro
	INT	TT	P is applicable but the change affects agreed	*		1			1	<u> </u>	-				-		1		-	-		_	-	1				-	1	1				_
PAS-NTC-AN-01 PAS-NTC-AN-02	Any change with impact on agreed upon technical contractual agreements Any change with impact on processability/menufacturability at customer, which is not covered in the matrix below.		technical contractual agreements.		в																		-	-				-					@•	
	Re matis bebs. DATASHET	1 1	Description of the second	component terminals.		Plade announcement day		_			-											_					_					- (s •	_
PAS-NTC-DS-01	Any change with inpact on processability/threat/actartabily at castomer, which is not covered in the metrix takes. DATAGETET During of databaset parameters/sectical specification (min.hma.lyp. value) and / or ACDC genefication.	Р	Not included: Editorial changes. No technical change of product, process or	e.g. lighten of electrical parameter distribution	A	Risk assessment depending on change for each application.				•			-				-				•			-	-			-						
PAS-NTC-DS-02	Connection of data abset or issue of errats		test. New description of behavior which was not specified before or which is different from	e.g. data abest correction because of new information about component behavior	A																													
	And the second second second	$ \cdot $	Next. Next description of behavior which was not specified before or which is different from Initial specification. Please indicate clearly, that infonds contains that type of change!	Information about component behavior	Ŷ																													
	1	++																																
PAS-NTC-DS-03	Specification of additional parameters		Description of a new not previously covered parameter. No inchinical change of the product. P (0; no influence (P): Risk assessment depending on change I such application to provide indence of additional parametes (stat. evaluation)	e.g. adding new (tested) parameter.	A			$(\mathbf{x}_{i}) \in \mathcal{X}_{i}$			-	· .					1.1	-															÷	
L	BATERIAL		each application to provide exidence of additional parametes (stat. evaluation)																															
	BALEMAL Change of material composition - Ceramic Binder	Р	P Charge of Binder Material to bind ceramics.		с		•	•	-	-	-		-		-	@• •	@•	@•		-	-		-	-	-	-		-	-	-	-	-	-	
PAS-NTC-MA-02	Dhange of material composition - Ceramic	Р	P Change of ceramic composition	e.g. changes in additives amount	с			•			-				-	• •		•		@В	•	@S		-		-							- @	• par
PAS-NTC-MA-03		++		es, e.g. change from AgPI material to AgPI material															_															
	Change of material composition - Inner Electrode		only.		c	A: Risk assessment on application level		• •				• •			-				• •	В	-	-		-	-	-		-		•	-	-	- (
PAS-NTC-MA-04	Change of material composition - Encapsulation	Р	P Change of encapsulation material.	e.g. change of coating e.g. change of additives in an insulation.	в	A: Risk assessment on application level, if interaction with other material expected.	- -	• •	•		•		-		-		@•	•		@B	@•	-	•	-	-	-		•	•	· ·	-	-	- @	• an per
PAS-NTC-MA-05	Change of material composition - Lead material / Termination	Р	P Change of lead or outer termination. Change lead (Iniah) material, termination material or attachment material.	of e.g. change from SnPb to pure Sn	в	Risk assessment needed to evaluate compatibility of soldering process.	•	•	-	-	@•	@•	-	- @		@• -	-	- @	e• @	• @В	-	@• @	• •	-	-	-		-	-	-	-	-	- @	•
PAS-NTC-MA-05	Change of supplier of malerial				с				•		•				•			•		в	•												- 4	• Aan da
	DESIGN																		_					1				_						
PAS-NTC-DE-01 PAS-NTC-DE-02	Dianges of termination, surface finish, shape, color, appearance or dimension structure - Lead Dianeter Oranges of termination, surface finish, shape, color, appearance or dimension structure - Termination Area		P Charge of lead dameter P Charge of termination area	e.g. change lead diameter from 0.5 to 0.4 mm	в				-					@• @•				-		@B		@• @		-	-	-		-		-	-	-		•
PAS-NTC-DE-02 PAS-NTC-DE-03	Changes of termination, surface finish, shape, color, appearance or dimension structure - Intern			e.g. change of termination layer thickness e.g. change in termination dimensions e.g. change from soldered connection to welded connection	B							 @• @•				@• ·				• @B		@• @		-		-		-				-		• =
PAS-NTC-DE-04	Connection Changes of termination, surface linish, shape, color, appearance or dimension situature -		P Change of appearance. P Note: Marking on device is defined as apparate change (PAS-FLM-PV-02).	connection e.g. change or adding of color on component Mainty in combination with other chances!	в								@•													-								
PAS-NTC-DE-05	Appairance Changes of Inner construction - Electrode		apprate change (PAS-FLM-PV-02). Change of electronic lower thickness -						6								6																	
			 geometry. For multi-bayer technology only. 		c				@•		-			@• ·	-		@•			-		@• @	_	-	•	-		-			-	-	-	
PAS-NTC-DE-06	Changes of inner construction - Layer Thickness		P Charge of ceramic layer thickness. For multi- layer technology only.	e.g. change from 1.5µm into 1.0µm	с		• •			@•	-				•		@•			-		@• @	-	-	•			-	-		-	•	-	·
PAS-NTC-DE-07	Changes of inner construction - Number of Layers	-	P Change of number of ceramic or electrode layers. For multi-layer technology only. Alleasy in combination with PAS-NTC-DE-06.	ys see also layer thickness	с		•		@•	@•	-	· ·	-	@• ·	-		@•	@•		-	-	@• @	• •	-				-	-	-	-	-	-	
PAS-NTC-PR-01	PROCESS Charges in process technology or manufacturing methods - Lamination	1.1			с					<i>@</i> •		@• ·					@•	@•		@B		@•			.	-			1		.	.	- @	
PAS-NTC-PR-02	Changes is process technology or manufacturing methods - Lamination Changes is process technology or manufacturing methods - Firing		P Change of lamination / press technique technology p Change of tring / sintering profile	e.g. samp press to scearc press e.g. temperature and / or time and / or atmosphere. e.g. from tunnel to batch kin.	c							@•			_			@• @															- 6	
			P Charge of dicing / slicing	e.g. from tunnel to batch kin.	c			0.				@• ·			@•					@B				-	-			-		-	-	-	- @	
PAS-NTC-PR-03	Changes in process technology or manufacturing methods - Dicing						• •	8.	@•							• •				в	-	•	-	-	-			-		-	-	-	- @	
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		-	P Change for termination preparation like platin or apply of termination base layer.	e.g. change in plating technology (final termination) e.g. change from dip in paste to plating (apply)	в				-	-	•	• •	•	• •			@•	@• @			-	@•	-	-	-	- L						-	- @	•
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ADSG To UTL Test Transfer Correlation Report For LT8611

Project Owner

Yang Tong Jiang

PRODUCT INFORMATION

Part Name	LT8611
Package	QFN 3x5
Lead Count	24
Description	42V, 2.5A Synchronous Step-Down Regulator with Current Sense and 2.5μA Quiescent Current

PRODUCT TEST SITE TRANSFER CORRELATION

SETUP INFORMATION

|--|

Test Site	Tester	Handler ID	BOARD ID	CONTACTOR ID 1	CONTACTOR ID 2
ADSG	ETS364B	RASCO1000	LT8611 DIB#1	JTI D#5701	JTI D#5701
UTL	ETS364B	RASCO1000	LT8611 DIB#1	JTI D#5701	JTI D#5701

SUMMARY OF TEST RESULTS

Test all good units in ATE-Handler setup through three test temperatures

Test Site	Program	Temp	Lot ID	Qty In	Qty Out
ADSG	LT8611_03	25C	1000536.1	310	310
UTL	LT8611_03	25C	1000536.1	310	310

Test Site	Program	Temp	Lot ID	Qty In	Qty Out
ADSG	LT8611_03	125C	1000536.1	310	310
UTL	LT8611_03	125C	1000536.1	310	310

Test Site	Program	Temp	Lot ID	Qty In	Qty Out
ADSG	LT8611_03	-40C	1000536.1	310	310
UTL	LT8611_03	-40C	1000536.1	310	310

4. Test five fresh (untrimmed) units using QC program if necessary.**

Test Site	Program	Temp	Lot ID	Qty Out	Scraps
ADSG	N/A	N/A	N/A	N/A	N/A
UTL	LT8611IUDD	Ambient	1000536.1	0	5

CORRELATION RESULT

Test Flow	Number of Test	Result
25C Ambient	206	all passed
125C HOT temp	206	all passed
-40C Cold temp	206	all passed

LT8611_25C A	LT8611_25C Analysis Data View Report									
Test Number	Test Name	Units	Overall Correlation Result	Mean Diff%	Mean diff <5% limit range	Stdv Ratio	Sigma Spread Criteria <1.3	СрК	Cpk >1.67	Comments
10.0	VCC cont	V	PASS		N/A		N/A	82.2615934	PASS	CpK greater than 1.67
10.0	VIN cont	v	PASS		N/A		N/A	68.95381273	PASS	CpK greater than 1.67
10.2	SW cont	v	PASS		N/A		N/A	10.83574079	PASS	CpK greater than 1.67
10.3	EN cont	v	PASS		N/A		N/A	56.00301176	PASS	CpK greater than 1.67
10.8	SYNC cont	V	PASS		N/A		N/A	35.73083527	PASS	CpK greater than 1.67
10.1	SS cont	V	PASS		N/A		N/A	38.40180831	PASS	CpK greater than 1.67
10.12	RT cont [18.2K to APU]	V	PASS		N/A		N/A	269.1120758	PASS	CpK greater than 1.67
10.13	PG cont	V	PASS		N/A		N/A	47.44317236	PASS	CpK greater than 1.67
10.15	 FB_cont	V	PASS		N/A		N/A	35.0110989	PASS	CpK greater than 1.67
10.17	BST cont	v	PASS		N/A		N/A	63.98976171	PASS	CpK greater than 1.67
10.19	BIAS cont	V	PASS		N/A		N/A	56.51777984	PASS	CpK greater than 1.67
10.21	IMON cont	V	PASS		N/A		N/A	28.94800088	PASS	CpK greater than 1.67
10.23	CTRL_cont	V	PASS		N/A		N/A	30.39600678	PASS	CpK greater than 1.67
10.25	ISN_cont	V	PASS		N/A		N/A	42.77621318	PASS	CpK greater than 1.67
10.27	ISP_cont	V	PASS		N/A		N/A	45.20094965	PASS	CpK greater than 1.67
10.29	NC_cont	MOhm	PASS		N/A		N/A	20634.36225	PASS	CpK greater than 1.67
940	Vref_Trim_Check [Open Loop]	V	PASS		N/A		N/A	4.27857867	PASS	CpK greater than 1.67
950	** Post-BURN Vout [0.970V] Vin=6V	V	PASS		N/A		N/A	2.33184393	PASS	CpK greater than 1.67
950.1	Post-BURN Vout [0.970V] Vin=40V	V	PASS		N/A		N/A	14.15900012	PASS	CpK greater than 1.67
950.2	Post-BURN OSCF	KHz	PASS		N/A		N/A	13.49640421	PASS	CpK greater than 1.67
950.3	Post-BURN ILIM	mA	PASS		N/A		N/A	5.134546067	PASS	CpK greater than 1.67
950.4	Post-BURN V_IMON	V	PASS		N/A		N/A	8.217665753	PASS	CpK greater than 1.67
950.6	Vref_Trim_Check [Open Loop] [From T940.0]	V	PASS		N/A		N/A	15.12302649	PASS	CpK greater than 1.67
950.7	Delta_of_Vref [T940.0-T950.0]	mV	PASS		N/A		N/A	4.305824486	PASS	CpK greater than 1.67
1000	** lvin_Sleep	uA	PASS		N/A		N/A	6.855451545	PASS	CpK greater than 1.67
1000.1	* Ien_Sleep	nA	PASS		N/A		N/A	170.8770701	PASS	CpK greater than 1.67
1000.2	Irt_Sleep	uA	PASS		N/A		N/A	82.14404288	PASS	CpK greater than 1.67
1000.3	lss_Sleep	uA	PASS		N/A		N/A	107.7335038	PASS	CpK greater than 1.67
1000.4	Ictrl_Sleep	uA	PASS		N/A		N/A	117.6163446	PASS	CpK greater than 1.67
1000.5	lisp_Sleep	uA	PASS		N/A		N/A	106.0866697	PASS	CpK greater than 1.67
1000.6	lisn_Sleep	uA	PASS		N/A		N/A	97.84318125	PASS	CpK greater than 1.67
1000.7	* Ipg_Sleep	nA	PASS		N/A		N/A	28.77456783	PASS	CpK greater than 1.67
1000.8	Ibias_Sleep	uA	PASS		N/A		N/A	10.53880847	PASS	CpK greater than 1.67
1000.9	lintvcc_Sleep [INTVCC=4.0V]	uA	PASS		N/A		N/A	7.054935208	PASS	CpK greater than 1.67
1000.12	Ibst_Sleep	uA	PASS		N/A		N/A	61.98928339	PASS	CpK greater than 1.67
1000.13	* lvin_Sleep_with_SYNC	mA	PASS		N/A		N/A	1.797912329	PASS	CpK greater than 1.67
1100	lvin_Sleep_ABS_MAX	uA	PASS		N/A		N/A	75.18807998	PASS	CpK greater than 1.67
1100.1	len_Sleep_ABS_MAX	uA	PASS		N/A		N/A	221.4230829	PASS	CpK greater than 1.67
1100.2	lisp_Sleep_ABS_MAX	uA	PASS		N/A		N/A	198.364668	PASS	CpK greater than 1.67
1100.3	lisn_Sleep_ABS_MAX	uA	PASS		N/A		N/A	240.9125634	PASS	CpK greater than 1.67
1100.4	Ipg_Sleep_ABS_MAX	uA	PASS		N/A		N/A	529.0105749	PASS	CpK greater than 1.67
1100.5	Imon_ABS_MAX	mA	PASS		N/A		N/A	224.0145775	PASS	CpK greater than 1.67
1200	** Ivin_Shutdown	uA	PASS		N/A		N/A	7.878928314	PASS	CpK greater than 1.67
1200.1	Irt_Shutdown	uA	PASS		N/A	<u> </u>	N/A	15.30246208	PASS	CpK greater than 1.67
1200.2	Iss_Shutdown	mA	PASS		N/A	<u> </u>	N/A	180.2785484	PASS	CpK greater than 1.67
1200.3	* Isync_Shutdown	nA	PASS		N/A	<u> </u>	N/A	132.1695724	PASS	CpK greater than 1.67
1200.4	Ictrl_Shutdown	uA	PASS		N/A		N/A	106.3887011	PASS	CpK greater than 1.67
1200.5	Imon_Shutdown	uA	PASS		N/A	<u> </u>	N/A	123.970603	PASS	CpK greater than 1.67
1200.6	lisn_Shutdown	uA	PASS		N/A		N/A	11.1554007	PASS	CpK greater than 1.67
1200.7	lisp_Shutdown	uA	PASS		N/A		N/A	10.96567933	PASS	CpK greater than 1.67
1200.8	* Ifb_Shutdown	nA mA	PASS	<u> </u>	N/A	<u> </u>	N/A	199.0580831	PASS	CpK greater than 1.67
1200.9	Ipg_Shutdown	mA	PASS		N/A		N/A	578.3132795	PASS	CpK greater than 1.67

1200.1	Ibias Chutdown	۵	DACC		NI / A		NI/A	F 17C700F20	DACC	Call greater than 1.67
1200.1	Ibias_Shutdown	uA	PASS PASS		N/A N/A		N/A N/A	5.176788539 27.28831382	PASS PASS	CpK greater than 1.67
1200.11	* SS_Pulldown_Resistance	Ohm	PASS		N/A N/A		N/A N/A	+		CpK greater than 1.67
1200.12 1300	** PG_Pulldown_Resistance	Ohm	PASS		N/A N/A		N/A N/A	24.92872093	PASS PASS	CpK greater than 1.67
	Ivin_Shutdown_ABS_MAX	uA			-			52.31539586		CpK greater than 1.67
1300.1	Iss_Shutdown_ABS_MAX	mA	PASS		N/A		N/A	26.25126872	PASS	CpK greater than 1.67
1300.2	lisn_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	186.7043882	PASS	CpK greater than 1.67
1300.3	lisp_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	123.6314973	PASS	CpK greater than 1.67
1300.4	Ipg_Shutdown_ABS_MAX	mA	PASS		N/A		N/A	8.806634384	PASS	CpK greater than 1.67
1300.5	Ibias_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	6.497663639	PASS	CpK greater than 1.67
1300.6	Irt_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	4.757308104	PASS	CpK greater than 1.67
1400	* Top_FET_Isw	uA	PASS		N/A		N/A	3.842536012	PASS	CpK greater than 1.67
1500	* Bot_FET_Leakage	uA	PASS		N/A		N/A	2.906756877	PASS	CpK greater than 1.67
1500.1	Bot_FET_AbsMax_Leakage [lbst]	uA	PASS		N/A		N/A	101.7422797	PASS	CpK greater than 1.67
1600	** Regulation_Light_Load_Ivin@1mA	uA	PASS		N/A		N/A	4.005181905	PASS	CpK greater than 1.67
1600.3	** Regulation_Light_Load_lvin@100uA	uA	PASS		N/A		N/A	4.40603539	PASS	CpK greater than 1.67
1600.7	Regulation_Light_Load_Ivin@1mA [Vout=7V]	uA	PASS		N/A		N/A	3.063369778	PASS	CpK greater than 1.67
1600.8	Vout_1mA [Vout-7V]	V	PASS		N/A		N/A	40.04250707	PASS	CpK greater than 1.67
2000	Freq with RT=48uA	KHz	PASS		N/A		N/A	9.721885293	PASS	CpK greater than 1.67
2000.1	RegulationMode Sync=0V	V	PASS		N/A		N/A	6.242514994	PASS	CpK greater than 1.67
2000.2	** SW_Min_Ontime Sync=0V	nS	PASS		N/A		N/A	3.279002118	PASS	CpK greater than 1.67
2100	Freq with RT=48uA	KHz	PASS		N/A		N/A	9.703767686	PASS	CpK greater than 1.67
2100.1	RegulationMode Sync=3.3V	V	PASS		N/A		N/A	6.092293124	PASS	CpK greater than 1.67
2100.2	** SW_Min_Ontime Sync=3.3V	nS	PASS		N/A		N/A	2.745780091	PASS	CpK greater than 1.67
2200	* TopRDSon [Vin-Vsw]	Ohm	PASS		N/A		N/A	2.699787532	PASS	CpK greater than 1.67
2200.1	V_sw_out@1A before ramp [Debug only]	V	PASS		N/A		N/A	29.62414972	PASS	CpK greater than 1.67
2200.2	Slop_Comp_Ilim	mA	PASS		N/A		N/A	6.059505646	PASS	CpK greater than 1.67
2300	V_sw_out@1.5A before ramp [Debug only]	V	PASS		N/A		N/A	21.43924069	PASS	CpK greater than 1.67
2300.1	** Top_I_Lim	mA	PASS		N/A		N/A	3.366386388	PASS	CpK greater than 1.67
2300.2	Burst_I_Lim	mA	PASS		N/A		N/A	2.236102603	PASS	CpK greater than 1.67
2300.3	SYNC_I_Lim	mA	PASS		N/A		N/A	7.684902576	PASS	CpK greater than 1.67
2400	Vout [0.6A load] @Vin=6V	V	PASS		N/A		N/A	15.7809118	PASS	CpK greater than 1.67
2400.1	** Minimum Input VOltage [Min_Vin_UVLO]	V	PASS		N/A		N/A	2.454479245	PASS	CpK greater than 1.67
2400.2	Vout [0.6A load] Drop	V	PASS	3.89101184	PASS	0.968	PASS	0.828161574	N/A	tightened limits
2400.3	SW_Min_Ontime Sync=0V [Calc]	nS	PASS		N/A		N/A	16.9838382	PASS	CpK greater than 1.67
2400.4	SW_Min_Ontime Sync=3V [Calc]	nS	PASS		N/A		N/A	13.83906647	PASS	CpK greater than 1.67
2500	* BotRDSon [Pgnd-Vsw]	Ohm	PASS		N/A		N/A	2.999796152	PASS	CpK greater than 1.67
2500.1	BST pin Voltage thru 1K	V	PASS		N/A		N/A	405.2715175	PASS	CpK greater than 1.67
2500.2	Zero cross current	mA	PASS		N/A		N/A	2.679742915	PASS	CpK greater than 1.67
2600	** DA_Current_Limit [Bot_I_Lim]	mA	PASS		N/A		N/A	2.201635285	PASS	CpK greater than 1.67
2700	SW Frequency	KHz	PASS		N/A		N/A	2.987595045	PASS	CpK greater than 1.67
2700.1	* Min Off Time	nS	PASS		N/A		N/A	2.509887405	PASS	CpK greater than 1.67
2700.2	 W_duty_cycle	%	PASS		N/A		N/A	2.992350576	PASS	CpK greater than 1.67
2700.3	Dropout Voltage	V	PASS		N/A		N/A	3.102284034	PASS	CpK greater than 1.67
2800	* Vintvcc OmA no bias	V	PASS		N/A		N/A	3.264437276	PASS	CpK greater than 1.67
2800.1	Vintvcc_20mA_no_bias	V	PASS		N/A		N/A	22.74922628	PASS	CpK greater than 1.67
2900	* Vintvcc_0mA_with_bias	V	PASS		N/A		N/A	12.1489637	PASS	CpK greater than 1.67
2900.1	Vintvcc 20mA with bias	V	PASS		N/A		N/A	15.05058051	PASS	CpK greater than 1.67
3000.1	Intvcc_llim_no_bias [Vccint=3V]	mA	PASS		N/A		N/A	13.97038926	PASS	CpK greater than 1.67
3100.1	Intvcc Ilim ABSMAX no bias [Vccint=3V]	mA	PASS		N/A		N/A	7.097514722	PASS	CpK greater than 1.67
3200.1	Intvcc Ilim with bias [Vccint=3V]	mA	PASS		N/A		N/A	7.533574121	PASS	CpK greater than 1.67
3300.1	Intvcc_llim_ABSMAX_with_bias [Vccint=3V]	mA	PASS		N/A		N/A	7.896753994	PASS	CpK greater than 1.67
3400	Intvcc BIAS Threshold RampDown	V	PASS		N/A		N/A	4.297966596	PASS	CpK greater than 1.67
3400.1	Intvcc_BIAS_Threshold RampUp	V	PASS		N/A		N/A N/A	2.715432363	PASS	CpK greater than 1.67
3400.2	Intvcc BIAS Threshold Hysteresis	v	PASS		N/A		N/A N/A	440.2469454	PASS	CpK greater than 1.67
3500	Intvcc_Vin_Threshold RampDown	V	PASS		N/A		N/A N/A	8.354033985	PASS	CpK greater than 1.67
3500.1	Intvcc Vin Threshold RampUp	V	PASS		N/A		N/A N/A	7.778331659	PASS	CpK greater than 1.67
3500.1	Intyce Vin Threshold Hysteresis	V	PASS		N/A		N/A N/A	781.2821339	PASS	CpK greater than 1.67
5500.2		v	1735		11/7			1 /01.2021339	1735	Concerter than 1.07

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4202 v*P0 Ugen Treahold Offset for VTPNNQ12095404FL023PL023PL035L02PL035L02PL035L02PL035L02PL035L02PL035L02PL035L02PL035L02PL035<							,			
4400 •••**********************************										
4300 **NC, Theshold Ramplo V PAS NA 6.48973425 PASS Cpreater than 1.67 4300.1 *SYNC, Theshold Ramplo V PASS N/A N/A 10.55675 PASS Cpreater than 1.67 4300.1 SYNC, Theshold Ramplow V PASS N/A N/A 10.55678 PASS Cpreater than 1.67 4500.1 Reference Voltage (Wn-4V. Luade) 5.4 V PASS N/A N/A N/A 10.556718 PASS Cpreater than 1.67 4500.1 Reference Voltage (Wn-4V. Luade) 5.4 V PASS N/A N/A N/A 10.550618 PASS Cpreater than 1.67 4500.1 Reference Voltage (Wn-4V. Luade) 4.1 V PASS N/A N/A N/A 10.570611 PASS Cpreater than 1.67 4500.4 Reference Voltage (Wn-12V. Load-0.4.1 V PASS N/A N/A N/A 10.570611 PASS Cpreater than 1.67 4600.4 Reference Voltage (Wn-12V. Load-0.4.1 V PASS N/A N/A		* PG Upper Threshold Offset from VFB				1.032				
4400.1 *SYN_Threshold Rengup V PASS N/A N/A 10.0632652 PASS Cpl greater ban 1.67 4500.2 SYN_Threshold Rengup V PASS N/A N/A 11.62 SSC pl greater ban 1.67 4500.1 Reference Voltage [Vin=42V, Laad=0.54] V PASS N/A N/A 11.05 Cols greater ban 1.67 4500.3 Reference Voltage [Vin=42V, Laad=0.54] V PASS N/A N/A 10.056634 PASS Cols greater ban 1.67 4500.3 Reference Voltage [Vin=42V, Laad=0.14] V PASS N/A N/A N/A 10.056649 PASS Cols greater ban 1.67 4500.4 Reference Voltage [Vin=42V, Laad=1.3] V PASS N/A N/A N/A 10.056634 PAS Cols greater ban 1.67 4500.4 Reference Voltage [Vin=42V, Laad=1.3] V PASS N/A N/A 10.46633 PASS Cols greater ban 1.67 4500.4 Reference Voltage [Vin=42V, Laad=1.3] V PASS N/A N/A 10.466377	4200.4	* PG Hi Hysteresis	%	PASS				8.982278174	PASS	CpK greater than 1.67
43002 ON, Threshold Hysteresis V PASS N/A N/A 24233863 PASS Cpt greater hun 1:67 45001 Hedden Efference Voltage (Vin-AV, Lado-D.SA) V PASS N/A N/A 113.0266932 PASS Cpt greater hun 1:67 45001 Reference Voltage (Vin-AV, Lado-D.SA) V PASS N/A N/A 113.0266932 PASS Cpt greater hun 1:67 45001 Reference Voltage (Vin-AV, Lado-D.SA) V PASS N/A N/A 6.72386248 PASS Cpt greater hun 1:67 45004 Reference Voltage (Vin-12V, Liado-12A) V PASS N/A N/A N/A 5.056 Cpt greater hun 1:67 45004 Reference Voltage (Vin-12V, Liado-12A) V PASS N/A N/A N/A 1.05100210 PASS Cpt greater hun 1:67 45004 Reference Voltage (Vin-12V, Liado-12A) M PASS N/A N/A N/A 1.05100210 PASS Cpt greater hun 1:67 45004 Reference Voltage (Vin-12V, Liado-12A) M <a< td=""> N/A</a<>	4300	* SYNC_Threshold RampDown	V	PASS	N/A		N/A	6.489734525	PASS	CpK greater than 1.67
deback kefernee voltage [vin-2y, Laad-0.5A V PASS NA NA NA NA I.G. Stability PASS CpC greater than 1.67 4500.1 Reference Voltage [vin-4y, Laad-0.5A] V PASS CPC greater than 1.67 4500.2 Reference Voltage [vin-4y, Laad-0.5A] V PASS CPC greater than 1.67 4500.4 Meference Voltage [vin-12y, Laad-0.5A] V PASS CPC greater than 1.67 4500.4 Meference Voltage [vin-12y, Laad-0.5A] V PASS N/A N/A N/A PASS CPC greater than 1.67 4500.4 Meference Voltage [vin-12y, Laad-0.5A] V PASS N/A N/A N/A PASS CPC greater than 1.67 4500.4 Feedback Voltage Laad Regulation r/A PASS N/A N/A N/A N/A PASS CPC greater than 1.67 4500 Feedback Voltage Laad Regulation r/A PASS CPC greater than 1.67 PASS CPC greater than 1.67 5000 *** Distablet, Oxt.; thig Revial Contagreater than 1.67 PASS CPC greater than 1.67	4300.1	* SYNC_Threshold RampUp	V	PASS	N/A		N/A	10.08526657	PASS	CpK greater than 1.67
49.00Reference Volkage (Vne-AV, Load-D-SA)VPASS(NANA13.0268-32PASS(C) genet rhan 1.6749.02A**feedbac Volkage Une Requision%VPASS(C) service Vnal-SCPASS(C) genet rhan 1.6749.04***feedbac Volkage Une Requision%VPASS(C) genet rhan 1.67(C) service Vnal-SC49.04***feedbac Volkage Une 12V, Load-2.5A)VPASS(C) genet rhan 1.6749.05Reference Volkage (Vna-12V, Load-2.5A)%VPASS(C) genet rhan 1.6749.06reedback Volkage Lond Regultion%PASS(C) genet rhan 1.6749.06reedback Volkage (Vna-12V, Load-2.5A)%VPASS(C) genet rhan 1.6749.06reedback Volkage (Vna-12V, Load-2.5A)%VPASS(C) genet rhan 1.6749.07Regulting vith, SVPASS(C) genet rhan 1.6749.08Regulting vith, SVPASS(C) genet rhan 1.6750.01** Volkage (Vna-12V, Log NethoneNANANANA50.02Volk (H) REL3.22HKPASS(C) genet rhan 1.6750.01Vith Return (Vna, RELSKVPASS(C) genet rhan 1.6750.02Volk (H) REL3.24HKPASS(C) genet rhan 1.6750.03Fifteency Vith MEL3.24HKPASS(C) genet rhan 1.6750.04Vith State (Vna, RELSKPASS(C) genet rhan 1.6750.05Volk (H) REL3.24HKPASS(C) genet rhan 1.6750.05Volk (H) REL3.24H	4300.2	SYN_Threshold Hysteresis	V	PASS	N/A		N/A	23.42539663	PASS	CpK greater than 1.67
49.00Reference Volkage (Vne-AV, Load-D-SA)VPASS(NANA13.0268-32PASS(C) genet rhan 1.6749.02A**feedbac Volkage Une Requision%VPASS(C) service Vnal-SCPASS(C) genet rhan 1.6749.04***feedbac Volkage Une Requision%VPASS(C) genet rhan 1.67(C) service Vnal-SC49.04***feedbac Volkage Une 12V, Load-2.5A)VPASS(C) genet rhan 1.6749.05Reference Volkage (Vna-12V, Load-2.5A)%VPASS(C) genet rhan 1.6749.06reedback Volkage Lond Regultion%PASS(C) genet rhan 1.6749.06reedback Volkage (Vna-12V, Load-2.5A)%VPASS(C) genet rhan 1.6749.06reedback Volkage (Vna-12V, Load-2.5A)%VPASS(C) genet rhan 1.6749.07Regulting vith, SVPASS(C) genet rhan 1.6749.08Regulting vith, SVPASS(C) genet rhan 1.6750.01** Volkage (Vna-12V, Log NethoneNANANANA50.02Volk (H) REL3.22HKPASS(C) genet rhan 1.6750.01Vith Return (Vna, RELSKVPASS(C) genet rhan 1.6750.02Volk (H) REL3.24HKPASS(C) genet rhan 1.6750.03Fifteency Vith MEL3.24HKPASS(C) genet rhan 1.6750.04Vith State (Vna, RELSKPASS(C) genet rhan 1.6750.05Volk (H) REL3.24HKPASS(C) genet rhan 1.6750.05Volk (H) REL3.24H	4500	eedback Reference Voltage [Vin=12V, ILoad=0.5A	V	PASS	N/A		N/A	116.5485431	PASS	CpK greater than 1.67
4500. ***Techock Voltage Line Regulation %/V PASS NA NA K K Cpk greater than 1.67 4500.4 Reference Voltage (Inr-12V, Load-2.5A) V PASS NA NA NA 2.4223242 PASS Cpk greater than 1.67 4500.6 Feedback Voltage Unr-12V, Load-2.5A) V PASS NA NA NA 2.4223242 PASS Cpk greater than 1.67 4800 *endback Voltage Line Regulation % PASS NA NA NA 1.53006417 PASS Cpk greater than 1.67 5000 **Baging untre, Consumption MA PASS NA NA A 831668797 PASS Cpk greater than 1.67 5100 **Datashect, Ox, High Reid Line RASS NA NA NA A 2.4293249 PASS Cpk greater than 1.67 5100.1 Lyin, R18K V PASS NA NA NA A PASS Cpk greater than 1.67 5100.2 Vou R18K V PASS NA NA	4500.1	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS	N/A		N/A	113.0266932	PASS	CpK greater than 1.67
4500. ***Techock Voltage Line Regulation %/V PASS NA NA K K Cpk greater than 1.67 4500.4 Reference Voltage (Inr-12V, Load-2.5A) V PASS NA NA NA 2.4223242 PASS Cpk greater than 1.67 4500.6 Feedback Voltage Unr-12V, Load-2.5A) V PASS NA NA NA 2.4223242 PASS Cpk greater than 1.67 4800 *endback Voltage Line Regulation % PASS NA NA NA 1.53006417 PASS Cpk greater than 1.67 5000 **Baging untre, Consumption MA PASS NA NA A 831668797 PASS Cpk greater than 1.67 5100 **Datashect, Ox, High Reid Line RASS NA NA NA A 2.4293249 PASS Cpk greater than 1.67 5100.1 Lyin, R18K V PASS NA NA NA A PASS Cpk greater than 1.67 5100.2 Vou R18K V PASS NA NA	4500.2	Reference Voltage [Vin=40V, ILoad=0.5A]	V	PASS	N/A		N/A	120.856449	PASS	CpK greater than 1.67
450.00 Reference Volage (Vm=2/2), (Load=0.1A) V PASS ONA N/A 113.270694 PASS Cpk greater than 1.67 450.05 Feedence Volage (un=2/2), (Load=0.2A) V PASS N/A N/A 12.3210.4212 PASS Cpk greater than 1.67 450.06 Feedback Volage (un=2/2), (Load=0.2A) N/A N/A N/A 10.5100107 PASS Cpk greater than 1.67 450.0 *BAS, pin, Current Consumption N/A N/A N/A 4.31660797 PASS Cpk greater than 1.67 5000 **Datasheet, Osc, High Her.13.271 KHz PASS N/A N/A 4.31660797 PASS Cpk greater than 1.67 5100.1 LV, In.184K V PASS N/A N/A N/A 2.3305097 PASS Cpk greater than 1.67 5100.1 LV, In.184K V PASS N/A N/A N/A 2.3305097 PASS Cpk greater than 1.67 5200.1 LV, In.184K V PASS N/A N/A N/A 1.3464031 PASS	4500.3		%/V	PASS	N/A		N/A	6.772862465	PASS	CpK greater than 1.67
450.0 Reference voltage (vm-12v, ltoad+2.5A) V PASS NA N/A 2.4242242 PASS Cpc greater than 1.67 450.0 * Belay sin_current_consumption mA PASS N/A N/A 10.51020107 PASS Cpc greater than 1.67 4800 * Belay sin_current_consumption mA PASS N/A N/A 8.105102007 PASS Cpc greater than 1.67 5100 * * Dutasheet_Oox_Hehh [Rt=18.2X] KH PASS N/A N/A A.3491345 PASS Cpc greater than 1.67 5100.1 L/un rt18k mA PASS N/A N/A N/A 2.3893657 PASS Cpc greater than 1.67 5100.1 L/un rt18k mA PASS N/A N/A N/A 2.3893657 PASS Cpc greater than 1.67 5100.3 Efficiency, Rt18K V PASS N/A N/A N/A N/A S.05 Cpc greater than 1.67 5200.1 L/un rt160K mA PASS N/A N/A N/A S.05	4500.4		V	PASS			N/A	115.3706941	PASS	
450.6 Feedback Vorge Load Regulation % PASS NA IVA IVA 17.3010471 PASS Cpf greater than 1.67 4800 * BAS jon (corrent, Consumption nA PASS N/A N/A N/A S000107 PASS Cpf greater than 1.67 5000 ** S Jin, Corrent uA PASS N/A N/A N/A 4.3431845 PASS Cpf greater than 1.67 5100 ** Databater Cox, Higi (FE1.2x) Kitz PASS N/A N/A N/A 2.43706698 PASS Cpf greater than 1.67 51001 I_Vin, RUBK MA PASS N/A N/A N/A PASS Cpf greater than 1.67 5100.2 Yout, RUBK MA PASS N/A N/A N/A PASS Cpf greater than 1.67 5100.3 Efficiency, RUBK MA PASS N/A N/A N/A PASS Cpf greater than 1.67 5200.1 I_Vin, RUBK MA PASS N/A N/A N/A PASS Cpf grea			V							
4800 **Bds pin_Current_consumption mA PASS CM NA 0.5102000 PASS Cpk greater than 1.67 5000 *** 52, Pin_Current u.A PASS Cpk greater than 1.67 5100 *** batabnetc, Oc. High [FIL32X] Kit PASS Cpk greater than 1.67 5100 1.'un R18K mA PASS Cpk greater than 1.67 5100.1 1.'un R18K mA PASS Cpk greater than 1.67 5100.2 Vout, R118K mA PASS N/A N/A 232358867 PASS Cpk greater than 1.67 5100.2 Vout, R118K mA PASS N/A N/A N/A 23285867 PASS Cpk greater than 1.67 5200.1 1.'un, R160K mA PASS N/A N/A N/A 238464073 PASS Cpk greater than 1.67 5200.1 1.'un, R160K mA PASS N/A N/A N/A 238464073 PASS Cpk greater than 1.67 5200.1 Vunt, R160K mA PASS			%	PASS					PASS	
4900 Regulating, with S: V PASS N/A N/A N/A 8.34668777 PASS Cox greater than 1.67 5000 *** Datasheet, Osc, High [Rt=18.2K] KHz PASS N/A N/A N/A 2.437066998 PASS Cox greater than 1.67 5100.1 _f.Yin, Rt18K mA PASS N/A N/A N/A 2.437066998 PASS Cox greater than 1.67 5100.2 Vout Rt18K v PASS N/A N/A N/A 1.717864697 PASS Cox greater than 1.67 5100.3 Efficiency, Rt18K mA PASS N/A N/A N/A 1.717864697 PASS Cox greater than 1.67 5200.1 _i.Yin, Rt50K mA PASS N/A N/A N/A 1.85.664973 PASS Cox greater than 1.67 5200.2 Vout, Rt60K mA PASS N/A N/A N/A 1.85.664973 PASS Cox greater than 1.67 5200.2 Vout, Rt60K mA PASS N/A N/A		U								
500 ***S pm_Current VA PASS N/A N/A 4.349145 PASS CpK greater than 1.67 5100 1**Datashet_Osz, High [Rt=18.2K] KHz PASS N/A N/A N/A 2.43706698 PASS CpK greater than 1.67 5100.1 1_Vin_R118K MA PASS N/A N/A N/A 2.43706698 PASS CpK greater than 1.67 5100.2 Vour, R18K V PASS N/A N/A N/A 2.430068967 PASS CpK greater than 1.67 5200.1 LVin, R16K PASS N/A N/A N/A 7.17864507 PASS CpK greater than 1.67 5200.1 LVin, R16K MA PASS N/A N/A N/A 2.9370417 PASS CpK greater than 1.67 5200.2 Vour, R160K V PASS N/A N/A N/A 12.93172931 PASS CpK greater than 1.67 5300.1 SYNC, Frequency [Sync-2/Mt1] KHz PASS N/A N/A N/A 12.93172931										
S100 **Datashet_Os_Light[ht=18.2K] KHz PASS IV/A IV/A IV/A 2.43706698 PASS CpK greater than 1.67 S100.1 I-Vin, R18K V PASS IV/A			· · ·							
S100.1 L Vin, R138 k PAS N/A N/A N/A PAS Qrk greater than 1.67 S100.2 Vout, R138 k V PASS N/A N/A 9.23055967 PASS Cpk greater than 1.67 S100.3 Efficiency, R138 k PASS N/A N/A 17.3766407 PASS Cpk greater than 1.67 S200.0 ** Datasheet, Osc. Low [Rt=60.4K] KHz PASS N/A N/A 17.3766407 PASS Cpk greater than 1.67 S200.1 L Vin, Rt60K mA PASS N/A N/A 18.844973 PASS Cpk greater than 1.67 S200.3 Efficiency, Rt60K V PASS N/A N/A 18.854973 PASS Cpk greater than 1.67 S300.1 SYNC, Frequency [Sync=1MHz] KHz PASS N/A N/A N/A 18.854934 PASS Cpk greater than 1.67 S400.1 Osc. Low [Rt=3.84/6.3 N/A N/A N/A 17.884943 PASS Cpk greater than 1.67 S400.2 Osc. [Rt=3.84/6.3.386K] <td></td> <td>= =</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>		= =								
5100.2 Vour, R128K V PASS N/A N/A 92.38058967 PASS Cpk greater than 1.67 5100.3 Efficiency, R128K KHz PASS N/A N/A N/A 7.389802813 PASS Cpk greater than 1.67 5200.1 I_Vin, R160K MA PASS N/A N/A N/A 7.389802813 PASS Cpk greater than 1.67 5200.2 Vour, R160K V PASS N/A N/A N/A 9.25207417 Cpk greater than 1.67 5200.2 Vour, R160K V PASS N/A N/A N/A 9.25207417 Cpk greater than 1.67 5300.3 Efficiency, R160K V PASS N/A N/A N/A 81.07450682 PASS Cpk greater than 1.67 5300.1 SYNC_Frequency [Sync-2.20kHz] KHz PASS N/A N/A N/A 17.8884953 PASS Cpk greater than 1.67 5400.1 Osc_Low [R1+3.84A] KHz PASS N/A N/A N/A N/A N/A <td></td>										
S10.3 Efficiency, R18K PASS N/A N/A 17.17864921 PASS CpK greater than 1.67 S200.1 L_Vin_Rt60K mA PASS N/A N/A 7.89802813 PASS CpK greater than 1.67 S200.1 L_Vin_Rt60K mA PASS N/A N/A 185.4644973 PASS CpK greater than 1.67 S200.3 Efficiency_Rt60K V PASS N/A N/A 185.4644973 PASS CpK greater than 1.67 S200.3 Efficiency_Rt60K V PASS N/A N/A N/A 18.0493216 PASS CpK greater than 1.67 S300.1 SYNC_Frequency [Sync=2.2MHz] KHz PASS N/A N/A 18.0450682 PASS CpK greater than 1.67 S400.1 Osc_Low [Rt=32uA] KHz PASS N/A N/A 17.884953 PASS CpK greater than 1.67 S400.1 Osc_Low [Rt=32uA] KHz PASS N/A N/A 17.884953 PASS CpK greater than 1.67 S400.1										· ·
S200 ** Datashet_Os_Low (Rt=60.4K) KHz PASS N/A N/A N/A 7.88940213 PASS CpK greater than 1.67 S200.1 I_Vin_R160K MA PASS CpK greater than 1.67 CpK greater than 1.67 S200.2 Vout_R160K V PASS N/A N/A N/A 2.52074417 PASS CpK greater than 1.67 S200.3 Efficiency_R160K V PASS N/A N/A N/A 12.93172953 PASS CpK greater than 1.67 S300 SYNC_Frequency [Sync=2.2MHz] KHz PASS N/A N/A 17.884953 PASS CpK greater than 1.67 S400 ** Datasheet_Osc_Low [Rt=21X] KHz PASS N/A N/A 17.884953 PASS CpK greater than 1.67 S400 ** Datasheet_Osc_Low [Rt=21X] KHz PASS N/A N/A 17.884953 PASS CpK greater than 1.67 S400.1 Osc_Med_HI [Rt=24N] KHz PASS N/A N/A 17.884953 CpK greater than 1.67			•							
S200.1 I_Vin_Rt60K mA PASS N/A N/A I85.4644973 PASS Cpk greater than 1.67 S200.2 Vout Rt60K V PASS N/A N/A N/A 92.507.4417 PASS Cpk greater than 1.67 S200.3 IEfficiency, Rt60K PASS N/A N/A 12.9317293 PASS Cpk greater than 1.67 S300.1 SYNC_Frequency [Sync=2MHz] KHz PASS N/A N/A 18.80.033216 PASS Cpk greater than 1.67 S300.1 SYNC_Frequency [Sync=2.0MHz] KHz PASS N/A N/A N/A 17.884953 PASS Cpk greater than 1.67 S400.0 ** Datashet_0sc, Low [Rt=2.21K] KHz PASS N/A N/A N/A 17.884953 PASS Cpk greater than 1.67 S400.1 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A N/A 15.085908 PASS Cpk greater than 1.67 S400.2 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A N/A 21.322809			KH7			_				
S200.2 Vout_Rt60K V PASS N/A N/A 92.5207417 PASS CpK greater than 1.67 S200.3 Efficiency_Rt60K PASS N/A N/A 12.93172953 PASS CpK greater than 1.67 S300 SYNC_Frequency [Sync=2.2MH2] KHz PASS N/A N/A 81.07450682 PASS CpK greater than 1.67 S300.1 SYNC_Frequency [Sync=2.2MH2] KHz PASS N/A N/A 81.07450682 PASS CpK greater than 1.67 S300.1 SYNC_Frequency [Sync=2.0KHz] KHz PASS N/A N/A 17.884953 PASS CpK greater than 1.67 S400.1 Osc_low [Rt=38uA] KHz PASS N/A N/A 15.0865908 PASS CpK greater than 1.67 S400.2 Osc_Med H [Rt=24uA] KHz PASS N/A N/A 2.13228092 PASS CpK greater than 1.67 S400.3 Rt_Voltage_Hit=18.28/K0.04x13.986K V PASS N/A N/A 2.035839169 PASS CpK greater than 1.67						_				
S200.3 Efficiency_REG0K PASS N/A N/A 12.93172933 PASS CpK greater than 1.67 S300 SYNC_Frequency [Sync=1MHz] KHz PASS N/A N/A 186.093216 PASS CpK greater than 1.67 S300.1 SYNC_Frequency [Sync=22MHz] KHz PASS N/A N/A 180.07450682 PASS CpK greater than 1.67 S400.1 SYNC_Frequency [Sync=20MHz] KHz PASS N/A N/A 17.8884933 PASS CpK greater than 1.67 S400.1 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A 16.8659508 PASS CpK greater than 1.67 S400.2 Osc_Med Hi [Rt=24uA] KHz PASS N/A N/A N/A 2.3228092 PASS CpK greater than 1.67 S400.3 R_t_Voltage_Hi [Rt=3.2K//60.4K=13.96KK] V PASS N/A N/A N/A 2.3228092 PASS CpK greater than 1.67 S500.1 R_t_Voltage_Hi [Rt=3.2K//60.4K=13.96KK] V PASS N/A N/A 2.3228092										
5300 SYNC_Frequency [Sync=1.MHz] KHz PASS N/A N/A N/A 186.093216 PASS CpK greater than 1.67 5300.1 SYNC_Frequency [Sync=2.0KHz] KHz PASS N/A N/A 81.07450682 PASS CpK greater than 1.67 5300.2 SYNC_Frequency [Sync=2.0KHz] KHz PASS N/A N/A N/A 81.07450682 PASS CpK greater than 1.67 5400 ** Datasheet_Osc_Low [Rt=221K] KHz PASS N/A N/A N/A 2.927320808 PASS CpK greater than 1.67 5400.1 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A N/A 2.927320808 PASS CpK greater than 1.67 5400.2 Osc_Med Hi [Rt=18.2K//60.4K=13.986K] V PASS N/A N/A N/A 2.13280992 PASS CpK greater than 1.67 5400.4 Rt_Voltage_Ini [Rt=18.2K//60.4K=13.986K] V PASS N/A N/A 2.032839169 PASS CpK greater than 1.67 5500.1 Rt_voltage_Loft=18.2K//60.4K=13.986K1		-	v							
5300.1 SYNC_Frequency [Sync=2.2MHz] KHz PASS N/A N/A 81.07450682 PASS CpK greater than 1.67 5300.2 SYNC_Frequency [Sync=200KHz] KHz PASS N/A N/A N/A 17.8884953 PASS CpK greater than 1.67 5400 ** Datasheet_Os_Low [Rt=221K] KHz PASS N/A N/A N/A 2.92732080 PASS CpK greater than 1.67 5400.1 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A 15.0865908 PASS CpK greater than 1.67 5400.2 Osc_Med_Hi [Rt=24.0A] KHz PASS N/A N/A N/A 2.132280992 PASS CpK greater than 1.67 5400.3 Rt_Voltage_Hi + 13.89K6*0.024.0A[Calc] V PASS N/A N/A N/A 2.03239169 PASS CpK greater than 1.67 5500.1 Rt_Voltage_Lo [Rt=13.2K//60.4K=13.986K] V PASS N/A N/A N/A 2.10877077 PASS CpK greater than 1.67 5500.2 Rt_Voltage_Lo + 13.986K*0.024u_A[Calc] V PASS N/A N/A N/A 2.4923854 PASS		· -	K 11-							
S300.2SYNC_Frequency [Sync=200KHz]KHzPASSPASSN/AN/A17.8884953PASSCpK greater than 1.67S400*** Datasheet_Osc_Low [Rt=32k]KHzPASSN/AN/A2.92730808PASSCpK greater than 1.67S400.1Osc_Low [Rt=3.8k]KHzPASSN/AN/A15.0850508PASSCpK greater than 1.67S400.2Osc_Med_Hi [Rt=124uA]KHzPASSN/AN/A2.13228092PASSCpK greater than 1.67S400.3Rt_Voltage_Hi [Rt=13.8X/Ko.4K=13.986K]VPASSN/AN/A2.13228092PASSCpK greater than 1.67S400.4Rt_Voltage_Hi 13.986K*0.024uA [cal]VPASSN/AN/A2.13228092PASSCpK greater than 1.67S400.4Rt_Voltage_Li [Rt=18.2K/Ko.4K=13.986K]VPASSN/AN/A2.13228092PASSCpK greater than 1.67S500.1Rt_Voltage_Lo [Rt=18.2K/Ko.4K=13.986K]VPASSN/AN/AN/A3.13892347PASSCpK greater than 1.67S500.2Rt_Voltage_Lo 13.986K*0.024uA [cal]VPASSN/AN/AN/A18.896087PASSCpK greater than 1.67S500.3S5_Threshold Lo_stop_chargingVPASSN/AN/AN/A17.885225PASSCpK greater than 1.67S500.4S5_Untage_Lis Histas/KindigVPASSN/AN/AN/A17.4852255PASSCpK greater than 1.67S600SS_Untage_Lis Histas/Lis MintageVPAS										
5400 ** Datasheet_Osc_Low [Rt=221K] KHz PASS N/A N/A 2.927320808 PASS Cpk greater than 1.67 5400.1 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A 15.0855958 PASS Cpk greater than 1.67 5400.2 Osc_Med Hi [Rt=24uA] KHz PASS N/A N/A 2.132280992 PASS Cpk greater than 1.67 5400.3 Rt Voltage_Hi [Rt=3k/fo.4k=13.986K] V PASS N/A N/A 2.0323734 PASS Cpk greater than 1.67 5400.4 Rt voltage_Hi [Rt=3k/fo.4k=13.986K] V PASS N/A N/A N/A 2.035839169 PASS Cpk greater than 1.67 5500 Frequency_Foldback KHz PASS N/A N/A N/A 2.031839169 PASS Cpk greater than 1.67 5500.1 Rt Voltage_Lo [t13.82K/fo.04k=13.986K] V PASS N/A N/A N/A 26.49238544 PASS Cpk greater than 1.67 5500.2 Rt voltage_Lo 11.386K^0.0.24uA [Calc] V PASS N/A <td></td>										
5400.1 Osc_Low [Rt=3.8uA] KHz PASS N/A N/A 15.08659508 PASS CpK greater than 1.67 5400.2 Osc_Med_Hi [Rt=24uA] KHz PASS N/A N/A 2.132280992 PASS CpK greater than 1.67 5400.3 Rt_Voltage_Hi [Rt=3.2K/f60.4K=13.986K] V PASS N/A N/A 28.02125734 PASS CpK greater than 1.67 5400.4 Rt_Voltage_Hi (Rt=3.2K/f60.4K=13.986K) V PASS N/A N/A 20.35839129 PASS CpK greater than 1.67 5400.4 Rt_Voltage_Li [Rt=8.2K/f60.4K=13.986K] V PASS N/A N/A 3.13228079 PASS CpK greater than 1.67 5500 Frequency_Foldback KHz PASS N/A N/A 8.89963087 PASS CpK greater than 1.67 5500.2 Rt_Voltage_Lo 1.3.986K*0.024uA [Calc] V PASS N/A N/A N/A 18.89963087 PASS CpK greater than 1.67 5500.2 St_Threshold_to_stop_charging V PASS N/A N/A N										· ·
5400.2Osc_Med_Hi [Rt=24uA]KHzPASSN/AN/A2.132280992PASSCpK greater than 1.675400.3Rt_Voltage_Hi [Rt=18.2K/K0.4K=13.986K]VPASSN/AN/A28.02125734PASSCpK greater than 1.675400.4Rt_Voltage_Hi + 13.986K*0.024uA [cdc]VPASSN/AN/A20.35839169PASSCpK greater than 1.675500Frequency_FoldbackKHzPASSN/AN/A1.8392347PASSCpK greater than 1.675500.1Rt_Voltage_Lo [Rt=18.2K/K0.4K=13.986K]VPASSN/AN/A1.83993087PASSCpK greater than 1.675500.2Rt_Voltage_Lo + 13.986K*0.024uA [cdc]VPASSN/AN/AN/A18.89963087PASSCpK greater than 1.675500.3St_Threshold_to_stop_chargingVPASSN/AN/AN/A18.89963087PASSCpK greater than 1.675500.4St_Threshold_to_stop_chargingVPASSN/AN/AN/A17.76852255PASSCpK greater than 1.675500.5St_Voltage [BST=IOV]VPASSN/AN/AN/A2.14111E+13PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A17.94026904PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/AN/A2.14111E+13PASSCpK greater than 1.675800.4BST_OK_Threshold [BST-SW]V <t< td=""><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td><td></td></t<>										
5400.3Rt_Voltage Hi [Rt=18.2k//60.4K=13.986K]VPASSN/AN/A28.02125734PASSCpK greater than 1.675400.4Rt_Voltage_Hi + 13.986K*0.024uA [Calc]VPASSN/AN/A20.35839169PASSCpK greater than 1.675500Frequency_FoldbackKHzPASSN/AN/A3.18392347PASSCpK greater than 1.675500.1Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A3.18392347PASSCpK greater than 1.675500.2Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A8.007707PASSCpK greater than 1.675500.2Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A16.8097077PASSCpK greater than 1.675500.3Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A18.89963087PASSCpK greater than 1.675500.4Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A18.89963087PASSCpK greater than 1.675500.5Sthreshold to_stop_chargingVPASSN/AN/AN/A17.76852225PASSCpK greater than 1.675500.4SW voltage [BST=10V]VPASSN/AN/AN/A1.41111+13PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A1.41111+13PASSCpK greater than 1.675800.2BST_OCK_Threshold [BST-SW]VPASS </td <td></td> <td></td> <td></td> <td></td> <td></td> <td>+</td> <td></td> <td></td> <td></td> <td></td>						+				
5400.4Rt_Voltage_lii + 13.986K*0.024uA [Calc]VPASSN/AN/AN/A20.35839169PASSCpK greater than 1.675500Frequency_FoldbackKHzPASSN/AN/AN/A3.18392347PASSCpK greater than 1.675500.1Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/AN/A26.10877077PASSCpK greater than 1.675500.2Rt_Voltage_Lo + 13.986K*0.024uA [Calc]VPASSN/AN/AN/A18.89963087PASSCpK greater than 1.675600SS_Threshold_to_stop_chargingVPASSN/AN/AN/A25.49238544PASSCpK greater than 1.675700PG_High_SW_Pulldown_CurrentmAPASSN/AN/AN/A17.76852225PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A2.1411113PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A2.1411113PASSCpK greater than 1.675800.3BST voltage part switchingVPASSN/AN/AN/A2.14111513PASSCpK greater than 1.675800.4BST voltage part switchingVPASSN/AN/AN/A2.1411113PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A2.14111513PASSCpK greater than 1.676900.1**										
5500Frequency_foldbackKHzPASSN/AN/A3.1839237PASSCpK greater than 1.675500.1Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A26.1087707PASSCpK greater than 1.675500.2Rt_Voltage_Lo + 13.986K*0.024uA [Calc]VPASSN/AN/A18.89963087PASSCpK greater than 1.675600SS_Threshold_to_stop_chargingVPASSN/AN/A18.89963087PASSCpK greater than 1.675700PG_High_SW_Pulldowr_currentMAPASSN/AN/A55.49238544PASSCpK greater than 1.675800SW voltage [BST=10V]VPASSN/AN/AN/A17.7685225PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A17.7685225PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A17.7685225PASSCpK greater than 1.675800.3BST voltage part switchingVPASSN/AN/AN/ASN/A2.1111E+13CpK greater than 1.675800.4BST_VOLTAGE (ISF-ISN=50mV]VPASSN/AN/AN/A19.402604PASSCpK greater than 1.675800.5BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A19.402604PASSCpK greater than 1.675800.4BST_OK_Threshold [BST-SN=50mV]VPASSN/AN/AN							,			
5500.1Rt_voltage_lo [Rt=18.2K//60.4K=13.986K]VPASSN/AN/A26.10877077PASSCpK greater than 1.675500.2Rt_voltage_lo + 13.986K*0.024uA [Calc]VPASSN/AN/A18.89963087PASSCpK greater than 1.675600SS_Threshold_to_stop_chargingVPASSN/AN/AS2.49238544PASSCpK greater than 1.675700PG_High_SW_Pulldown_currentmAPASSN/AN/A17.7685225PASSCpK greater than 1.675800SW voltage [BST=10V]VPASSN/AN/AN/A42.15825584PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A2.14111E+13PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A2.14111E+13PASSCpK greater than 1.676900** IMON ABS MAX CM [ISP-ISN=50mV]VPASSN/AN/AN/A10.6808037PASSCpK greater than 1.676900.1** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A10.6808037PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A2.779762425PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A3.889639753PASSCpK greater than 1.67										
5500.2Rt_Voltage_Lo + 13.986k*0.024uA [Calc]VPASSN/AN/A18.89963087PASSCpK greater than 1.675600SS_Threshold_to_stop_chargingVPASSN/AN/AN/A25.49238544PASSCpK greater than 1.675700PG_High_SW_Pulldown_CurrentmAPASSN/AN/AN/A17.76852225PASSCpK greater than 1.675800SW voltage [BST=10V]VPASSN/AN/AN/A42.15825544PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A2.14111E+13PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A17.94026904PASSCpK greater than 1.676900.1** IMON ABS MAX CM [ISP-ISN=50mV]VPASSN/AN/AN/A10.6808037PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A2.779762425PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/AS.89639753PASSCpK greater than 1.67		· · · -						1		
5600SS_Threshold_to_stop_chargingVPASSN/AN/A25.49238544PASSCpK greater than 1.675700PG_High_SW_Pulldown_CurrentmAPASSN/AN/A17.7685225PASSCpK greater than 1.675800SW voltage [BST=10V]VPASSN/AN/AN/A42.1582584PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A2.14111E+13PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A17.94026904PASSCpK greater than 1.676900** IMON ABS MAX CM [ISP-ISN=50mV]VPASSN/AN/AN/A10.6808037PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A2.779762425PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/AS.89639753PASSCpK greater than 1.67										
5700PG_High_SW_Pulldown_CurrentmAPASSN/AN/A17.7685225PASSCpK greater than 1.675800SW voltage [BST=10V]VPASSN/AN/AN/A42.1582584PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/AN/A2.14111E+13PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A17.94026904PASSCpK greater than 1.676900** IMON ABS MAX CM [ISP-ISN=50mV]VPASSN/AN/AN/A10.6806037PASSCpK greater than 1.676900.1** IMON ABS MAX CM [ISP-ISN=10mV]VPASSN/AN/AN/A2.779762425PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/AS.89639753PASSCpK greater than 1.67										
5800SW voltage [BST=10V]VPASSN/AN/A42.15825584PASSCpK greater than 1.675800.1BST voltage part switchingVPASSN/AN/A2.14111E+13PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A17.94026904PASSCpK greater than 1.676900** IMON ABS MAX CM [ISP-ISN=50mV]VPASSN/AN/AN/A10.6808037PASSCpK greater than 1.676900.1** IMON ABS MAX CM [ISP-ISN=10mV]VPASSN/AN/AN/A2.779762425PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A3.889639753PASSCpK greater than 1.67										
5800.1BST voltage part switchingVPASSN/AN/A2.1411E+13PASSCpK greater than 1.675800.2BST_OK_Threshold [BST-SW]VPASSN/AN/AN/A17.9402694PASSCpK greater than 1.676900** IMON ABS MAX CM [ISP-ISN=50mV]VPASSN/AN/AN/A10.6808037PASSCpK greater than 1.676900.1** IMON ABS MAX CM [ISP-ISN=10mV]VPASSN/AN/AN/A2.779762425PASSCpK greater than 1.676900.2** IMON ABS MAX CM [ISP-ISN=0mV]VPASSN/AN/AN/A3.889639753PASSCpK greater than 1.67										· ·
5800.2 BST_OK_Threshold [BST-SW] V PASS N/A N/A 17.94026904 PASS CpK greater than 1.67 6900 ** IMON ABS MAX CM [ISP-ISN=50mV] V PASS N/A N/A 10.6808037 PASS CpK greater than 1.67 6900.1 ** IMON ABS MAX CM [ISP-ISN=10mV] V PASS N/A N/A 2.779762425 PASS CpK greater than 1.67 6900.2 ** IMON ABS MAX CM [ISP-ISN=0mV] V PASS N/A N/A 3.889639753 PASS CpK greater than 1.67							1	1 1		
6900 ** IMON ABS MAX CM [ISP-ISN=50mV] V PASS N/A N/A 10.68086037 PASS CpK greater than 1.67 6900.1 ** IMON ABS MAX CM [ISP-ISN=10mV] V PASS N/A N/A 2.779762425 PASS CpK greater than 1.67 6900.2 ** IMON ABS MAX CM [ISP-ISN=0mV] V PASS N/A N/A 3.889639753 PASS CpK greater than 1.67			· · ·					1 1		
6900.1 ** IMON ABS MAX CM [ISP-ISN=10mV] V PASs N/A N/A 2.779762425 PASs CpK greater than 1.67 6900.2 ** IMON ABS MAX CM [ISP-ISN=0mV] V PASs N/A N/A 3.889639753 PASs CpK greater than 1.67										
6900.2 ** IMON ABS MAX CM [ISP-ISN=0mV] V PASS N/A N/A 3.889639753 PASS CpK greater than 1.67										
6900.3 ** Isense Voltage ABS MAX CM [CTRL=0.2V] mV PASS N/A N/A 2.976487271 PASS CpK greater than 1.67	6900.2		V	PASS				3.889639753	PASS	
	6900.3	** Isense Voltage ABS MAX CM [CTRL=0.2V]	mV	PASS	N/A		N/A	2.976487271	PASS	CpK greater than 1.67

6900.5	** Isense Voltage ABS MAX CM [CTRL=0.8V]				N/A		N/A	3.337769827	PASS	CpK greater than 1.67
	** Isense Voltage ABS MAX CM [CTRL=1.5V]	mV	PASS		N/A		N/A	3.736442968	PASS	CpK greater than 1.67
7000	Vout Current [Rsen=50mOhm] [Ctrl=0.2V]	mA	PASS		N/A		N/A	6.757618272	PASS	CpK greater than 1.67
7000.1	Vout Current [Rsen=50mOhm] [Ctrl=0.8V]	mA	PASS	0.616179032	PASS	0.984	PASS	0.692839669	N/A	tightened limits
7000.2	Vout Current [Rsen=50mOhm] [Ctrl=1.5V]	mA	PASS		N/A		N/A	11.84916246	PASS	CpK greater than 1.67
7000.3 **	* Isense Voltage High CM [Ctrl=0.2V ISP RampDn	mV	PASS		N/A		N/A	3.351492642	PASS	CpK greater than 1.67
7000.4 **	* Isense Voltage High CM [Ctrl=0.8V ISP RampDn	mV	PASS		N/A		N/A	3.745516194	PASS	CpK greater than 1.67
	* Isense Voltage High CM [Ctrl=1.5V ISP RampDn	mV	PASS		N/A		N/A	2.935994372	PASS	CpK greater than 1.67
7000.7	** IMON High CM [ISN=3.3V,ISP=3.35V]	V	PASS		N/A		N/A	2.365954971	PASS	CpK greater than 1.67
7000.8	** IMON High CM [ISN=3.3V,ISP=3.31V]	V	PASS		N/A		N/A	2.621556678	PASS	CpK greater than 1.67
7000.9	IMON High CM [ISN=3.3V,ISP=3.3V]	V	PASS		N/A		N/A	3.952017915	PASS	CpK greater than 1.67
7000.1	IMON Source Current [ISP-ISN=50mV]	mA	PASS		N/A		N/A	5.324152781	PASS	CpK greater than 1.67
7000.11	IMON Sink Current [ISP-ISN=50mV]	mA	PASS		N/A		N/A	8.42683168	PASS	CpK greater than 1.67
7000.12	IMON Source Current [ISP-ISN=10mV]	mA	PASS		N/A		N/A	6.512447964	PASS	CpK greater than 1.67
7000.13	IMON Sink Current [ISP-ISN=10mV]	mA	PASS		N/A		N/A	6.649624729	PASS	CpK greater than 1.67
7000.14	Vout Current [Rsen=50mOhm] [Ctrl=0.2V]	mA	PASS		N/A		N/A	3.025958886	PASS	CpK greater than 1.67
7000.17 **	** Isense Voltage Low CM [Ctrl=0.2V ISP_RampDn]	mV	PASS		N/A		N/A	3.262651221	PASS	CpK greater than 1.67
	** Isense Voltage Low CM [Ctrl=0.8V ISP_RampDn]	mV	PASS		N/A		N/A	2.546107077	PASS	CpK greater than 1.67
7000.19 **	** Isense Voltage Low CM [Ctrl=1.5V ISP_RampDn]	mV	PASS		N/A		N/A	2.263694105	PASS	CpK greater than 1.67
7000.21	** IMON Lo CM [ISN=0V,ISP=50mV]	V	PASS		N/A		N/A	2.301824177	PASS	CpK greater than 1.67
7000.22	** IMON Lo CM [ISN=0V,ISP=10mV]	V	PASS		N/A		N/A	4.181018945	PASS	CpK greater than 1.67
7000.23	IMON Lo CM [ISN=0V,ISP= 0mV]	V	PASS		N/A		N/A	6.944013647	PASS	CpK greater than 1.67
7000.24	* CTRL pin Current [CTRL=1.5V]	uA	PASS		N/A		N/A	1.93142318	PASS	CpK greater than 1.67
7000.25	** ISN Current 0mVsen High CM	uA	PASS		N/A		N/A	16.32174347	PASS	CpK greater than 1.67
7000.26	** ISP Current 0mVsen High CM	uA	PASS		N/A		N/A	73.73197368	PASS	CpK greater than 1.67
7000.27	** ISN Current 50mVsen High CM	uA	PASS		N/A		N/A	4.529809151	PASS	CpK greater than 1.67
7000.28	** ISP Current 50mVsen High CM	uA	PASS		N/A		N/A	11.05503411	PASS	CpK greater than 1.67
7000.29	** ISN Current 0mVsen Low CM	uA	PASS		N/A		N/A	72.88985213	PASS	CpK greater than 1.67
7000.3	** ISP Current 0mVsen Low CM	uA	PASS		N/A		N/A	1392.031577	PASS	CpK greater than 1.67
7000.31	** ISN Current 50mVsen Low CM	uA	PASS		N/A		N/A	25.84562263	PASS	CpK greater than 1.67
7000.32	** ISP Current 50mVsen Low CM	uA	PASS		N/A		N/A	1135.464248	PASS	CpK greater than 1.67
7000.36	Com Mode Thresholds ISN&ISP RampUp	V	PASS		N/A		N/A	12.89487271	PASS	CpK greater than 1.67
7000.37	Com Mode Thresholds ISN&ISP RampDn	V	PASS		N/A		N/A	9.49504806	PASS	CpK greater than 1.67
7000.38	Com Mode Thresholds_Hyst	V	PASS		N/A		N/A	18.08011754	PASS	CpK greater than 1.67
9000	VCC_cont Damage Check	V	PASS		N/A		N/A	43.61321085	PASS	CpK greater than 1.67
9000.1	VIN_cont Danage Check	V	PASS		N/A		N/A	39.17482311	PASS	CpK greater than 1.67
9000.2	SW_cont Damage Check	V	PASS		N/A		N/A	10.21768538	PASS	CpK greater than 1.67
9000.3	Vin_current Damage Check	uA	PASS		N/A		N/A	18.86284624	PASS	CpK greater than 1.67
9000.4	Vbst_leakage Damage Check	uA	PASS		N/A		N/A	9.989435027	PASS	CpK greater than 1.67
9000.5	Vcc_leakage Damage Check	uA	PASS		N/A		N/A	2.388892654	PASS	CpK greater than 1.67

LT8611_125CA	LT8611_125CA Analysis Data View Report										
Test Number	Test Name	Units	Overall Correlation Result	Mean Diff% Mean diff <5% limit range	Stdv Ratio	Sigma Spread Criteria <1.3	СрК	Cpk >1.67	Annotations		
10.0	VCC_cont	V	PASS	NA		NA	18.68104952	PASS	Cpk greater than 1.67		
10.1	VIN_cont	V	PASS	NA		NA	23.86602197	PASS	Cpk greater than 1.67		
10.2	SW_cont	V	PASS	NA		NA	6.266339288	PASS	Cpk greater than 1.67		
10.3	EN_cont	V	PASS	NA		NA	34.23058737	PASS	Cpk greater than 1.67		
10.8	SYNC_cont	V	PASS	NA		NA	31.73860675	PASS	Cpk greater than 1.67		
10.1	SS_cont	V	PASS	NA		NA	32.57432862	PASS	Cpk greater than 1.67		
10.12	RT_cont [18.2K to APU]	V	PASS	NA		NA	93.27891271	PASS	Cpk greater than 1.67		
10.13	PG_cont	V	PASS	NA		NA	33.4049991	PASS	Cpk greater than 1.67		
10.15	FB_cont	V	PASS	NA		NA	30.90996362	PASS	Cpk greater than 1.67		
10.17	BST_cont	V	PASS	NA		NA	20.99782437	PASS	Cpk greater than 1.67		
10.19	BIAS_cont	V	PASS	NA		NA	30.86492395	PASS	Cpk greater than 1.67		
10.21	IMON_cont	V	PASS	NA		NA	30.92295572	PASS	Cpk greater than 1.67		
10.23	CTRL_cont	V	PASS	NA		NA	30.37164891	PASS	Cpk greater than 1.67		
10.25	ISN_cont	V	PASS	NA		NA	33.415691	PASS	Cpk greater than 1.67		
10.27	ISP_cont	V	PASS	NA		NA	33.71170554	PASS	Cpk greater than 1.67		
10.29	NC_cont	MOhm	PASS	NA		NA	791.6279457	PASS	Cpk greater than 1.67		
940	Vref_Trim_Check [Open Loop]	V	PASS	NA		NA	2.831877536	PASS	Cpk greater than 1.67		
950	** Post-BURN Vout [0.970V] Vin=6V	V	PASS	NA		NA	2.309639677	PASS	Cpk greater than 1.67		
950.1	Post-BURN Vout [0.970V] Vin=40V	V	PASS	NA		NA	3.198961845	PASS	Cpk greater than 1.67		
950.2	Post-BURN OSCF	KHz	PASS	NA		NA	6.435893949	PASS	Cpk greater than 1.67		
950.3	Post-BURN ILIM	mA	PASS	NA		NA	5.729927718	PASS	Cpk greater than 1.67		
950.4	Post-BURN V_IMON	V	PASS	NA		NA	6.795784962	PASS	Cpk greater than 1.67		
950.6	Vref_Trim_Check [Open Loop] [From T940.0]	V	PASS	NA		NA	3.001631386	PASS	Cpk greater than 1.67		
950.7	Delta_of_Vref [T940.0-T950.0]	mV	PASS	NA		NA	5.519490817	PASS	Cpk greater than 1.67		
1000	** lvin_Sleep	uA	PASS	NA		NA	8.471383297	PASS	Cpk greater than 1.67		
1000.1	* len_Sleep	nA	PASS	NA		NA	96.89160327	PASS	Cpk greater than 1.67		
1000.2	Irt_Sleep	uA	PASS	NA		NA	129.4594802	PASS	Cpk greater than 1.67		
1000.3	lss_Sleep	uA	PASS	NA		NA	118.8077541	PASS	Cpk greater than 1.67		
1000.4	Ictrl_Sleep	uA	PASS	NA		NA	144.4859785	PASS	Cpk greater than 1.67		
1000.5	lisp_Sleep	uA	PASS	NA		NA	120.9580407	PASS	Cpk greater than 1.67		
1000.6	lisn_Sleep	uA	PASS	NA		NA	112.1732901	PASS	Cpk greater than 1.67		
1000.7	* lpg_Sleep	nA	PASS	NA		NA	71.9406685	PASS	Cpk greater than 1.67		
1000.8	Ibias Sleep	uA	PASS	NA		NA	32.07801092	PASS	Cpk greater than 1.67		
1000.9	lintvcc_Sleep [INTVCC=4.0V]	uA	PASS	NA		NA	8.444700536	PASS	Cpk greater than 1.67		
1000.12		uA	PASS	NA		NA	9.491193525	PASS	Cpk greater than 1.67		
1000.13	* Ivin_Sleep_with_SYNC	mA	PASS	NA		NA	1.712123451	PASS	Cpk greater than 1.67		
1100.0		uA	PASS	NA		NA	132.0112528	PASS	Cpk greater than 1.67		
1100.1	len_Sleep_ABS_MAX	uA	PASS	NA		NA	269.0778074	PASS	Cpk greater than 1.67		
1100.2	lisp_Sleep_ABS_MAX	uA	PASS	NA		NA	236.8246535	PASS	Cpk greater than 1.67		
1100.3	lisn_Sleep_ABS_MAX	uA	PASS	NA		NA	239.2318041	PASS	Cpk greater than 1.67		
1100.4	lpg_Sleep_ABS_MAX	uA	PASS	NA		NA	381.7874018	PASS	Cpk greater than 1.67		
1100.5	Imon_ABS_MAX	mA	PASS	NA		NA	178.4795931	PASS	Cpk greater than 1.67		
1200	** Ivin Shutdown	uA	PASS	NA		NA	8.410845038	PASS	Cpk greater than 1.67		
1200.1	Irt Shutdown	uA	PASS	NA		NA	128.917458	PASS	Cpk greater than 1.67		
1200.2	lss Shutdown	mA	PASS	NA		NA	212.7771787	PASS	Cpk greater than 1.67		
1200.3	* Isync_Shutdown	nA	PASS	NA		NA	234.4015557	PASS	Cpk greater than 1.67		
1200.4	Ictrl_Shutdown	uA	PASS	NA		NA	135.4994657	PASS	Cpk greater than 1.67		
1200.5	Imon Shutdown	uA	PASS	NA		NA	126.1642995	PASS	Cpk greater than 1.67		
1200.6	lisn Shutdown	uA	PASS	NA		NA	12.9980658	PASS	Cpk greater than 1.67		
1200.7	lisp_Shutdown	uA	PASS	NA		NA	13.31193768	PASS	Cpk greater than 1.67		
1200.8	* Ifb Shutdown	nA	PASS	NA		NA	91.24336906	PASS	Cpk greater than 1.67		
					1		32.2.330300		-F. O. sater than alor		

1200.0	las Chutdaum		DACC		NIA			072 5024744	DACC	California da CZ
1200.9 1200.1	Ipg_Shutdown	mA	PASS PASS		NA NA		NA	873.5931744 37.49688292	PASS	Cpk greater than 1.67
	Ibias_Shutdown	uA					NA	+ +	PASS	Cpk greater than 1.67
1200.11 1200.12	* SS_Pulldown_Resistance ** PG Pulldown Resistance	Ohm Ohm	PASS		NA		NA	27.82937659	PASS	Cpk greater than 1.67
			PASS		NA		NA	33.42847863	PASS	Cpk greater than 1.67
1300	Ivin_Shutdown_ABS_MAX	uA	PASS		NA		NA	37.64671408	PASS	Cpk greater than 1.67
1300.1	Iss_Shutdown_ABS_MAX	mA	PASS		NA		NA	21.93653122	PASS	Cpk greater than 1.67
1300.2 1300.3	lisn_Shutdown_ABS_MAX	uA	PASS		NA		NA	192.5655036	PASS	Cpk greater than 1.67
1300.3	lisp_Shutdown_ABS_MAX Ipg_Shutdown_ABS_MAX	uA mA	PASS PASS		NA NA		NA NA	110.6758409 13.33687285	PASS	Cpk greater than 1.67
	Ibias Shutdown_ABS_MAX		PASS		NA		NA		PASS PASS	Cpk greater than 1.67 Cpk greater than 1.67
1300.5 1300.6		uA uA	PASS		NA		NA	14.64426162		
1300.6	Irt_Shutdown_ABS_MAX * Top_FET_Isw	uA	PASS		NA		NA	3.393251891 54.41050752	PASS PASS	Cpk greater than 1.67 Cpk greater than 1.67
1400	* Bot FET Leakage		PASS					40.77441404	PASS	
		uA	PASS		NA NA		NA NA			Cpk greater than 1.67 Cpk greater than 1.67
1500.1 1600	Bot_FET_AbsMax_Leakage [lbst] ** Regulation_Light_Load_lvin@1mA	uA uA	PASS		NA		NA	165.7842369 7.949489752	PASS PASS	Cpk greater than 1.67 Cpk greater than 1.67
1600.3	** Regulation_Light_Load_lvin@100uA	uA	PASS		NA		NA	8.001612326	PASS	Cpk greater than 1.67
		uA	PASS		NA					
1600.7 1600.8	Regulation_Light_Load_Ivin@1mA [Vout=7V] Vout_1mA [Vout-7V]	UA V	PASS				NA	8.26056906 18.87436839	PASS	Cpk greater than 1.67
2000	Freq with RT=48uA	V KHz	PASS		NA NA		NA	8.579898462	PASS	Cpk greater than 1.67 Cpk greater than 1.67
2000		KHZ V	PASS				NA		PASS	Cpk greater than 1.67 Cpk greater than 1.67
2000.1	RegulationMode Sync=0V ** SW Min Ontime Sync=0V	v nS	PASS		NA NA		NA NA	5.280886329 5.864785175	PASS PASS	Cpk greater than 1.67 Cpk greater than 1.67
	Freg with RT=48uA	KHz						1 1		
2100		V KHZ	PASS		NA		NA	8.566454452	PASS	Cpk greater than 1.67
2100.1	RegulationMode Sync=3.3V		PASS		NA		NA	4.186927733	PASS	Cpk greater than 1.67
2100.2	** SW_Min_Ontime Sync=3.3V	nS	PASS		NA		NA	3.907814522	PASS	Cpk greater than 1.67
2200	* TopRDSon [Vin-Vsw]	Ohm	PASS		NA		NA	5.454228828	PASS	Cpk greater than 1.67
2200.1	V_sw_out@1A before ramp [Debug only]	V	PASS		NA		NA	29.43994077	PASS	Cpk greater than 1.67
2200.2	Slop_Comp_Ilim	mA	PASS		NA		NA	7.083799193	PASS	Cpk greater than 1.67
2300	V_sw_out@1.5A before ramp [Debug only]	V	PASS		NA		NA	23.22281431	PASS	Cpk greater than 1.67
2300.1	** Top_I_Lim	mA	PASS		NA		NA	6.969662048	PASS	Cpk greater than 1.67
2300.2 2300.3	Burst_I_Lim SYNC I Lim	mA	PASS PASS	2 155070410	NA	0.020020254	NA	3.523547798	PASS	Cpk greater than 1.67
	Vout [0.6A load] @Vin=6V	mA V		3.155078418	PASS	0.679872354	PASS	1.36649608	NA	tightened limits
2400 2400.1		V	PASS PASS		NA		NA	15.81975636 10.62163012	PASS PASS	Cpk greater than 1.67
2400.1	** Minimum Input VOltage [Min_Vin_UVLO]	V	PASS	2 524265062	NA PASS	0.056122115	NA	-		Cpk greater than 1.67
	Vout [0.6A load] Drop SW_Min_Ontime Sync=0V [Calc]		PASS	2.524365962		0.956122115	PASS	1.353366107	NA	tightened limits
2400.3		nS			NA		NA	18.69741397	PASS	Cpk greater than 1.67
2400.4 2500	SW_Min_Ontime Sync=3V [Calc] * BotRDSon [Pgnd-Vsw]	nS Ohm	PASS PASS		NA NA		NA	11.45074552	PASS	Cpk greater than 1.67
2500		V	PASS		NA		NA NA	8.066459992	PASS	Cpk greater than 1.67
2500.1	BST pin Voltage thru 1K Zero cross current	mA	PASS		NA		NA	394.0361798 3.564885673	PASS PASS	Cpk greater than 1.67 Cpk greater than 1.67
2600	** DA Current Limit [Bot Lim]		PASS		NA		NA	3.102645322	PASS	Cpk greater than 1.67
2800	SW_Frequency	MA KHz	PASS		NA		NA	3.504118965	PASS	Cpk greater than 1.67
2700	* Min Off Time	nS	PASS		NA NA		NA NA	4.174989148	PASS	Cpk greater than 1.67 Cpk greater than 1.67
2700.1		ns %	PASS		NA NA		NA NA	3.254608992	PASS	Cpk greater than 1.67 Cpk greater than 1.67
	W_duty_cycle							1 1		
2700.3	Dropout Voltage * Vintvcc_0mA_no_bias	V V	PASS		NA NA		NA NA	1.697502829 3.298146149	PASS PASS	Cpk greater than 1.67 Cpk greater than 1.67
2800.1	Vintvcc_0mA_no_bias	V	PASS		NA		NA	14.26222138	PASS	Cpk greater than 1.67 Cpk greater than 1.67
2800.1	* Vintvcc_20mA_no_blas	V	PASS		NA NA			6.344243422	PASS	Cpk greater than 1.67 Cpk greater than 1.67
2900	Vintvcc_0mA_with_bias	V	PASS		NA		NA NA	9.334347285	PASS	
3000.1	Intvcc Ilim no bias [Vccint=3V]	mA	PASS		NA		NA	10.0291581	PASS	Cpk greater than 1.67 Cpk greater than 1.67
3100.1	Intvcc_IIII_IO_Dias [VccIII_SV]	mA	PASS		NA		NA	6.770977539	PASS	Cpk greater than 1.67
3200.1	Intvcc_Ilim_ABSWAA_IO_Blas [Vccint=3V]	mA	PASS		NA		NA	6.377839143	PASS	Cpk greater than 1.67 Cpk greater than 1.67
3300.1	Intvcc_lim_with_bias [vccint=3v]	mA	PASS		NA		NA	23.67274483	PASS	Cpk greater than 1.67 Cpk greater than 1.67
3400	Intvcc BIAS Threshold RampDown	V	PASS		NA		NA	3.445054684	PASS	Cpk greater than 1.67
3400.1	Intvcc_BIAS_Threshold RampUp	V	PASS		NA		NA	2.4896277	PASS	Cpk greater than 1.67
3400.1	Intvcc_BIAS_Threshold Hysteresis	V	PASS		NA		NA	335.2074529	PASS	Cpk greater than 1.67
3500	Intvcc_BAS_Inteshold Hysteresis	V	PASS		NA		NA	9.463173646	PASS	Cpk greater than 1.67
5500		v	FASS		NA		INA	9.4031/3040	FASS	Chk Bigarei filali 1.07

2522.4								
3500.1	Intvcc_Vin_Threshold RampUp	V	PASS	NA	NA	9.207066264	PASS	Cpk greater than 1.67
3500.2	Intvcc_Vin_Threshold Hysteresis	V	PASS	NA	NA	699.2767495	PASS	Cpk greater than 1.67
3600	* Intvcc_UVLO_Threshold RampDown	V	PASS	NA	NA	4.855015526	PASS	Cpk greater than 1.67
3600.1	Intvcc_UVLO_Threshold RampUp	V	PASS	NA	NA	11.6303389	PASS	Cpk greater than 1.67
3600.2	Intvcc_UVLO_Threshold Hysteresis	V	PASS	NA	NA	54.73189904	PASS	Cpk greater than 1.67
4000	EN_Threshold RampDown	V	PASS	NA	NA	31.61489148	PASS	Cpk greater than 1.67
4000.1	** EN_Threshold RampUp	V	PASS	NA	NA	2.928357159	PASS	Cpk greater than 1.67
4000.2	* EN_Threshold Hysteresis	V	PASS	NA	NA	14.0128833	PASS	Cpk greater than 1.67
4100	PG_pin_Low_Threshold RampDown	V	PASS	NA	NA	28.65164085	PASS	Cpk greater than 1.67
4100.1	PG_pin_Low_Threshold RampUp	V	PASS	NA	NA	29.77398434	PASS	Cpk greater than 1.67
4100.2	* PG_pin_Low_Threshold Hysteresis	V	PASS	NA	NA	1581.439812	PASS	Cpk greater than 1.67
4100.3	* PG Lower Threshold Offset from VFB	%	PASS	NA	NA	2.201713275	PASS	Cpk greater than 1.67
4100.4	* PG Low Hysteresis	%	PASS	NA	NA	10.09511314	PASS	Cpk greater than 1.67
4200	PG_pin_High_Threshold RampDown	V	PASS	NA	NA	38.4777137	PASS	Cpk greater than 1.67
4200.1	PG_pin_High_Threshold RampUp	V	PASS	NA	NA	39.50515184	PASS	Cpk greater than 1.67
4200.2	* PG_pin_High_Threshold Hysteresis	V	PASS	NA	NA	1613.086262	PASS	Cpk greater than 1.67
4200.3	* PG Upper Threshold Offset from VFB	%	PASS	NA	NA	1.700980381	PASS	Cpk greater than 1.67
4200.4	* PG Hi Hysteresis	%	PASS	NA	NA	10.76543153	PASS	Cpk greater than 1.67
4300	* SYNC Threshold RampDown	V	PASS	NA	NA	14.82540518	PASS	Cpk greater than 1.67
4300.1	* SYNC Threshold RampUp	V	PASS	NA	NA	12.33066594	PASS	Cpk greater than 1.67
4300.2	SYN Threshold Hysteresis	v	PASS	NA	NA	24.78855039	PASS	Cpk greater than 1.67
4500	Feedback Reference Voltage [Vin=12V, ILoad=0.5A]		PASS	NA	NA	29.82206684	PASS	Cpk greater than 1.67
4500.1	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS	NA NA	NA	29.72085623	PASS	Cpk greater than 1.67
4500.2	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS	NA NA	NA	29.7134784	PASS	Cpk greater than 1.67
4500.2	** Feedback Voltage Line Regulation	v %/V	PASS	NA NA	NA	10.40277471	PASS	Cpk greater than 1.67
		76/ V	PASS					
4500.4	Reference Voltage [Vin=12V, ILoad=0.1A]	V		NA	NA	29.38278608	PASS	Cpk greater than 1.67
4500.5	Reference Voltage [Vin=12V, ILoad=2.5A]		PASS	NA	NA	15.53733607	PASS	Cpk greater than 1.67
4500.6	Feedback Voltage Load Regulation	%	PASS	NA	NA	9.651334091	PASS	Cpk greater than 1.67
4800	* BIAS_pin_Current_Consumption	mA	PASS	NA	NA	16.17331086	PASS	Cpk greater than 1.67
4900	Regulating_with_SS	V	PASS	NA	NA	8.392816318	PASS	Cpk greater than 1.67
5000	** SS_Pin_Current	uA	PASS	NA	NA	4.428651916	PASS	Cpk greater than 1.67
5100	** Datasheet_Osc_High [Rt=18.2K]	KHz	PASS	NA	NA	2.120315028	PASS	Cpk greater than 1.67
5100.1	I_Vin_Rt18K	mA	PASS	NA	NA	95.91516372	PASS	Cpk greater than 1.67
5100.2	Vout_Rt18K	V	PASS	NA	NA	80.86484144	PASS	Cpk greater than 1.67
5100.3	Efficiency_Rt18K		PASS	NA	NA	18.75000852	PASS	Cpk greater than 1.67
5200	** Datasheet_Osc_Low [Rt=60.4K]	KHz	PASS	NA	NA	3.928105144	PASS	Cpk greater than 1.67
5200.1	I_Vin_Rt60K	mA	PASS	NA	NA	113.5695354	PASS	Cpk greater than 1.67
5200.2	Vout_Rt60K	V	PASS	NA	NA	80.30820346	PASS	Cpk greater than 1.67
5200.3	Efficiency_Rt60K		PASS	NA	NA	16.09326497	PASS	Cpk greater than 1.67
5300	SYNC_Frequency [Sync=1MHz]	KHz	PASS	NA	NA	277.8556431	PASS	Cpk greater than 1.67
5300.1	SYNC_Frequency [Sync=2.2MHz]	KHz	PASS	NA	NA	190.5260783	PASS	Cpk greater than 1.67
5300.2	SYNC_Frequency [Sync=200KHz]	KHz	PASS	NA	NA	5053.042931	PASS	Cpk greater than 1.67
5400	** Datasheet_Osc_Low [Rt=221K]	KHz	PASS	NA	NA	4.365517537	PASS	Cpk greater than 1.67
5400.1	Osc_Low [Rt=3.8uA]	KHz	PASS	NA	NA	19.55861526	PASS	Cpk greater than 1.67
5400.2	Osc_Med_Hi [Rt=24uA]	KHz	PASS	NA	NA	4.200735536	PASS	Cpk greater than 1.67
5400.3	Rt_Voltage_Hi [Rt=18.2K//60.4K=13.986K]	V	PASS	NA	NA	26.49412206	PASS	Cpk greater than 1.67
5400.4	Rt_Voltage_Hi + 13.986K*0.024uA [Calc]	V	PASS	NA	NA	19.26020413	PASS	Cpk greater than 1.67
5500	Frequency_Foldback	KHz	PASS	NA	NA	3.629584601	PASS	Cpk greater than 1.67
5500.1	Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]	V	PASS	NA	NA	25.93971996	PASS	Cpk greater than 1.67
5500.2	Rt_Voltage_Lo + 13.986K*0.024uA [Calc]	V	PASS	NA	NA	18.84498423	PASS	Cpk greater than 1.67
5600	SS_Threshold_to_stop_charging	V	PASS	NA	NA	17.28364008	PASS	Cpk greater than 1.67
5700	PG High SW Pulldown Current	mA	PASS	NA	NA	14.82751615	PASS	Cpk greater than 1.67
5800	SW voltage [BST=10V]	V	PASS	NA	NA	34.41726994	PASS	Cpk greater than 1.67
5800.1	BST voltage part switching	V	PASS	NA	NA	8.665934469	PASS	Cpk greater than 1.67
5800.2	BST_OK_Threshold [BST-SW]	V	PASS	NA	NA	4.586420039	PASS	Cpk greater than 1.67
6900	** IMON ABS MAX CM [ISP-ISN=50mV]	V	PASS	NA NA	NA	10.27838242	PASS	Cpk greater than 1.67
0500		*	1735		I NA	10.27030242	1 435	leby Preater man 107

6900.1	** IMON ABS MAX CM [ISP-ISN=10mV]	V	PASS		NA		NA	5.140779549	PASS	Cpk greater than 1.67
6900.2	** IMON ABS MAX CM [ISP-ISN=10HV]	V	PASS		NA		NA	8.396377277	PASS	Cpk greater than 1.67
6900.3	** Isense Voltage ABS MAX CM [CTRL=0.2V]	mV	PASS		NA		NA	4.120430981	PASS	Cpk greater than 1.67
6900.4	** Isense Voltage ABS MAX CM [CTRL=0.2V]	mV	PASS		NA	+	NA	5.679165461	PASS	Cpk greater than 1.67
					NA NA		NA			
6900.5 7000	** Isense Voltage ABS MAX CM [CTRL=1.5V]	mV	PASS PASS					9.070376451	PASS	Cpk greater than 1.67
	Vout Current [Rsen=50mOhm] [Ctrl=0.2V]	mA		2.445200547	NA	0.624600720	NA	6.985706005	PASS	Cpk greater than 1.67
7000.1	Vout Current [Rsen=50mOhm] [Ctrl=0.8V]	mA	PASS	2.115389547	PASS	0.624689729	PASS	0.833650278	NA	tightened limits
7000.2	Vout Current [Rsen=50mOhm] [Ctrl=1.5V]	mA	PASS		NA		NA	9.38626567	PASS	Cpk greater than 1.67
7000.3	** Isense Voltage High CM [Ctrl=0.2V ISP_RampDn]	mV	PASS		NA		NA	3.428680811	PASS	Cpk greater than 1.67
7000.4	** Isense Voltage High CM [Ctrl=0.8V ISP_RampDn]	mV	PASS		NA		NA	3.924894988	PASS	Cpk greater than 1.67
7000.5	** Isense Voltage High CM [Ctrl=1.5V ISP_RampDn]		PASS		NA		NA	2.297003114	PASS	Cpk greater than 1.67
7000.7	** IMON High CM [ISN=3.3V,ISP=3.35V]	V	PASS		NA		NA	2.104437011	PASS	Cpk greater than 1.67
7000.8	** IMON High CM [ISN=3.3V,ISP=3.31V]	V	PASS		NA		NA	3.157830107	PASS	Cpk greater than 1.67
7000.9	IMON High CM [ISN=3.3V,ISP=3.3V]	V	PASS	ļ	NA		NA	7.502909177	PASS	Cpk greater than 1.67
7000.1	IMON Source Current [ISP-ISN=50mV]	mA	PASS		NA		NA	24.68044754	PASS	Cpk greater than 1.67
7000.11	IMON Sink Current [ISP-ISN=50mV]	mA	PASS		NA		NA	24.71721626	PASS	Cpk greater than 1.67
7000.12	IMON Source Current [ISP-ISN=10mV]	mA	PASS		NA		NA	8.280094158	PASS	Cpk greater than 1.67
7000.13	IMON Sink Current [ISP-ISN=10mV]	mA	PASS		NA		NA	8.261085163	PASS	Cpk greater than 1.67
7000.14	Vout Current [Rsen=50mOhm] [Ctrl=0.2V]	mA	PASS		NA		NA	3.354886602	PASS	Cpk greater than 1.67
7000.17	** Isense Voltage Low CM [Ctrl=0.2V ISP_RampDn]	mV	PASS		NA		NA	3.729602767	PASS	Cpk greater than 1.67
7000.18	** Isense Voltage Low CM [Ctrl=0.8V ISP_RampDn]	mV	PASS		NA		NA	2.919266778	PASS	Cpk greater than 1.67
7000.19	** Isense Voltage Low CM [Ctrl=1.5V ISP_RampDn]	mV	PASS		NA		NA	2.649329805	PASS	Cpk greater than 1.67
7000.21	** IMON Lo CM [ISN=0V,ISP=50mV]	V	PASS		NA		NA	2.519549435	PASS	Cpk greater than 1.67
7000.22	** IMON Lo CM [ISN=0V,ISP=10mV]	V	PASS		NA		NA	4.287492124	PASS	Cpk greater than 1.67
7000.23	IMON Lo CM [ISN=0V,ISP= 0mV]	V	PASS		NA		NA	11.26652808	PASS	Cpk greater than 1.67
7000.24	* CTRL pin Current [CTRL=1.5V]	uA	PASS		NA		NA	4.671729874	PASS	Cpk greater than 1.67
7000.25	** ISN Current OmVsen High CM	uA	PASS		NA		NA	17.11288906	PASS	Cpk greater than 1.67
7000.26	** ISP Current 0mVsen High CM	uA	PASS		NA		NA	72.34623552	PASS	Cpk greater than 1.67
7000.27	** ISN Current 50mVsen High CM	uA	PASS		NA		NA	5.098019624	PASS	Cpk greater than 1.67
7000.28	** ISP Current 50mVsen High CM	uA	PASS		NA		NA	10.56069911	PASS	Cpk greater than 1.67
7000.29	** ISN Current 0mVsen Low CM	uA	PASS		NA		NA	71.06155985	PASS	Cpk greater than 1.67
7000.3	** ISP Current 0mVsen Low CM	uA	PASS		NA		NA	1328.289903	PASS	Cpk greater than 1.67
7000.31	** ISN Current 50mVsen Low CM	uA	PASS		NA		NA	28.08030741	PASS	Cpk greater than 1.67
7000.32	** ISP Current 50mVsen Low CM	uA	PASS		NA		NA	1478.642546	PASS	Cpk greater than 1.67
7000.36	Com Mode Thresholds ISN&ISP RampUp	V	PASS		NA		NA	14.19200568	PASS	Cpk greater than 1.67
7000.37	Com Mode Thresholds ISN&ISP RampDn	V	PASS		NA		NA	10.33234767	PASS	Cpk greater than 1.67
7000.38	Com Mode Thresholds_Hyst	V	PASS		NA		NA	18.45084617	PASS	Cpk greater than 1.67
9000	VCC cont Damage Check	V	PASS		NA		NA	21.6656741	PASS	Cpk greater than 1.67
9000.1	VIN cont Danage Check	V	PASS		NA		NA	27.10613713	PASS	Cpk greater than 1.67
9000.2	SW cont Damage Check	V	PASS		NA		NA	6.651117145	PASS	Cpk greater than 1.67
9000.3	Vin current Damage Check	uA	PASS		NA		NA	63.85132154	PASS	Cpk greater than 1.67
9000.4	Vbst_leakage Damage Check	uA	PASS	<u> </u>	NA	+	NA	39.14480897	PASS	Cpk greater than 1.67
9000.5	Vcc leakage Damage Check	uA	PASS		NA	+	NA	3.001667157	PASS	Cpk greater than 1.67
3000.5	VCC_IEdkage Daillage Clieck	uA	FASS	ļ	INA		INA	3.00100/13/	FA33	

LT861140C_C	QA Analysis Data View Report									
Test Number	Test Name	Units	Overall Correlation Result	Mean Diff%	Mean diff <5% limit range	Stdv Ratio	Sigma Spread Criteria <1.3	СрК	Cpk >1.67	Annotations
10	VCC_cont	V	PASS		N/A		N/A	47.3554444	PASS	
10.1	 VIN_cont	V	PASS		N/A		N/A	48.13570841	PASS	
10.2	 SW_cont	V	PASS		N/A		N/A	14.21105131	PASS	
10.3	EN cont	v	PASS		N/A		N/A	29.55280177	PASS	
10.8	SYNC cont	V	PASS		N/A		N/A	16.0422588	PASS	
10.1	 SS cont	v	PASS		N/A		N/A	23.7589948	PASS	
10.12		v	PASS		N/A		N/A	221.9725064	PASS	
10.13	PG_cont	V	PASS		N/A		N/A	39.78594944	PASS	
10.15	 FB_cont	v	PASS		N/A		N/A	16.48141508	PASS	
10.17	BST cont	v	PASS		N/A		N/A	80.6006564	PASS	
10.19	BIAS cont	v	PASS		N/A		N/A	37.54005361	PASS	
10.21	IMON cont	v	PASS		N/A		N/A	14.31651201	PASS	
10.23	 CTRL_cont	V	PASS		N/A		N/A	15.90484181	PASS	
10.25	ISN cont	v	PASS		N/A		N/A	32.93284395	PASS	
10.27	ISP cont	v	PASS		N/A	İ	N/A	38.92906001	PASS	
10.29	NC cont	MOhm	PASS		N/A		N/A	793.5909058	PASS	
940	Vref_Trim_Check [Open Loop]	V	PASS		N/A	İ	N/A	2.683925049	PASS	
950	** Post-BURN Vout [0.970V] Vin=6V	v	PASS		N/A		N/A	2.071687261	PASS	
950.1	Post-BURN Vout [0.970V] Vin=40V	V	PASS		N/A		N/A	3.037651952	PASS	
950.2	Post-BURN OSCF	KHz	PASS		N/A		N/A	5.34667494	PASS	
950.3	Post-BURN ILIM	mA	PASS		N/A		N/A	4.701430546	PASS	
950.4	Post-BURN V IMON	V	PASS		N/A		N/A	5.621620732	PASS	
950.6	Vref Trim Check [Open Loop] [From T940.0]	v	PASS		N/A		N/A	2.866926646	PASS	
950.7	Delta of Vref [T940.0-T950.0]	mV	PASS		N/A		N/A	6.859592604	PASS	
1000	** Ivin Sleep	uA	PASS		N/A		N/A	6.193351491	PASS	
1000.1	* len_Sleep	nA	PASS		N/A		N/A	219.8346893	PASS	
1000.2	Irt_Sleep	uA	PASS		N/A		N/A	135.5088768	PASS	
1000.3	lss_Sleep	uA	PASS		N/A		N/A	120.6736881	PASS	
1000.4	Ictrl_Sleep	uA	PASS		N/A		N/A	137.4244114	PASS	
1000.5	lisp_Sleep	uA	PASS		N/A		N/A	112.1747006	PASS	
1000.6	lisn_Sleep	uA	PASS		N/A		N/A	110.5546318	PASS	
1000.7	* Ipg_Sleep	nA	PASS		N/A		N/A	50.88851383	PASS	
1000.8	Ibias_Sleep	uA	PASS		N/A		N/A	37.07110563	PASS	
1000.9	lintvcc_Sleep [INTVCC=4.0V]	uA	PASS		N/A		N/A	10.09099819	PASS	
1000.12	lbst_Sleep	uA	PASS		N/A		N/A	16.94868963	PASS	
1000.12	* Ivin Sleep with SYNC	mA	PASS	1.621846286	PASS	0.981383917	PASS	1.305045722	N/A	
1100	lvin_Sleep_ABS_MAX	uA	PASS	1.021040200	N/A	0.501505517	N/A	154.9537706	PASS	
1100.1	len_Sleep_ABS_MAX	uA	PASS		N/A		N/A	253.9415392	PASS	
1100.2	lisp_Sleep_ABS_MAX	uA	PASS		N/A		N/A	232.5703257	PASS	
1100.2	lisn_Sleep_ABS_MAX	uA	PASS		N/A N/A		N/A	253.5599545	PASS	
1100.3	Ipg_Sleep_ABS_MAX	uA	PASS		N/A N/A		N/A	387.3663653	PASS	
1100.4	Imon_ABS_MAX	mA	PASS		N/A N/A		N/A	167.7177395	PASS	
1200	** Ivin_Shutdown	uA	PASS		N/A N/A		N/A	5.954247028	PASS	
1200.1	Irt Shutdown	uA	PASS		N/A N/A		N/A	141.8806681	PASS	
1200.1	Iss_Shutdown	mA	PASS		N/A N/A		N/A	163.3492153	PASS	
1200.2	* Isync Shutdown	nA	PASS		N/A N/A		N/A N/A	493.4505269	PASS	
1200.3	Ictrl Shutdown	uA	PASS		N/A N/A		N/A N/A	131.9083388	PASS	
1200.4	Imon Shutdown	uA	PASS		N/A N/A		N/A N/A	89.05602	PASS	
1200.5	lisn_Shutdown	uA	PASS		N/A N/A		N/A N/A	12.40135501	PASS	
1200.8	lisp Shutdown	uA	PASS		N/A N/A		N/A N/A	12.40135501	PASS	
1200.7	* Ifb Shutdown	nA	PASS		N/A N/A		N/A N/A	124.9428224	PASS	
1200.8	Ipg_Shutdown	mA	PASS		N/A N/A		N/A N/A	493.397587	PASS	
1200.9	Ibias Shutdown	uA	PASS		N/A N/A		N/A N/A	493.397587	PASS	
1200.1	* SS Pulldown Resistance	Ohm	PASS		N/A N/A			1		
1200.11	- SS_Pulluown_Kesistance		PASS		IN/A	ļ	N/A	29.96741478	PASS	

1000.10										
1200.12	** PG_Pulldown_Resistance	Ohm	PASS		N/A		N/A	24.05171697	PASS	
1300	Ivin_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	49.532422	PASS	
1300.1	Iss_Shutdown_ABS_MAX	mA	PASS		N/A		N/A	23.65583948	PASS	
1300.2	lisn_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	136.7085433	PASS	
1300.3	lisp_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	100.3887731	PASS	
1300.4	Ipg_Shutdown_ABS_MAX	mA	PASS		N/A		N/A	6.246849101	PASS	
1300.5	Ibias_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	12.90165571	PASS	
1300.6	Irt_Shutdown_ABS_MAX	uA	PASS		N/A		N/A	5.054116991	PASS	
1400	* Top_FET_Isw	uA	PASS		N/A		N/A	69.00201208	PASS	
1500	* Bot_FET_Leakage	uA	PASS		N/A		N/A	55.33808364	PASS	
1500.1	Bot_FET_AbsMax_Leakage [Ibst]	uA	PASS		N/A		N/A	166.2310879	PASS	
1600	** Regulation Light Load Ivin@1mA	uA	PASS		N/A		N/A	2.005816047	PASS	
1600.3	** Regulation_Light_Load_lvin@100uA	uA	PASS		N/A		N/A	3.17292849	PASS	
1600.7	Regulation_Light_Load_lvin@1mA [Vout=7V]	uA	PASS		N/A		N/A	2.373631883	PASS	
1600.8	Vout 1mA [Vout-7V]	V	PASS		N/A		N/A	20.73366558	PASS	
2000	Freq with RT=48uA	KHz	PASS		N/A		N/A	9.534816115	PASS	
2000.1	RegulationMode Sync=0V	V	PASS		N/A		N/A	6.354202163	PASS	
2000.1	** SW Min Ontime Sync=0V	nS	PASS		N/A N/A		N/A N/A	2.371763379	PASS	
			PASS							
2100	Freq with RT=48uA	KHz			N/A		N/A	9.52239964	PASS	
2100.1	RegulationMode Sync=3.3V	V	PASS		N/A		N/A	6.56069803	PASS	
2100.2	** SW_Min_Ontime Sync=3.3V	nS	PASS		N/A		N/A	4.795987651	PASS	
2200	* TopRDSon [Vin-Vsw]	Ohm	PASS		N/A		N/A	3.249703362	PASS	
2200.1	V_sw_out@1A before ramp [Debug only]	V	PASS		N/A		N/A	37.21269867	PASS	
2200.2	Slop_Comp_Ilim	mA	PASS		N/A		N/A	5.956091449	PASS	
2300	V_sw_out@1.5A before ramp [Debug only]	V	PASS		N/A		N/A	17.16699372	PASS	
2300.1	** Top_I_Lim	mA	PASS		N/A		N/A	3.971375525	PASS	
2300.2	Burst_I_Lim	mA	PASS		N/A		N/A	1.804998173	PASS	
2300.3	SYNC_I_Lim	mA	PASS		N/A		N/A	8.037436692	PASS	
2400	Vout [0.6A load] @Vin=6V	V	PASS		N/A		N/A	11.3308567	PASS	
2400.1	** Minimum Input VOltage [Min_Vin_UVLO]	V	PASS		N/A		N/A	3.206094461	PASS	
2400.2	Vout [0.6A load] Drop	V	PASS	3.64791463	PASS	1.027102425	PASS	0.785243475	N/A	
2400.3	SW Min Ontime Sync=0V [Calc]	nS	PASS		N/A		N/A	14.14854278	PASS	
2400.4	SW_Min_Ontime Sync=3V [Calc]	nS	PASS		N/A		N/A	15.02733203	PASS	
2500	* BotRDSon [Pgnd-Vsw]	Ohm	PASS		N/A		N/A	3.277571204	PASS	
2500.1	BST pin Voltage thru 1K	V	PASS		N/A		N/A	294.5417104	PASS	
2500.2	Zero_cross_current	mA	PASS		N/A		N/A	2.070723166	PASS	
2600	** DA_Current_Limit [Bot_I_Lim]	mA	PASS	1.191520594	PASS	1.056133794	PASS	1.201615638	N/A	
2700	SW Frequency	KHz	PASS	1.191520594	N/A	1.050155794	N/A	2.406890704	PASS	
2700	* Min Off Time	nS	PASS		N/A		N/A	3.642286348	PASS	
2700.2	W_duty_cycle	%	PASS		N/A		N/A	2.629750922	PASS	
2700.3	Dropout Voltage	V	PASS		N/A		N/A	2.986270354	PASS	
2800	* Vintvcc_0mA_no_bias	V	PASS		N/A		N/A	3.306412293	PASS	
2800.1	Vintvcc_20mA_no_bias	V	PASS		N/A		N/A	22.70527675	PASS	
2900	* Vintvcc_0mA_with_bias	V	PASS		N/A		N/A	14.30519681	PASS	
2900.1	Vintvcc_20mA_with_bias	V	PASS		N/A		N/A	9.022710886	PASS	
3000.1	Intvcc_Ilim_no_bias [Vccint=3V]	mA	PASS		N/A		N/A	12.35429383	PASS	
3100.1	Intvcc_Ilim_ABSMAX_no_bias [Vccint=3V]	mA	PASS		N/A		N/A	7.129841702	PASS	
3200.1	Intvcc_Ilim_with_bias [Vccint=3V]	mA	PASS		N/A		N/A	7.342985575	PASS	
3300.1	Intvcc_Ilim_ABSMAX_with_bias [Vccint=3V]	mA	PASS		N/A		N/A	18.4684145	PASS	
3400	Intvcc_BIAS_Threshold RampDown	V	PASS		N/A		N/A	4.231665205	PASS	
3400.1	Intvcc_BIAS_Threshold RampUp	V	PASS		N/A		N/A	2.646550459	PASS	
3400.2	Intvcc_BIAS_Threshold Hysteresis	V	PASS		N/A		N/A	280.1459868	PASS	
3500	Intvcc Vin Threshold RampDown	v	PASS		N/A		N/A	7.599877641	PASS	
3500.1	Intvcc Vin Threshold RampUp	v	PASS		N/A		N/A	7.077784857	PASS	
3500.2	Intvcc Vin Threshold Hysteresis	v	PASS		N/A		N/A	936.563655	PASS	
3600	* Intvcc_UVLO_Threshold RampDown	V	PASS		N/A		N/A N/A	2.517287255	PASS	
3600.1	Intvcc_UVLO_Threshold RampUp	V	PASS		N/A N/A		N/A N/A	8.036863254	PASS	
		V	PASS		N/A N/A					
3600.2	Intvcc_UVLO_Threshold Hysteresis						N/A	50.05394006	PASS	
4000	EN_Threshold RampDown	V	PASS		N/A		N/A	30.55638413	PASS	

1000.1		V	DAGG		N1/A		N1/A	2 452752462	DACC	
4000.1	** EN_Threshold RampUp	V	PASS		N/A		N/A	3.153753163	PASS	
4000.2	* EN_Threshold Hysteresis	V	PASS		N/A		N/A	11.25959282	PASS	
4100	PG_pin_Low_Threshold RampDown	V	PASS		N/A		N/A	28.05050612	PASS	
4100.1	PG_pin_Low_Threshold RampUp	V	PASS		N/A		N/A	29.21149432	PASS	
4100.2	* PG_pin_Low_Threshold Hysteresis	V	PASS		N/A		N/A	1147.736224	PASS	
4100.3	* PG Lower Threshold Offset from VFB	%	PASS		N/A		N/A	1.912047142	PASS	
4100.4	* PG Low Hysteresis	%	PASS		N/A		N/A	8.12841587	PASS	
4200	PG_pin_High_Threshold RampDown	V	PASS		N/A		N/A	40.77059208	PASS	
4200.1	PG_pin_High_Threshold RampUp	V	PASS		N/A		N/A	41.46706291	PASS	
4200.2	* PG_pin_High_Threshold Hysteresis	V	PASS		N/A		N/A	1276.242225	PASS	
4200.3	* PG Upper Threshold Offset from VFB	%	PASS		N/A		N/A	1.724937041	PASS	
4200.4	* PG Hi Hysteresis	%	PASS		N/A		N/A	8.81228132	PASS	
4300	* SYNC Threshold RampDown	V	PASS		N/A		N/A	14.64235933	PASS	
4300.1	* SYNC Threshold RampUp	V	PASS		N/A		N/A	10.66399327	PASS	
4300.2	SYN_Threshold Hysteresis	V	PASS		N/A		N/A	20.75576504	PASS	
4500	Feedback Reference Voltage [Vin=12V, ILoad=0.5A]	V	PASS		N/A		N/A	32.61493787	PASS	
4500.1	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS		N/A		N/A	32.02738736	PASS	
4500.2	Reference Voltage [Vin=40V, ILoad=0.5A]	V	PASS		N/A		N/A	32.19429133	PASS	
4500.3	** Feedback Voltage Line Regulation	%/V	PASS		N/A		N/A	10.97785893	PASS	
4500.3	Reference Voltage [Vin=12V, ILoad=0.1A]	70/ V	PASS		N/A		N/A N/A	32.12067816	PASS	
4500.4	Reference Voltage [Vin=12V, ILoad=0.1A]	V	PASS		N/A N/A		N/A N/A	22.47560271	PASS	
4500.6	Feedback Voltage Load Regulation	%	PASS		N/A		N/A	18.68951082	PASS	
4800	* BIAS_pin_Current_Consumption	mA	PASS		N/A		N/A	14.747264	PASS	
4900	Regulating_with_SS	V	PASS		N/A		N/A	7.797699709	PASS	
5000	** SS_Pin_Current	uA	PASS		N/A		N/A	3.603761239	PASS	
5100	** Datasheet_Osc_High [Rt=18.2K]	KHz	PASS		N/A		N/A	2.164836709	PASS	
5100.1	I_Vin_Rt18K	mA	PASS		N/A		N/A	118.151124	PASS	
5100.2	Vout_Rt18K	V	PASS		N/A		N/A	57.0278549	PASS	
5100.3	Efficiency_Rt18K		PASS		N/A		N/A	10.01352015	PASS	
5200	<pre>** Datasheet_Osc_Low [Rt=60.4K]</pre>	KHz	PASS		N/A		N/A	3.889197909	PASS	
5200.1	I_Vin_Rt60K	mA	PASS		N/A		N/A	112.4514488	PASS	
5200.2	Vout_Rt60K	V	PASS		N/A		N/A	57.00522677	PASS	
5200.3	Efficiency_Rt60K		PASS		N/A		N/A	7.810263022	PASS	
5300	SYNC_Frequency [Sync=1MHz]	KHz	PASS		N/A		N/A	282.998486	PASS	
5300.1	SYNC_Frequency [Sync=2.2MHz]	KHz	PASS		N/A		N/A	156.4127888	PASS	
5300.2	SYNC_Frequency [Sync=200KHz]	KHz	PASS		N/A		N/A	1466.674751	PASS	
5400	** Datasheet Osc Low [Rt=221K]	KHz	PASS		N/A		N/A	2.39600072	PASS	
5400.1	Osc_Low [Rt=3.8uA]	KHz	PASS		N/A		N/A	12.31762004	PASS	
5400.2	Osc_Med_Hi [Rt=24uA]	KHz	PASS		N/A		N/A	5.349672728	PASS	
5400.3	Rt Voltage Hi [Rt=18.2K//60.4K=13.986K]	V	PASS		N/A		N/A	25.93269498	PASS	
5400.4	Rt_Voltage_Hi + 13.986K*0.024uA [Calc]	V	PASS		N/A		N/A	19.10928864	PASS	
5500	Frequency_Foldback	KHz	PASS		N/A		N/A	2.903794718	PASS	
5500.1	Rt Voltage Lo [Rt=18.2K//60.4K=13.986K]	V	PASS		N/A		N/A	25.14836067	PASS	
5500.2	Rt Voltage Lo + 13.986K*0.024uA [Calc]	V	PASS		N/A		N/A N/A	18.62539318	PASS	
5600	SS Threshold to stop charging	V	PASS		N/A		N/A N/A	28.45734584	PASS	
5700	PG_High_SW_Pulldown_Current	mA	PASS		N/A N/A		N/A N/A	18.50615457	PASS	
		V			-					
5800	SW voltage [BST=10V]	V	PASS		N/A		N/A	35.29251706	PASS	
5800.1	BST voltage part switching		PASS		N/A		N/A	25.13255494	PASS	
5800.2	BST_OK_Threshold [BST-SW]	V	PASS		N/A		N/A	11.7416352	PASS	
6900	** IMON ABS MAX CM [ISP-ISN=50mV]	V	PASS		N/A		N/A	11.00288466	PASS	
6900.1	** IMON ABS MAX CM [ISP-ISN=10mV]	V	PASS		N/A		N/A	4.31766726	PASS	
6900.2	** IMON ABS MAX CM [ISP-ISN=0mV]	V	PASS		N/A		N/A	3.157551705	PASS	
6900.3	** Isense Voltage ABS MAX CM [CTRL=0.2V]	mV	PASS		N/A		N/A	3.5439596	PASS	
6900.4	** Isense Voltage ABS MAX CM [CTRL=0.8V]	mV	PASS		N/A		N/A	5.895484274	PASS	
6900.5	** Isense Voltage ABS MAX CM [CTRL=1.5V]	mV	PASS		N/A		N/A	10.05791972	PASS	
7000	Vout Current [Rsen=50mOhm] [Ctrl=0.2V]	mA	PASS		N/A		N/A	5.053964883	PASS	
7000.1	Vout Current [Rsen=50mOhm] [Ctrl=0.8V]	mA	PASS	3.698532452	PASS	1.170491404	PASS	0.694390295	N/A	
7000.2	Vout Current [Rsen=50mOhm] [Ctrl=1.5V]	mA	PASS		N/A		N/A	10.15845696	PASS	
	** Isense Voltage High CM [Ctrl=0.2V ISP RampDn]	mV	PASS		N/A		N/A	2.591112515	PASS	

7000.4	** Isense Voltage High CM [Ctrl=0.8V ISP_RampDn]	mV	PASS	N/A	N/A	2.889629202	PASS	
7000.5	** Isense Voltage High CM [Ctrl=1.5V ISP RampDn]	mV	PASS	N/A	N/A	1.867985179	PASS	
7000.7	** IMON High CM [ISN=3.3V,ISP=3.35V]	V	PASS	N/A	N/A	2.169678675	PASS	
7000.8	** IMON High CM [ISN=3.3V,ISP=3.31V]	V	PASS	N/A	N/A	2.487348776	PASS	
7000.9	IMON High CM [ISN=3.3V,ISP=3.3V]	V	PASS	N/A	N/A	3.476167	PASS	
7000.1	IMON Source Current [ISP-ISN=50mV]	mA	PASS	N/A	N/A	2.693619563	PASS	
7000.11	IMON Sink Current [ISP-ISN=50mV]	mA	PASS	N/A	N/A	3.286718931	PASS	
7000.12	IMON Source Current [ISP-ISN=10mV]	mA	PASS	N/A	N/A	5.744644897	PASS	
7000.13	IMON Sink Current [ISP-ISN=10mV]	mA	PASS	N/A	N/A	5.721383481	PASS	
7000.14	Vout Current [Rsen=50mOhm] [Ctrl=0.2V]	mA	PASS	N/A	N/A	2.641039502	PASS	
7000.17	** Isense Voltage Low CM [Ctrl=0.2V ISP_RampDn]	mV	PASS	N/A	N/A	3.799892	PASS	
7000.18	** Isense Voltage Low CM [Ctrl=0.8V ISP_RampDn]	mV	PASS	N/A	N/A	2.409934488	PASS	
7000.19	** Isense Voltage Low CM [Ctrl=1.5V ISP_RampDn]	mV	PASS	N/A	N/A	2.017968901	PASS	
7000.21	** IMON Lo CM [ISN=0V,ISP=50mV]	V	PASS	N/A	N/A	2.243488283	PASS	
7000.22	** IMON Lo CM [ISN=0V,ISP=10mV]	V	PASS	N/A	N/A	4.082852081	PASS	
7000.23	IMON Lo CM [ISN=0V,ISP= 0mV]	V	PASS	N/A	N/A	7.462044913	PASS	
7000.24	* CTRL pin Current [CTRL=1.5V]	uA	PASS	N/A	N/A	3.531423432	PASS	
7000.25	** ISN Current 0mVsen High CM	uA	PASS	N/A	N/A	19.18554719	PASS	
7000.26	** ISP Current 0mVsen High CM	uA	PASS	N/A	N/A	84.47092797	PASS	
7000.27	** ISN Current 50mVsen High CM	uA	PASS	N/A	N/A	4.27465034	PASS	
7000.28	** ISP Current 50mVsen High CM	uA	PASS	N/A	N/A	12.99998494	PASS	
7000.29	** ISN Current 0mVsen Low CM	uA	PASS	N/A	N/A	85.46741152	PASS	
7000.3	** ISP Current 0mVsen Low CM	uA	PASS	N/A	N/A	1305.528519	PASS	
7000.31	** ISN Current 50mVsen Low CM	uA	PASS	N/A	N/A	23.16442155	PASS	
7000.32	** ISP Current 50mVsen Low CM	uA	PASS	N/A	N/A	747.039071	PASS	
7000.36	Com Mode Thresholds ISN&ISP RampUp	V	PASS	N/A	N/A	10.40696617	PASS	
7000.37	Com Mode Thresholds ISN&ISP RampDn	V	PASS	N/A	N/A	7.422052489	PASS	
7000.38	Com Mode Thresholds_Hyst	V	PASS	N/A	N/A	24.13861959	PASS	
9000	VCC_cont Damage Check	V	PASS	N/A	N/A	53.96445379	PASS	
9000.1	VIN_cont Danage Check	V	PASS	N/A	N/A	54.2448282	PASS	
9000.2	SW_cont Damage Check	V	PASS	N/A	N/A	13.22961488	PASS	
9000.3	Vin_current Damage Check	uA	PASS	N/A	N/A	4.852185179	PASS	
9000.4	Vbst_leakage Damage Check	uA	PASS	N/A	N/A	39.97893108	PASS	
9000.5	Vcc_leakage Damage Check	uA	PASS	N/A	N/A	4.481396967	PASS	

ADSG To UTL Test Transfer Correlation Report For LT8614

PRODUCT INFORMATION

Part Name	LT8614
Package	QFN3x4
Lead Count	18
Description	42V, 4A Synchronous Step-Down Silent Switcher with 2.5μA Quiescent Current

PRODUCT TEST SITE TRANSFER CORRELATION

SETUP INFORMATION

Test Site	Tester ID	Handler ID	BOARD ID	CONTACTOR ID 1	CONTACTOR ID 2
ADSG	ETS364B	RASCO1000	LT8614 DIB#2	JTI D#9037	JTI D#9037
UTL	ETS364B	RASCO1000	LT8614 DIB#2	JTI D#9037	JTI D#9037

SUMMARY OF TEST RESULTS

Test all good units in ATE-Handler setup through three test temperatures

Test Site	Program	Temp	Lot ID	Qty In	Qty Out
ADSG	LT8614_03	25C	1012692.1	310	310
UTL	LT8614_03	25C	1012692.1	310	310

Test Site	Program	Temp	Lot ID	Qty In	Qty Out
ADSG	LT8614_03	125C	1012692.1	310	310
UTL	LT8614_03	125C	1012692.1	310	310

Test Site	Program	Temp	Lot ID	Qty In	Qty Out
ADSG	LT8614_03	-40C	1012692.1	310	310
UTL	LT8614_03	-40C	1012692.1	310	310

CORRELATION RESULT

Test Flow	Number of Test	Result
25C Ambient	153	all passed
125C HOT temp	153	all passed
-40C Cold temp	153	all passed

LT8614_25C A	Analysis Data View Report									
Test Number	Test Name	Units	Overall Correlation Result	Mean Diff	Mean diff <5% limit range	Stdv Ratio	Sigma Spread Criteria <1.3	Cpk Result	Cpk >1.67	Comments
20.0	VCC_cont	V	PASS		NA		NA	106.6299165	PASS	CpK greater than 1.67
20.1	VIN_cont	V	PASS		NA		NA	108.7498268	PASS	CpK greater than 1.67
20.2	SW_cont	V	PASS		NA		NA	12.23424169	PASS	CpK greater than 1.67
20.3	EN_cont @-100uA	V	PASS		NA		NA	96.10203563	PASS	CpK greater than 1.67
20.4	SYNC_cont	V	PASS		NA		NA	31.9173075	PASS	CpK greater than 1.67
20.5	SS_cont	V	PASS		NA		NA	39.20374345	PASS	CpK greater than 1.67
20.6	RT_cont [18.2K to APU]	V	PASS		NA		NA	259.3977126	PASS	CpK greater than 1.67
20.7	PG_cont	V	PASS		NA		NA	65.68781446	PASS	CpK greater than 1.67
20.8	FB_cont	V	PASS		NA		NA	28.78614914	PASS	CpK greater than 1.67
20.9	BST_cont	V	PASS		NA		NA	102.2448733	PASS	CpK greater than 1.67
20.1	BIAS_cont	V	PASS		NA		NA	71.04652678	PASS	CpK greater than 1.67
940	Vref_Trim_Check [Open Loop]	V	PASS		NA		NA	5.282206043	PASS	CpK greater than 1.67
950	*** Post-BURN Vout [0.970V] Vin=6V	V	PASS		NA		NA	4.077188023	PASS	CpK greater than 1.67
950.1	Post-BURN Vout [0.970V] Vin=40V	V	PASS		NA		NA	17.41145422	PASS	CpK greater than 1.67
950.2	Post-BURN OSCF	KHz	PASS		NA		NA	11.71012949	PASS	CpK greater than 1.67
950.6	Vref_Trim_Check [Open Loop] [From T940.0]	V	PASS		NA		NA	12.97156468	PASS	CpK greater than 1.67
950.7	Delta_of_Vref [T940.0-T950.0]	mV	PASS		NA		NA	2.434571445	PASS	CpK greater than 1.67
1000	** lvin_Sleep	uA	PASS		NA		NA	7.074213702	PASS	CpK greater than 1.67
1000.1	* len_Sleep	nA	PASS		NA		NA	675.7467841	PASS	CpK greater than 1.67
1000.2	Irt_Sleep	uA	PASS		NA		NA	88.87750728	PASS	CpK greater than 1.67
1000.3	lss_Sleep	uA	PASS		NA		NA	109.3680764	PASS	CpK greater than 1.67
1000.7	* Ipg_Sleep	nA	PASS		NA		NA	10.78896523	PASS	CpK greater than 1.67
1000.8	Ibias_Sleep	uA	PASS		NA		NA	27.59480729	PASS	CpK greater than 1.67
1000.9	lintvcc_Sleep [INTVCC=4.0V]	uA	PASS		NA		NA	9.620820818	PASS	CpK greater than 1.67
1000.1	lintvcc_Sleep [INTVCC=3.3V]	uA	PASS		NA		NA	26.01798075	PASS	CpK greater than 1.67
1000.11	lintvcc_Sleep [INTVCC=2.8V]	uA	PASS		NA		NA	34.64700028	PASS	CpK greater than 1.67
1000.12	Ibst_Sleep	uA	PASS		NA		NA	14.23793918	PASS	CpK greater than 1.67
1000.13	** Ivin_Sleep_with_SYNC	mA	PASS		NA		NA	9.681276299	PASS	CpK greater than 1.67
1100	lvin_Sleep_ABS_MAX	uA	PASS		NA		NA	93.01527944	PASS	CpK greater than 1.67
1100.1	len_Sleep_ABS_MAX	uA	PASS		NA		NA	256.1989847	PASS	CpK greater than 1.67
1100.4	lpg_Sleep_ABS_MAX	uA	PASS		NA		NA	487.1420615	PASS	CpK greater than 1.67
1200	** Ivin_Shutdown	uA	PASS		NA		NA	6.730636731	PASS	CpK greater than 1.67
1200.1	Irt_Shutdown	uA	PASS		NA		NA	92.59838324	PASS	CpK greater than 1.67
1200.2	Iss_Shutdown	mA	PASS		NA		NA	249.4857929	PASS	CpK greater than 1.67
1200.3	* Isync_Shutdown	nA	PASS		NA		NA	134.653325	PASS	CpK greater than 1.67
1200.8	* Ifb_Shutdown	nA	PASS		NA		NA	207.2782159	PASS	CpK greater than 1.67
1200.9	Ipg_Shutdown	mA	PASS		NA		NA	588.6143962	PASS	CpK greater than 1.67
1200.1	Ibias_Shutdown	uA	PASS		NA		NA	33.81858112	PASS	CpK greater than 1.67
1200.11	* SS_Pulldown_Resistance	Ohm	PASS		NA		NA	42.93129038	PASS	CpK greater than 1.67
1200.12	** PG_Pulldown_Resistance	Ohm	PASS		NA		NA	25.38994116	PASS	CpK greater than 1.67
1300	Ivin_Shutdown_ABS_MAX	uA	PASS		NA		NA	73.22212557	PASS	CpK greater than 1.67
1300.1	Iss_Shutdown_ABS_MAX	mA	PASS		NA		NA	18.43323076	PASS	CpK greater than 1.67
1300.4	Ipg_Shutdown_ABS_MAX	mA	PASS		NA		NA	3.363861847	PASS	CpK greater than 1.67
1300.5	Ibias_Shutdown_ABS_MAX	uA	PASS		NA		NA	11.88387574	PASS	CpK greater than 1.67
1300.6	Irt_Shutdown_ABS_MAX	uA	PASS		NA		NA	7.260396011	PASS	CpK greater than 1.67
1400	* Top_FET_Isw	uA	PASS		NA		NA	22.37268465	PASS	CpK greater than 1.67
1500	* Bot_FET_Leakage	uA	PASS		NA		NA	24.09141353	PASS	CpK greater than 1.67
1500.1	Bot_FET_AbsMax_Leakage [lbst]	uA	PASS		NA		NA	184.2852316	PASS	CpK greater than 1.67
1600	** Regulation_Light_Load_lvin@1mA	uA	PASS		NA		NA	6.780879164	PASS	CpK greater than 1.67
1600.3	** Regulation_Light_Load_Ivin@100uA	uA	PASS		NA		NA	3.133478066	PASS	CpK greater than 1.67
1700	Regulation_Mode_Short_Circuit	mA	PASS		NA		NA	3.316900303	PASS	CpK greater than 1.67
2000	Freq with RT=48uA	KHz	PASS		NA		NA	9.479815097	PASS	CpK greater than 1.67

100001***1***NA1***NA<	2002.4	Degulation Martin Course OV/		DACC		N1.4	<u>т</u> т	N1.4	E 225642426	DACC	Cell greater than 1.67
1010Impound Merson	2000.1	RegulationMode Sync=OV	V	PASS		NA		NA	5.335613126	PASS	CpK greater than 1.67
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2700 SW_Frequency Hrz PASS NA NA 8.32888666 PASS Optimization 2700.1 'Min, Or, Time nS PASS NA NA 3.84440266 PASS Optimization 2700.2 W_dur, cycle % PASS NA NA 3.8442658 PASS Optimization 2800.1 Vintorc, Om, no, bias V PASS NA NA 3.33745394 PASS Optimization Optimization <td></td> <td></td> <td></td> <td></td> <td>4.489099339</td> <td></td> <td>0.971166481</td> <td></td> <td></td> <td></td> <td></td>					4.489099339		0.971166481				
2700.1 **Min_Off_Time nS PASS NA NA BAS BAS CpS grader than 1.67 2700.2 W_dity, cycle % PASS NA NA NA 3.3144280.5 Ox grader than 1.67 2700.3 Tropout Voltage Y PASS NA NA NA 7.16673.5 PASS Ox grader than 1.67 2800.1 Wintex, Cum, no, bias Y PASS NA NA 1.43470137 PASS Ox grader than 1.67 2900.1 Wintex, Cum, with, bias Y PASS NA NA NA 1.5386277 PASS Ox grader than 1.67 2900.1 Intexc, lim, no, bias ViccintOV mA PASS NA NA 1.434318080 PASS Ox grader than 1.67 3000.1 Intexc, lim, noth, bias Viccin-OV mA PASS NA NA 1.433143080 PASS Ox grader than 1.67 3100 Intexc, lim, noth, bias Viccin-OV mA PASS NA NA 3.4344431 PASS Ox grader than 1.67 </td <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>											
2702 W. div, Cycle % MASS NA NA 31.42658 PASS Cpt greater than 1.67 2700.3 Dropout Voltage V PASS NA NA 74.67366 PASS Cpt greater than 1.67 2800.1 Vintorc, OmA, no, bias V PASS NA NA 13.4347304 PASS Cpt greater than 1.67 2800.1 Vintorc, OmA, no, bias V PASS NA NA 13.53662776 PASS Cpt greater than 1.67 2900.1 Vintorc, OmA, with, bias V PASS NA NA 12.33562776 PASS Cpt greater than 1.67 3000.1 Intorc, Ilim, ABMAA, no, bias (VicintoV) mA PASS NA NA 2.33356413 PASS Cpt greater than 1.67 3100.1 Intorc, Ilim, ABMAA, no, bias (VicintoV) mA PASS NA NA 2.33356413 PASS Cpt greater than 1.67 3200.1 Intorc, Ilim, ABMAA, no, bias (VicintoV) mA PASS NA NA 2.33356413 PASS Cpt greater than 1		= ; ;									
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3500.1Introc_Vin_Threshold RampUpVPASSNANA3.090658017PASSCpK greater than 1.673500.2Introc_VIO_Threshold RampDownVPASSNANA17.9517736PASSCpK greater than 1.673600*Introc_UVLO_Threshold RampDownVPASSNANA3.63364354PASSCpK greater than 1.673600.1Introc_UVLO_Threshold RampDownVPASSNANA3.63364354PASSCpK greater than 1.673600.2Introc_UVLO_Threshold HysteresisVPASSNANA13.6732657PASSCpK greater than 1.674000EN_Threshold RampDownVPASSNANANA4.67656922PASSCpK greater than 1.674000.1** EN_Threshold RampDownVPASSNANANA11.73861508PASSCpK greater than 1.674000.2*EN_Threshold HysteresisVPASSONANA14.7310587PASSCpK greater than 1.674000.2*EN_Threshold HysteresisVPASSNANA14.7310587PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampDownVPASSNANA14.7310587PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HysteresisVPASSNANA3.66435156PASSCpK greater than 1.674100.3*PG Low_Threshold HysteresisVPASSNANA3.62055299PASSCpK greater than 1.67 <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td> <td>CpK greater than 1.67</td>											CpK greater than 1.67
350.2Introc_Vin_Threshold HysteresisVPASSINANANA17.9517346PASSCpK great rhan 1.673600* Introc_VVLO_Threshold RampDownVPASSNAANA3.6336434PASSCpK great rhan 1.67360.1Introc_VVLO_Threshold RampDownVPASSNANA3.6336434PASSCpK great rhan 1.67360.2Introc_VVLO_Threshold RampDownVPASSPASSPASSCpK great rhan 1.67360.2Introc_VVLO_Threshold RampDownVPASSNAIntro4.6766529PASSCpK great rhan 1.67400.1EN_Threshold RampDownVPASSIntroIntro1.7381508PASSCpK great rhan 1.67400.2EN_Threshold RampDownVPASSIntroIntro1.7381508PASSCpK great rhan 1.67400.1Introphyshold RampDownVPASSIntroIntrophyshold RampDownVPASSIntrophyshold RampDownIntrophyshold RampDown410.2FS Introphyshold RampDownVPASSIntrophyshold RampDownVPASSIntrophyshold RampDownIntrophyshold RampDown410.1PG Introphyshold RampDownVPASSIntrophyshold RampDownVPASSIntrophyshold RampDownIntrophyshold RampDown410.2PG Introphyshold RampDownVPASSPASSIntrophyshold RampDownVPASSIntrophyshold RampDown410.1PG Introphyshold RampDownVPASSPASSIntrophyshold RampDownIntrophyshold RampDo	3500		V	PASS		NA		NA	3.605317264	PASS	CpK greater than 1.67
3600* Introc_UVL0_Threshold RampDownVPASSNANA3.633643544PASSCpK greater than 1.673600.1Introc_UVL0_Threshold RampUpVPASSNANANA13.67932657PASSCpK greater than 1.673600.2Introc_UVL0_Threshold HysteresisVPASSNANANA64.67665922PASSCpK greater than 1.674000EN_Threshold RampDownVPASSNANA11.73861508PASSCpK greater than 1.674000.1** EN_Threshold RampDownVPASSNANA14.73861508PASSCpK greater than 1.674000.2* EN_Threshold RampDownVPASSNANA14.4312387PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampDownVPASSNANANA3.927900209PASSCpK greater than 1.674100.2PG_pin_Low_Threshold RampUpVPASSNANANA3.636435156PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampUpVPASSNANANA3.227900209PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HysteresisVPASSNANANA2.95632592PASSCpK greater than 1.674100.3* PG Lower Threshold HysteresisVPASSNANANA2.9565139PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANAS.2526599 <td< td=""><td></td><td>Intvcc_Vin_Threshold RampUp</td><td></td><td></td><td></td><td></td><td></td><td>NA</td><td>3.090658017</td><td>PASS</td><td>CpK greater than 1.67</td></td<>		Intvcc_Vin_Threshold RampUp						NA	3.090658017	PASS	CpK greater than 1.67
3600.1Intvcc_UVLO_Threshold RampUpVPASSNANA13.67932657PASSCpK greater than 1.673600.2Intvcc_UVLO_Threshold HysteresisVPASSNANA64.67665922PASSCpK greater than 1.674000EN_Threshold RampDownVPASSNANANA11.73861508PASSCpK greater than 1.674000.1** EN_Threshold RampUpVPASSNANANA2.46423236PASSCpK greater than 1.674000.2* EN_Threshold HysteresisVPASSNANANA14.7310587PASSCpK greater than 1.674100PG_pin_Low_Threshold RampDownVPASSNANANA3.927900209PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampDownVPASSNANANA3.66435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold RampDownVPASSNANANA3.66435156PASSCpK greater than 1.674100.3* PG Low Threshold MysteresisVPASSNANANA2.05526599PASSCpK greater than 1.674100.3* PG Low Hysteresis%PASSNANANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANAS.0526599PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANAS.0526599PASSCp	3500.2	Intvcc_Vin_Threshold Hysteresis	V			NA		NA	17.95177346	PASS	CpK greater than 1.67
3600.2Intvcc_UVLO_Threshold HysteresisVPASSNANA64.67665922PASSCpK greater than 1.674000EN_Threshold RampDownVPASSNANA11.73861508PASSCpK greater than 1.674000.1** EN_Threshold RampUpVPASSNANA2.464232366PASSCpK greater than 1.674000.2*EN_Threshold HysteresisVPASSNANA14.7310587PASSCpK greater than 1.674100PG_pin_Low_Threshold RampDownVPASSNANA3.92790029PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampDownVPASSNANA3.92790029PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampDownVPASSNANA3.666435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HysteresisVPASSNANAS.666435156PASSCpK greater than 1.674100.3*PG Lower Threshold HysteresisVPASSNANAS.666435159PASSCpK greater than 1.674100.4*PG Lower Threshold HysteresisVPASSNANAS.666435159PASSCpK greater than 1.674100.4*PG Lower Threshold Hysteresis%PASSNANAS.666435159PASSCpK greater than 1.674100.4*PG Lower Threshold RampDownVPASSNANAS.6526599PASSCpK greater than 1.674100.4<				PASS		NA		NA			
4000EN_Threshold RampDownVPASSNANA11.73861508PASSCpK greater than 1.674000.1** EN_Threshold RampUpVPASSNANA2.464232396PASSCpK greater than 1.674000.2* EN_Threshold HystersisVPASSNANA14.73105987PASSCpK greater than 1.674100PG_pin_Low_Threshold RampDownVPASSNANA3.92790209PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampUpVPASSNANA3.666435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HystersisVPASSNANA3.666435156PASSCpK greater than 1.674100.3PG_pin_Low_Threshold HystersisVPASSNANANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hystersis%PASSNANANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hystersis%PASSNANANAS.424989862PASSCpK greater than 1.674200.1 <td>3600.1</td> <td>Intvcc_UVLO_Threshold RampUp</td> <td>V</td> <td>PASS</td> <td></td> <td>NA</td> <td></td> <td>NA</td> <td></td> <td>PASS</td> <td>CpK greater than 1.67</td>	3600.1	Intvcc_UVLO_Threshold RampUp	V	PASS		NA		NA		PASS	CpK greater than 1.67
4000.1** EN_Threshold RampUpVPASSNANA2.46423236PASSCpK greater than 1.674000.2* EN_Threshold HysteresisVPASSNANANA14.73105987PASSCpK greater than 1.674100PG_pin_Low_Threshold RampDownVPASSNANANA3.92790209PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampUpVPASSNANAS.666435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HysteresisVPASSNANAS.666435156PASSCpK greater than 1.674100.3* PG Lower Threshold Offset from VFB%PASSNANAS.666435156PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANANAS.0526599PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANANAS.6543516133PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANANAS.6545199PASSCpK greater than 1.674200PG_pin_High_Threshold RampDownVPASSNANANAS.424989862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANANAPASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANANAPASSCpK greater than 1.67 <td>3600.2</td> <td>Intvcc_UVLO_Threshold Hysteresis</td> <td>V</td> <td>PASS</td> <td></td> <td>NA</td> <td></td> <td>NA</td> <td>64.67665922</td> <td>PASS</td> <td></td>	3600.2	Intvcc_UVLO_Threshold Hysteresis	V	PASS		NA		NA	64.67665922	PASS	
4000.2* EN_Threshold HysteresisVPASSNANA14.73105987PASSCpK greater than 1.674100PG_pin_Low_Threshold RampUpVPASSNANA3.92790209PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampUpVPASSNANA3.66435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HystersisVPASSNANA3.666435156PASSCpK greater than 1.674100.3* PG Lower Threshold MystersisVPASSNANA229.6532592PASSCpK greater than 1.674100.4* PG Lower Threshold Offset from VFB%PASSNANA2.05526599PASSCpK greater than 1.674100.4* PG Lower Threshold RampDown%PASSNANA2.05526599PASSCpK greater than 1.674100.4* PG Lower Threshold RampDown%PASSNANA3.42498862PASSCpK greater than 1.674200.4PG_pin_High_Threshold RampDowVPASSNANA3.42498862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANANA4.87983544PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANAA.87983544PASSCpK greater than 1.67	4000	EN_Threshold RampDown	V	PASS		NA		NA	11.73861508	PASS	
4100PG_pin_Low_Threshold RampDowVPASSNANA3.92790209PASSCpK greater than 1.674100.1PG_pin_Low_Threshold RampDpVPASSNANA3.66435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HystersisVPASSNANA3.66435156PASSCpK greater than 1.674100.3PG_pin_Low_Threshold MystersisVPASSNANA229.53259PASSCpK greater than 1.674100.4*PG Lower Threshold Offset from VFB%PASSNANA2.0552659PASSCpK greater than 1.674100.4*PG Lower Threshold RampDown%PASSNANAS.05151013PASSCpK greater than 1.674100.4PG_pin_High_Threshold RampDown%PASSNANAS.42498862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampDow%PASSNANAS.42498862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampDow%PASSNANAS.42498862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampDow%PASSNANAS.42498862PASSCpK greater than 1.67		** EN_Threshold RampUp	V	PASS		NA		NA		PASS	CpK greater than 1.67
4100.1PG_pin_Low_Threshold RampUpVPASSNANA3.666435156PASSCpK greater than 1.674100.2PG_pin_Low_Threshold HysteresisVPASSNANA229.6532592PASSCpK greater than 1.674100.3* PG Lower Threshold Offset from VFB%PASSNANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANA7.851510133PASSCpK greater than 1.674200PG_pin_High_Threshold RampDownVPASSNANA3.424989862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANA4.879839544PASSCpK greater than 1.67	4000.2	* EN_Threshold Hysteresis	V	PASS		NA		NA	14.73105987	PASS	CpK greater than 1.67
4100.2PG_pin_Low_Threshold HystersisVPASSNANA229.6532592PASSCpK greater than 1.674100.3* PG Lower Threshold Offset from VFB%PASSNANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hystersis%PASSNANANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hystersis%PASSNANANA7.851510133PASSCpK greater than 1.674200PG_pin_High_Threshold RampDownVPASSNANA3.42498962PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANA4.879839544PASSCpK greater than 1.67	4100	PG_pin_Low_Threshold RampDown		PASS		NA		NA		PASS	CpK greater than 1.67
4100.3* PG Lower Threshold Offset from VFB%PASSNANA2.05526599PASSCpK greater than 1.674100.4* PG Low Hysteresis%PASSNANANA7.851510133PASSCpK greater than 1.674100.4PG_pin_High_Threshold RampDownVPASSNANANA3.424989862PASSCpK greater than 1.674200.1PG_pin_High_Threshold RampUpVPASSNANA4.879839544PASSCpK greater than 1.67				PASS		NA		NA	1	PASS	
4100.4 * PG Low Hysteresis % PASS NA NA NA 7.851510133 PASS CpK greater than 1.67 4200 PG_pin_High_Threshold RampDown V PASS NA NA 3.424989862 PASS CpK greater than 1.67 4200.1 PG_pin_High_Threshold RampUp V PASS NA NA 4.879839544 PASS CpK greater than 1.67	4100.2		V	PASS		NA		NA	229.6532592	PASS	CpK greater than 1.67
4200 PG_pin_High_Threshold RampDown V PASS NA NA 3.424989862 PASS CpK greater than 1.67 4200.1 PG_pin_High_Threshold RampUp V PASS NA NA 4.879839544 PASS CpK greater than 1.67	4100.3			PASS		NA		NA	2.05526599	PASS	
4200.1 PG_pin_High_Threshold RampUp V PASS NA NA 4.879839544 PASS CpK greater than 1.67	4100.4		%	PASS		NA		NA	7.851510133	PASS	
	4200	PG_pin_High_Threshold RampDown	V	PASS		NA		NA	3.424989862	PASS	
	4200.1	PG_pin_High_Threshold RampUp	V	PASS		NA		NA	4.879839544	PASS	CpK greater than 1.67
4200.2 PG_pin_High_Threshold Hysteresis V PASS NA NA 238.2220203 PASS CpK greater than 1.67	4200.2	PG_pin_High_Threshold Hysteresis	V	PASS		NA		NA	238.2220203	PASS	CpK greater than 1.67

4200.3	* PG Upper Threshold Offset from VFB	%	PASS	NA	NA	1.791010609	PASS	CpK greater than 1.67
4200.4	* PG Hi Hysteresis	%	PASS	NA	NA	7.61402837	PASS	CpK greater than 1.67
4300	* SYNC Threshold RampDown	V	PASS	NA	NA	6.082033832	PASS	CpK greater than 1.67
4300.1	* SYNC Threshold RampUp	V	PASS	NA	NA	8.130710051	PASS	CpK greater than 1.67
4300.2	SYN Threshold Hysteresis	V	PASS	NA	NA	22.66848193	PASS	CpK greater than 1.67
4500	Feedback Reference Voltage [Vin=12V, ILoad=0.5A	V	PASS	NA	NA	16.44147763	PASS	CpK greater than 1.67
4500.1	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS	NA	NA	17.09499827	PASS	CpK greater than 1.67
4500.2	Reference Voltage [Vin=40V, ILoad=0.5A]	V	PASS	NA	NA	14.4775746	PASS	CpK greater than 1.67
4500.3	** Feedback Voltage Line Regulation	%/V	PASS	NA	NA	5.605926147	PASS	CpK greater than 1.67
4500.4	Reference Voltage [Vin=12V, ILoad=0.1A]	V	PASS	NA	NA	119.1107016	PASS	CpK greater than 1.67
4500.5	Reference Voltage [Vin=12V, ILoad=2.5A]	V	PASS	NA	NA	107.1725861	PASS	CpK greater than 1.67
4500.6	Feedback Voltage Load Regulation	%	PASS	NA	NA	89.84002396	PASS	CpK greater than 1.67
4500.7	Delta Vref (Vin=6V - Vin=4V)	mV	PASS	NA	NA	5.168104511	PASS	CpK greater than 1.67
4500.8	Delta Vref (Vin=6V - Vin=40V)	mV	PASS	NA	NA	3.41847278	PASS	CpK greater than 1.67
4800	* BIAS pin Current Consumption	mA	PASS	NA	NA	12.80085421	PASS	CpK greater than 1.67
4900	Regulating_with_SS	V	PASS	NA	NA	8.522804134	PASS	CpK greater than 1.67
5000	** SS_Pin_Current	uA	PASS	NA	NA	2.166375035	PASS	CpK greater than 1.67
5100	** Datasheet Osc High [Rt=18.2K]	KHz	PASS	NA	NA	2.492782189	PASS	CpK greater than 1.67
5100.1	I Vin Rt18K	mA	PASS	NA	NA	258.1016933	PASS	CpK greater than 1.67
5100.2	Vout Rt18K	V	PASS	NA	NA	137.692082	PASS	CpK greater than 1.67
5100.3	Efficiency Rt18K		PASS	NA	NA	20.96179746	PASS	CpK greater than 1.67
5200	** Datasheet_Osc_Low [Rt=60.4K]	KHz	PASS	NA	NA	6.065938648	PASS	CpK greater than 1.67
5200.1	I Vin Rt60K	mA	PASS	NA	NA	263.1901444	PASS	CpK greater than 1.67
5200.2	Vout_Rt60K	V	PASS	NA	NA	139.5051254	PASS	CpK greater than 1.67
5200.3	Efficiency_Rt60K		PASS	NA	NA	14.19589753	PASS	CpK greater than 1.67
5300	SYNC_Frequency [Sync=1MHz]	KHz	PASS	NA	NA	314.5746242	PASS	CpK greater than 1.67
5300.1	SYNC_Frequency [Sync=3.1MHz]	KHz	PASS	NA	NA	81.34813055	PASS	CpK greater than 1.67
5300.2	SYNC_Frequency [Sync=200KHz]	KHz	PASS	NA	NA	57.49870155	PASS	CpK greater than 1.67
5400	** Datasheet_Osc_Low [Rt=221K]	KHz	PASS	NA	NA	2.799224146	PASS	CpK greater than 1.67
5400.1	Osc_Low [Rt=3.8uA]	KHz	PASS	NA	NA	14.93577433	PASS	CpK greater than 1.67
5400.2	Osc_Med_Hi [Rt=24uA]	KHz	PASS	NA	NA	2.126012179	PASS	CpK greater than 1.67
5400.3	Rt_Voltage_Hi [Rt=18.2K//60.4K=13.986K]	V	PASS	NA	NA	27.12908111	PASS	CpK greater than 1.67
5400.4	Rt_Voltage_Hi + 13.986K*0.024uA [Calc]	V	PASS	NA	NA	19.54137422	PASS	CpK greater than 1.67
5500	Frequency_Foldback	KHz	PASS	NA	NA	3.458466515	PASS	CpK greater than 1.67
5500.1	Rt_Voltage_Lo [Rt=18.2K//60.4K=13.986K]	V	PASS	NA	NA	43.92050364	PASS	CpK greater than 1.67
5500.2	Rt_Voltage_Lo + 13.986K*0.024uA [Calc]	V	PASS	NA	NA	18.46498387	PASS	CpK greater than 1.67
5600	SS_Threshold_to_stop_charging	V	PASS	NA	NA	24.73274818	PASS	CpK greater than 1.67
5700	PG_High_SW_Pulldown_Current	mA	PASS	NA	NA	29.21127346	PASS	CpK greater than 1.67
5800	SW voltage [BST=10V]	V	PASS	NA	NA	249.8181759	PASS	CpK greater than 1.67
5800.1	BST voltage part switching	V	PASS	NA	NA	15.0818726	PASS	CpK greater than 1.67
5800.2	BST_OK_Threshold [BST-SW]	V	PASS	NA	NA	6.782057145	PASS	CpK greater than 1.67
9000	VCC_cont Damage Check	V	PASS	NA	NA	78.80699869	PASS	CpK greater than 1.67
9000.1	VIN_cont Danage Check	V	PASS	NA	NA	60.836769	PASS	CpK greater than 1.67
9000.2	SW_cont Damag Check	V	PASS	NA	NA	13.21357832	PASS	CpK greater than 1.67

Test NumberTest NameUnitsOverall Correlation ResultMean DiffSigma Spread limit rangeSigma Spread Criteria <1.3	Cpk >1.67	
20.0 VCC_cont V PASS N/A N/A 16.62301472		Annotations
	PASS	CpK greater than 1.67
20.1 VIN_cont V PASS N/A N/A 22.20309818	PASS	CpK greater than 1.67
20.2 SW_cont V PASS N/A N/A 6.323068753	PASS	CpK greater than 1.67
20.3 EN_cont @-100uA V PASS N/A N/A 14.46554758	PASS	CpK greater than 1.67
20.4 SYNC_cont V PASS N/A N/A 24.78709836	PASS	CpK greater than 1.67
20.5 SS_cont V PASS N/A N/A 26.08948375	PASS	CpK greater than 1.67
20.6 RT_cont [18.2K to APU] V PASS N/A N/A 62.75733837	PASS	CpK greater than 1.67
20.7 PG_cont V PASS N/A N/A 28.49258691	PASS	CpK greater than 1.67
20.8 FB_cont V PASS N/A N/A 24.10272793	PASS	CpK greater than 1.67
20.9 BST_cont V PASS N/A N/A 17.90502618	PASS	CpK greater than 1.67
20.1 BIAS_cont V PASS N/A N/A 28.47002707	PASS	CpK greater than 1.67
940 Vref_Trim_Check [Open Loop] V PASS N/A N/A 2.481808772	PASS	CpK greater than 1.67
950 *** Post-BURN Vout [0.970V] Vin=6V V PASS N/A N/A 1.739501495	PASS	CpK greater than 1.67
950.1 Post-BURN Vout [0.970V] Vin=40V V PASS N/A N/A 3.252087743	PASS	CpK greater than 1.67
950.2 Post-BURN OSCF KHz PASS N/A N/A 6.443491013	PASS	CpK greater than 1.67
950.6 Vref_Trim_Check [Open Loop] [From T940.0] V PASS N/A N/A 2.808987475	PASS	CpK greater than 1.67
950.7 Delta of Vref [T940.0-T950.0] mV PASS N/A N/A 4.674452713	PASS	CpK greater than 1.67
1000 ** lvin_Sleep uA PASS N/A N/A 9.630294904	PASS	CpK greater than 1.67
1000.1 * len Sleep nA PASS N/A N/A 110.0945615	PASS	CpK greater than 1.67
1000.2 Irt_Sleep uA PASS N/A N/A 82.97896436	PASS	CpK greater than 1.67
1000.3 Iss_Sleep uA PASS N/A N/A 111.8952538	PASS	CpK greater than 1.67
1000.7 * Ipg Sleep nA PASS N/A N/A 61.56777618	PASS	CpK greater than 1.67
1000.8 Ibias Sleep uA PASS N/A N/A 8.469516148	PASS	CpK greater than 1.67
1000.9 lintvcc_Sleep [INTVCC=4.0V] uA PASS N/A N/A 7.777488833	PASS	CpK greater than 1.67
1000.1 lintvcc Sleep [INTVCC=3.3V] uA PASS N/A N/A 25.11006232	PASS	CpK greater than 1.67
1000.11 lintvcc_Sleep [INTVCC=2.8V] uA PASS N/A N/A 35.65305123	PASS	CpK greater than 1.67
1000.12 Ibst_Sleep uA PASS N/A N/A 7.112419172	PASS	CpK greater than 1.67
1000.13 ** Ivin_Sleep_with_SYNC mA PASS N/A N/A 16.80430471	PASS	CpK greater than 1.67
1100 lvin_Sleep_ABS_MAX uA PASS N/A N/A 153.9681706	PASS	CpK greater than 1.67
1100.1 len Sleep ABS MAX uA PASS N/A N/A 276.6095707	PASS	CpK greater than 1.67
1100.4 lpg Sleep ABS MAX uA PASS N/A N/A 494.6588627	PASS	CpK greater than 1.67
1200 ** lvin_Shutdown uA PASS N/A N/A 8.922680118	PASS	CpK greater than 1.67
1200.1 Irt_Shutdown uA PASS N/A N/A 90.82112753	PASS	CpK greater than 1.67
1200.2 lss_Shutdown mA PASS N/A N/A 250.6850256	PASS	CpK greater than 1.67
1200.3 * Isync Shutdown nA PASS N/A N/A 479.731775	PASS	CpK greater than 1.67
1200.8 *Ifb_Shutdown nA PASS N/A N/A 414.2675626	PASS	CpK greater than 1.67
1200.9 lpg_Shutdown mA PASS N/A N/A 476.7023467	PASS	CpK greater than 1.67
1200.1 Ibias_Shutdown uA PASS N/A N/A 8.401292031	PASS	CpK greater than 1.67
1200.11 * SS_Pulldown_Resistance Ohm PASS N/A N/A 38.3113145	PASS	CpK greater than 1.67
1200.12 ** PG_Pulldown_Resistance Ohm PASS N/A N/A 17.70339227	PASS	CpK greater than 1.67
1300 Ivin_Shutdown_ABS_MAX uA PASS N/A N/A 35.70538524	PASS	CpK greater than 1.67
1300.1 Iss_Shutdown_ABS_MAX mA PASS N/A N/A 17.22603556	PASS	CpK greater than 1.67
1300.4 lpg_Shutdown_ABS_MAX mA PASS N/A N/A 3.660380361	PASS	CpK greater than 1.67
1300.5 Ibias_Shutdown_ABS_MAX uA PASS N/A N/A 5.936013425	PASS	CpK greater than 1.67
1300.6 Irt_Shutdown_ABS_MAX uA PASS N/A N/A 7.955035159	PASS	CpK greater than 1.67
1400 * Top_FET_Isw uA PASS N/A N/A 41.5685587	PASS	CpK greater than 1.67
1500 * Bot_FET_Leakage uA PASS N/A N/A 44.51116199	PASS	CpK greater than 1.67
1500.1 Bot_FET_AbsMax_Leakage [lbst] uA PASS N/A N/A 142.8911996	PASS	CpK greater than 1.67
1600 ** Regulation_Light_Load_lvin@1mA uA PASS N/A N/A 6.161350025	PASS	CpK greater than 1.67
1600.3 ** Regulation_Light_Load_lvin@100uA uA PASS N/A N/A 4.650014695	PASS	CpK greater than 1.67
1700 Regulation_Mode_Short_Circuit mA PASS N/A N/A 3.487144612	PASS	CpK greater than 1.67

2000	Freq with RT=48uA	KHz	PASS	N/A		N/A	7.988129456	PASS	CoV groater than 1.67
2000	RegulationMode Sync=0V	V V	PASS	N/A N/A		N/A N/A	4.573350376	PASS	CpK greater than 1.67 CpK greater than 1.67
2000.1	** SW Min Ontime Sync=0V	nS	PASS	N/A N/A		N/A N/A	11.42264904	PASS	CpK greater than 1.67
2100	Freq with RT=48uA	KHz	PASS	N/A N/A		N/A N/A	7.982071692	PASS	CpK greater than 1.67
2100	RegulationMode Sync=3.3V	V	PASS	N/A N/A		N/A N/A	1.905891613	PASS	CpK greater than 1.67
2100.1	** SW_Min_Ontime Sync=3.3V	nS	PASS	N/A N/A				PASS	
	* TopRDSon [Vin-Vsw]	Ohm	PASS	N/A N/A		N/A	8.834423403		CpK greater than 1.67
2200 2200.1	V_sw_out@1A before ramp [Debug only]	V	PASS	N/A N/A		N/A	5.611881238	PASS	CpK greater than 1.67
2200.1	Slop Comp Ilim			N/A N/A		N/A	105.6468533	PASS	CpK greater than 1.67
2300.2	V_sw_out@1.5A before ramp [Debug only]	mA V	PASS PASS	N/A N/A		N/A	7.504759542	PASS	CpK greater than 1.67
						N/A	75.29764067	PASS	CpK greater than 1.67
2300.1	** Top_l_Lim	mA	PASS	N/A	_	N/A	5.386243118	PASS	CpK greater than 1.67
2300.2	Burst_l_Lim	mA	PASS	N/A		N/A	4.080501866	PASS	CpK greater than 1.67
2300.3	SYNC_I_Lim	mA	PASS	N/A		N/A	2.958617666	PASS	CpK greater than 1.67
2400	Vout [0.6A load] @Vin=6V	V	PASS	N/A		N/A	6.775913503	PASS	CpK greater than 1.67
2400.1	** Minimum Input VOltage [Min_Vin_UVLO]	V	PASS	N/A		N/A	10.99009659	PASS	CpK greater than 1.67
2400.2	Vout [0.6A load] Drop	V	PASS	1.885022525 PASS	1.106	PASS	0.826200608	N/A	tightened limits
2400.3	SW_Min_Ontime Sync=0V [Calc]	nS	PASS	N/A		N/A	20.45100407	PASS	CpK greater than 1.67
2400.4	SW_Min_Ontime Sync=3V [Calc]	nS	PASS	N/A		N/A	15.24811008	PASS	CpK greater than 1.67
2500	* BotRDSon [Pgnd-Vsw]	Ohm	PASS	N/A		N/A	4.045040374	PASS	CpK greater than 1.67
2500.1	BST pin Voltage thru 1K	V	PASS	N/A		N/A	203.6062955	PASS	CpK greater than 1.67
2500.2	Zero_cross_current	mA	PASS	N/A		N/A	3.418477893	PASS	CpK greater than 1.67
2600	** DA_Current_Limit [Bot_I_Lim]	mA	PASS	N/A		N/A	4.728374079	PASS	CpK greater than 1.67
2700	SW_Frequency	KHz	PASS	N/A		N/A	3.920583192	PASS	CpK greater than 1.67
2700.1	* Min_Off_Time	nS	PASS	N/A		N/A	6.575557121	PASS	CpK greater than 1.67
2700.2	W_duty_cycle	%	PASS	N/A		N/A	3.819284211	PASS	CpK greater than 1.67
2700.3	Dropout Voltage	V	PASS	N/A		N/A	3.632168957	PASS	CpK greater than 1.67
2800	* Vintvcc_0mA_no_bias	V	PASS	N/A		N/A	3.257428598	PASS	CpK greater than 1.67
2800.1	Vintvcc_20mA_no_bias	V	PASS	N/A		N/A	10.56478429	PASS	CpK greater than 1.67
2900	* Vintvcc_0mA_with_bias	V	PASS	N/A		N/A	7.415065079	PASS	CpK greater than 1.67
2900.1	Vintvcc_20mA_with_bias	V	PASS	N/A		N/A	12.80900557	PASS	CpK greater than 1.67
3000	Intvcc_Ilim_no_bias [Vccint=0V]	mA	PASS	N/A		N/A	2.696037847	PASS	CpK greater than 1.67
3000.1	Intvcc_Ilim_no_bias [Vccint=3V]	mA	PASS	N/A		N/A	2.930103241	PASS	CpK greater than 1.67
3100	Intvcc_Ilim_ABSMAX_no_bias [Vccint=0V]	mA	PASS	N/A		N/A	3.303500094	PASS	CpK greater than 1.67
3100.1	Intvcc_Ilim_ABSMAX_no_bias [Vccint=3V]	mA	PASS	N/A		N/A	3.081268205	PASS	CpK greater than 1.67
3200	Intvcc_Ilim_with_bias [Vccint=0V]	mA	PASS	N/A		N/A	2.780647284	PASS	CpK greater than 1.67
3200.1	Intvcc_Ilim_with_bias [Vccint=3V]	mA	PASS	N/A		N/A	3.927415962	PASS	CpK greater than 1.67
3300	Intvcc_Ilim_ABSMAX_with_bias [Vccint=0V]	mA	PASS	N/A		N/A	33.32485627	PASS	CpK greater than 1.67
3300.1	Intvcc_Ilim_ABSMAX_with_bias [Vccint=3V]	mA	PASS	N/A		N/A	11.71361083	PASS	CpK greater than 1.67
3400	Intvcc_BIAS_Threshold RampDown	V	PASS	N/A		N/A	2.936402603	PASS	CpK greater than 1.67
3400.1	Intvcc_BIAS_Threshold RampUp	V	PASS	N/A		N/A	2.677056012	PASS	CpK greater than 1.67
3400.2	Intvcc_BIAS_Threshold Hysteresis	V	PASS	N/A		N/A	374.4531384	PASS	CpK greater than 1.67
3500	Intvcc_Vin_Threshold RampDown	V	PASS	N/A		N/A	8.283428898	PASS	CpK greater than 1.67
3500.1	Intvcc_Vin_Threshold RampUp	V	PASS	N/A		N/A	7.906993793	PASS	CpK greater than 1.67
3500.2	Intvcc_Vin_Threshold Hysteresis	V	PASS	N/A		N/A	814.7131298	PASS	CpK greater than 1.67
3600	* Intvcc_UVLO_Threshold RampDown	V	PASS	N/A		N/A	5.343421817	PASS	CpK greater than 1.67
3600.1	Intvcc_UVLO_Threshold RampUp	V	PASS	N/A		N/A	17.99180799	PASS	CpK greater than 1.67
3600.2	Intvcc_UVLO_Threshold Hysteresis	V	PASS	N/A		N/A	86.85390954	PASS	CpK greater than 1.67
4000	EN Threshold RampDown	V	PASS	N/A		N/A	11.10055298	PASS	CpK greater than 1.67
4000.1	** EN Threshold RampUp	V	PASS	N/A		N/A	2.549264157	PASS	CpK greater than 1.67
4000.2	* EN Threshold Hysteresis	V	PASS	N/A		N/A	19.32681762	PASS	CpK greater than 1.67
4100	PG_pin_Low_Threshold RampDown	V	PASS	N/A	1	N/A	3.428064103	PASS	CpK greater than 1.67
4100.1	PG_pin_Low_Threshold RampUp	V	PASS	N/A		N/A	3.442908462	PASS	CpK greater than 1.67
4100.2	PG_pin_Low_Threshold Hysteresis	V	PASS	N/A		N/A	268.1775114	PASS	CpK greater than 1.67
4100.3	* PG Lower Threshold Offset from VFB	%	PASS	N/A		N/A	2.332501349	PASS	CpK greater than 1.67
4100.4	* PG Low Hysteresis	%	PASS	N/A	1	N/A	9.646439684	PASS	CpK greater than 1.67
4200	PG_pin_High_Threshold RampDown	V	PASS	N/A		N/A	2.806142253	PASS	CpK greater than 1.67
.200		•	17.55			11/1	2.000172233	17.55	opin Disorter trian 1107

4200.1	PG pin High Threshold RampUp	V	PASS	N/A	N/A	4.108298698	DACC	Coll greater than 1.07
					· · · ·		PASS	CpK greater than 1.67
4200.2	PG_pin_High_Threshold Hysteresis	V	PASS	N/A	N/A	257.2832772	PASS	CpK greater than 1.67
4200.3	* PG Upper Threshold Offset from VFB		PASS	N/A	N/A	1.907095529	PASS	CpK greater than 1.67
4200.4	* PG Hi Hysteresis	%	PASS	N/A	N/A	10.1545083	PASS	CpK greater than 1.67
4300	* SYNC_Threshold RampDown	V	PASS	N/A	N/A	11.28976289	PASS	CpK greater than 1.67
4300.1	* SYNC_Threshold RampUp	V	PASS	N/A	N/A	11.27156965	PASS	CpK greater than 1.67
4300.2	SYN_Threshold Hysteresis	V	PASS	N/A	N/A	23.31960236	PASS	CpK greater than 1.67
4500	Feedback Reference Voltage [Vin=12V, ILoad=0.5A]	V	PASS	N/A	N/A	3.285069202	PASS	CpK greater than 1.67
4500.1	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS	N/A	N/A	3.132739569	PASS	CpK greater than 1.67
4500.2	Reference Voltage [Vin=40V, ILoad=0.5A]	V	PASS	N/A	N/A	3.304933869	PASS	CpK greater than 1.67
4500.3	** Feedback Voltage Line Regulation	%/V	PASS	N/A	N/A	10.31230563	PASS	CpK greater than 1.67
4500.4	Reference Voltage [Vin=12V, ILoad=0.1A]	V	PASS	N/A	N/A	29.16927587	PASS	CpK greater than 1.67
4500.5	Reference Voltage [Vin=12V, ILoad=2.5A]	V	PASS	N/A	N/A	28.62600015	PASS	CpK greater than 1.67
4500.6	Feedback Voltage Load Regulation	%	PASS	N/A	N/A	262.7869239	PASS	CpK greater than 1.67
4500.7	Delta Vref (Vin=6V - Vin=4V)	mV	PASS	N/A	N/A	29.16493058	PASS	CpK greater than 1.67
4500.8	Delta Vref (Vin=6V - Vin=40V)	mV	PASS	N/A	N/A	19.59240424	PASS	CpK greater than 1.67
4800	* BIAS_pin_Current_Consumption	mA	PASS	N/A	N/A	15.41581825	PASS	CpK greater than 1.67
4900	Regulating_with_SS	V	PASS	N/A	N/A	8.458842253	PASS	CpK greater than 1.67
5000	** SS_Pin_Current	uA	PASS	N/A	N/A	2.636851248	PASS	CpK greater than 1.67
5100	** Datasheet_Osc_High [Rt=18.2K]	KHz	PASS	N/A	N/A	2.157286533	PASS	CpK greater than 1.67
5100.1	I_Vin_Rt18K	mA	PASS	N/A	N/A	101.0342795	PASS	CpK greater than 1.67
5100.2	Vout_Rt18K	V	PASS	N/A	N/A	38.05426931	PASS	CpK greater than 1.67
5100.3	Efficiency_Rt18K		PASS	N/A	N/A	8.001781918	PASS	CpK greater than 1.67
5200	** Datasheet_Osc_Low [Rt=60.4K]	KHz	PASS	N/A	N/A	3.624747738	PASS	CpK greater than 1.67
5200.1	I Vin Rt60K	mA	PASS	N/A	N/A	103.5460088	PASS	CpK greater than 1.67
5200.2	Vout Rt60K	V	PASS	N/A	N/A	38.67394974	PASS	CpK greater than 1.67
5200.3	Efficiency Rt60K		PASS	N/A	N/A	5.976539841	PASS	CpK greater than 1.67
5300	SYNC_Frequency [Sync=1MHz]	KHz	PASS	N/A	N/A	290.635567	PASS	CpK greater than 1.67
5300.1	SYNC Frequency [Sync=3.1MHz]	KHz	PASS	N/A	N/A	80.54913383	PASS	CpK greater than 1.67
5300.2	SYNC Frequency [Sync=200KHz]	KHz	PASS	N/A	N/A	55.26093843	PASS	CpK greater than 1.67
5400	** Datasheet_Osc_Low [Rt=221K]	KHz	PASS	N/A	N/A	4.546057895	PASS	CpK greater than 1.67
5400.1	Osc_Low [Rt=3.8uA]	KHz	PASS	N/A	N/A	19.25866447	PASS	CpK greater than 1.67
5400.2	Osc Med Hi [Rt=24uA]	KHz	PASS	N/A	N/A	5.37758534	PASS	CpK greater than 1.67
5400.3	Rt Voltage Hi [Rt=18.2K//60.4K=13.986K]	V	PASS	N/A	N/A	24.02353904	PASS	CpK greater than 1.67
5400.4	Rt Voltage Hi + 13.986K*0.024uA [Calc]	V	PASS	N/A	N/A	17.78303373	PASS	CpK greater than 1.67
5500	Frequency Foldback	KHz	PASS	N/A	N/A	4.282053375	PASS	CpK greater than 1.67
5500.1	Rt Voltage Lo [Rt=18.2K//60.4K=13.986K]	V	PASS	N/A	N/A	44.74463591	PASS	CpK greater than 1.67
5500.2	Rt Voltage Lo + 13.986K*0.024uA [Calc]	V	PASS	N/A	N/A	18.57363072	PASS	CpK greater than 1.67
5600	SS Threshold to stop charging	V	PASS	N/A	N/A	22.72354817	PASS	CpK greater than 1.67
5700	PG_High_SW_Pulldown_Current	mA	PASS	N/A	N/A	19.42082605	PASS	CpK greater than 1.67
5800	SW voltage [BST=10V]	V	PASS	N/A	N/A	86.90482628	PASS	CpK greater than 1.67
5800.1	BST voltage part switching	V	PASS	N/A	N/A	18.68577464	PASS	CpK greater than 1.67
5800.2	BST_OK_Threshold [BST-SW]	V	PASS	N/A N/A	N/A N/A	6.835096501	PASS	CpK greater than 1.67
9000	VCC cont Damage Check	V V	PASS	N/A N/A	N/A N/A	21.21344736	PASS	CpK greater than 1.67
9000.1	VIN cont Danage Check	V	PASS	N/A N/A	N/A N/A	20.7436691	PASS	CpK greater than 1.67
9000.1	SW cont Damag Check	V	PASS	· · · · · · · · · · · · · · · · · · ·	N/A N/A	8.226235749	PASS	CpK greater than 1.67
9000.2		v	PASS	N/A	IN/A	0.220235749	PASS	Chv Riegtei (1191) 1.07

LT861440C_	T861440C_QA Analysis Data View Report									
Test Number	Test Name	Units	Overall Correlation Result	Mean Diff	Mean diff <5% limit range	Stdv Ratio	Sigma Spread Criteria <1.3	Cpk Value	Cpk >1.67	Annotations
20.0	VCC_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.1	VIN_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.2	SW_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.3	EN_cont @-100uA	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.4	SYNC_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.5	SS_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.6	RT_cont [18.2K to APU]	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.7	PG_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.8	FB_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.9	BST_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
20.1	BIAS_cont	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
940	Vref_Trim_Check [Open Loop]	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
950	*** Post-BURN Vout [0.970V] Vin=6V	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
950.1	Post-BURN Vout [0.970V] Vin=40V	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
950.2	Post-BURN OSCF	KHz	PASS		N/A		N/A		PASS	CpK greater than 1.67
950.6	Vref_Trim_Check [Open Loop] [From T940.0]	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
950.7	Delta_of_Vref [T940.0-T950.0]	mV	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000	** Ivin_Sleep	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.1	* Ien_Sleep	nA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.2	Irt_Sleep	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.3	lss_Sleep	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.7	* lpg_Sleep	nA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.8	lbias_Sleep	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.9	lintvcc_Sleep [INTVCC=4.0V]	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.1	lintvcc_Sleep [INTVCC=3.3V]	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.11	lintvcc_Sleep [INTVCC=2.8V]	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.12	Ibst_Sleep	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1000.13	** Ivin_Sleep_with_SYNC	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1100	Ivin_Sleep_ABS_MAX	uA	PASS PASS		N/A N/A		N/A		PASS	CpK greater than 1.67
1100.1 1100.4	len_Sleep_ABS_MAX	uA uA	PASS				N/A		PASS PASS	CpK greater than 1.67
1200	Ipg_Sleep_ABS_MAX ** Ivin Shutdown	uA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200	Irt Shutdown	uA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67 CpK greater than 1.67
1200.1	Iss Shutdown	mA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200.2	* Isync Shutdown	nA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200.3	* Ifb Shutdown	nA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200.9	Ipg Shutdown	mA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200.1	Ibias_Shutdown	uA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200.11	* SS Pulldown Resistance	Ohm	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1200.12	** PG_Pulldown_Resistance	Ohm	PASS		N/A		N/A		PASS	CpK greater than 1.67
1300	Ivin Shutdown ABS MAX	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1300.1	Iss Shutdown ABS MAX	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1300.4	Ipg_Shutdown_ABS_MAX	mA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1300.5	Ibias_Shutdown_ABS_MAX	uA	PASS		N/A N/A		N/A N/A		PASS	CpK greater than 1.67
1300.6	Irt_Shutdown_ABS_MAX	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1400	* Top FET Isw	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1500	* Bot FET Leakage	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1500.1	Bot FET AbsMax Leakage [lbst]	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1600	** Regulation Light Load Ivin@1mA	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1600.3	** Regulation_Light_Load_lvin@100uA	uA	PASS		N/A		N/A		PASS	CpK greater than 1.67
1700	Regulation_Mode_Short_Circuit	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
2000	Freq with RT=48uA	KHz	PASS		N/A		N/A		PASS	CpK greater than 1.67
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2000.1	RegulationMode Sync=0V	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
2000.2	** SW_Min_Ontime Sync=0V	nS	PASS		N/A		N/A		PASS	CpK greater than 1.67
2100	Freq with RT=48uA	KHz	PASS		N/A		N/A		PASS	CpK greater than 1.67
2100.1	RegulationMode Sync=3.3V	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
2100.2	** SW_Min_Ontime Sync=3.3V	nS	PASS		N/A		N/A		PASS	CpK greater than 1.67
2200	* TopRDSon [Vin-Vsw]	Ohm	PASS		N/A		N/A		PASS	CpK greater than 1.67
2200.1	V_sw_out@1A before ramp [Debug only]	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
2200.2	Slop_Comp_Ilim	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
2300	V_sw_out@1.5A before ramp [Debug only]	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
2300.1	** Top_I_Lim	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
2300.2	Burst_I_Lim	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
2300.3	SYNC_I_Lim	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
2400	Vout [0.6A load] @Vin=6V	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
2400.1	** Minimum Input VOltage [Min_Vin_UVLO]	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
2400.2	Vout [0.6A load] Drop	V	PASS	0.776479067	PASS	1.043165299	PASS	1.126200848	N/A	tightened limits
2400.3	SW_Min_Ontime Sync=0V [Calc]	nS	PASS		N/A		N/A		PASS	CpK greater than 1.67
2400.4	SW Min Ontime Sync=3V [Calc]	nS	PASS		N/A		N/A		PASS	CpK greater than 1.67
2500	* BotRDSon [Pgnd-Vsw]	Ohm	PASS	1.81551557	PASS	1.149410262	PASS	0.12166657	N/A	tightened limits
2500.1	BST pin Voltage thru 1K	V	PASS	1.915489558	PASS	1.10906009	PASS	1.099938341	N/A	tightened limits
2500.2	Zero cross current	mA	PASS	2.142040069	PASS	0.956707273	PASS	1.154196161	N/A	tightened limits
2600	** DA Current Limit [Bot Lim]	mA	PASS		N/A	0.000707270	N/A	1110 1100101	PASS	CpK greater than 1.67
2700	SW_Frequency	KHz	PASS		N/A		N/A		PASS	CpK greater than 1.67
2700.1	* Min Off Time	nS	PASS		N/A		N/A		PASS	CpK greater than 1.67
2700.1	W_duty_cycle	//////////////////////////////////////	PASS		N/A		N/A		PASS	CpK greater than 1.67
2700.2	Dropout Voltage	V	PASS		N/A N/A		N/A		PASS	CpK greater than 1.67
2700.3	* Vintvcc OmA no bias	V	PASS		N/A N/A		N/A			CpK greater than 1.67
		V	PASS		N/A N/A				PASS	
2800.1	Vintvcc_20mA_no_bias	V					N/A		PASS	CpK greater than 1.67
2900	* Vintvcc_0mA_with_bias	-	PASS		N/A		N/A		PASS	CpK greater than 1.67
2900.1	Vintvcc_20mA_with_bias	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3000	Intvcc_llim_no_bias [Vccint=0V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3000.1	Intvcc_llim_no_bias [Vccint=3V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3100	Intvcc_llim_ABSMAX_no_bias [Vccint=0V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3100.1	Intvcc_Ilim_ABSMAX_no_bias [Vccint=3V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3200	Intvcc_Ilim_with_bias [Vccint=0V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3200.1	Intvcc_llim_with_bias [Vccint=3V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3300	Intvcc_Ilim_ABSMAX_with_bias [Vccint=0V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3300.1	Intvcc_Ilim_ABSMAX_with_bias [Vccint=3V]	mA	PASS		N/A		N/A		PASS	CpK greater than 1.67
3400	Intvcc_BIAS_Threshold RampDown	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3400.1	Intvcc_BIAS_Threshold RampUp	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3400.2	Intvcc_BIAS_Threshold Hysteresis	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3500	Intvcc_Vin_Threshold RampDown	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3500.1	Intvcc_Vin_Threshold RampUp	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3500.2	Intvcc_Vin_Threshold Hysteresis	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3600	* Intvcc_UVLO_Threshold RampDown	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3600.1	Intvcc_UVLO_Threshold RampUp	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
3600.2	Intvcc_UVLO_Threshold Hysteresis	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4000	EN_Threshold RampDown	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4000.1	** EN_Threshold RampUp	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4000.2	* EN Threshold Hysteresis	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4100	PG pin Low Threshold RampDown	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4100.1	PG pin Low Threshold RampUp	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4100.2	PG pin Low Threshold Hysteresis	v	PASS		N/A		N/A		PASS	CpK greater than 1.67
4100.2	* PG Lower Threshold Offset from VFB	%	PASS		N/A	1	N/A	1	PASS	CpK greater than 1.67
4100.3	* PG Low Hysteresis	%	PASS		N/A		N/A	1	PASS	CpK greater than 1.67
4200	PG_pin_High_Threshold RampDown	V	PASS		N/A N/A	+ +	N/A		PASS	CpK greater than 1.67
4200.1	PG pin High Threshold RampUp	V	PASS		N/A		N/A		PASS	CpK greater than 1.67
4200.1	PG_pin_High_Threshold Hysteresis	V	PASS			+ +			PASS	CpK greater than 1.67
4200.2		v	r Abb		N/A		N/A		FA33	כאיג פו כמנכו נוומוז ב.טי

4200.2	* DC Linney Threshold Offect from V/FD	0/	PASS	N/A	NI / A	DACC	Call grapher than 1 C7
4200.3	* PG Upper Threshold Offset from VFB	%		N/A	N/A	PASS	CpK greater than 1.67
4200.4	* PG Hi Hysteresis	%	PASS	N/A	N/A	PASS	CpK greater than 1.67
4300	* SYNC_Threshold RampDown	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4300.1	* SYNC_Threshold RampUp	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4300.2	SYN_Threshold Hysteresis	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500	Feedback Reference Voltage [Vin=12V, ILoad=0.5A]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.1	Reference Voltage [Vin=4V, ILoad=0.5A]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.2	Reference Voltage [Vin=40V, ILoad=0.5A]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.3	** Feedback Voltage Line Regulation	%/V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.4	Reference Voltage [Vin=12V, ILoad=0.1A]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.5	Reference Voltage [Vin=12V, ILoad=2.5A]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.6	Feedback Voltage Load Regulation	%	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.7	Delta Vref (Vin=6V - Vin=4V)	mV	PASS	N/A	N/A	PASS	CpK greater than 1.67
4500.8	Delta Vref (Vin=6V - Vin=40V)	mV	PASS	N/A	N/A	PASS	CpK greater than 1.67
4800	* BIAS_pin_Current_Consumption	mA	PASS	N/A	N/A	PASS	CpK greater than 1.67
4900	Regulating_with_SS	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5000	** SS_Pin_Current	uA	PASS	N/A	N/A	PASS	CpK greater than 1.67
5100	** Datasheet_Osc_High [Rt=18.2K]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5100.1	I_Vin_Rt18K	mA	PASS	N/A	N/A	PASS	CpK greater than 1.67
5100.2	Vout_Rt18K	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5100.3	Efficiency_Rt18K		PASS	N/A	N/A	PASS	CpK greater than 1.67
5200	** Datasheet_Osc_Low [Rt=60.4K]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5200.1	I_Vin_Rt60K	mA	PASS	N/A	N/A	PASS	CpK greater than 1.67
5200.2	Vout_Rt60K	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5200.3	Efficiency_Rt60K		PASS	N/A	N/A	PASS	CpK greater than 1.67
5300	SYNC_Frequency [Sync=1MHz]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5300.1	SYNC_Frequency [Sync=3.1MHz]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5300.2	SYNC Frequency [Sync=200KHz]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5400	** Datasheet Osc Low [Rt=221K]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5400.1	Osc Low [Rt=3.8uA]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5400.2	Osc Med Hi [Rt=24uA]	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5400.3	Rt Voltage Hi [Rt=18.2K//60.4K=13.986K]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5400.4	Rt_Voltage_Hi + 13.986K*0.024uA [Calc]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5500	Frequency Foldback	KHz	PASS	N/A	N/A	PASS	CpK greater than 1.67
5500.1	Rt Voltage Lo [Rt=18.2K//60.4K=13.986K]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5500.2	Rt_Voltage_Lo + 13.986K*0.024uA [Calc]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5600	SS Threshold to stop charging	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5700	PG_High_SW_Pulldown_Current	mA	PASS	N/A	N/A	PASS	CpK greater than 1.67
5800	SW voltage [BST=10V]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5800.1	BST voltage part switching	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
5800.2	BST_OK_Threshold [BST-SW]	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
9000	VCC cont Damage Check	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
9000.1	VIN cont Danage Check	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
9000.2	SW cont Damag Check	V	PASS	N/A	N/A	PASS	CpK greater than 1.67
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GAGE MSA STUDY		
GAGE TYPE/NAME:	TESTER ETS115/ETS	<u>1</u> 16
CHARACTERISTIC MEA	ASURED: TEST PA	RAMETER
PART MEASURED (FOR	R BIAS/LINEARITY):	LTC8614
PART MEASURED (FOR	R GR&R STUDY):	LTC8614
MSA DATE:	Yr 2020	
GAGE OWNER:	UTAC Tha	iland
RESULT / COMMENT:	PASS	
SIGNATURE:		

Test #	Test Name	Result GR&R	Result
95000000	*** Post-BURN Vout [0.970V] Vin=6V	4.980195	PASS
10000000	** Ivin_Sleep	1.8229312	PASS
10000001	* len_Sleep	1.431906	PASS
10000007	* lpg_Sleep	4.201244	PASS
10000013	** Ivin_Sleep_with_SYNC	1.797112	PASS
120000000	** lvin_Shutdown	1.730056	PASS
12000003	* Isync_Shutdown	0.755767	PASS
12000008	* Ifb_Shutdown	1.683225	PASS
120000011	* SS_Pulldown_Resistance	6.226861	PASS
120000012	** PG_Pulldown_Resistance	4.376655	PASS
14000000	* Top_FET_Isw	3.848640	PASS
150000000	* Bot_FET_Leakage	3.664196	PASS
16000000	** Regulation_Light_Load_lvin@1mA	6.668205	PASS
16000003	** Regulation_Light_Load_lvin@100uA	8.152861	PASS
20000002	** SW_Min_Ontime Sync=0V	5.488522	PASS
21000003	** SW_Min_Ontime Sync=3.3V	5.729720	PASS
220000000	* TopRDSon [Vin-Vsw]	8.741214	PASS
230000001	** Top_I_Lim	7.553578	PASS
240000001	** Minimum Input VOltage [Min_Vin_UVLO]	1.993776	PASS
25000000	* BotRDSon [Pgnd-Vsw]	8.415162	PASS
26000000	** DA_Current_Limit [Bot_I_Lim]	9.251783	PASS
27000001	* Min_Off_Time	2.935384	PASS
28000000	* Vintvcc_0mA_no_bias	5.744688	PASS
290000000	* Vintvcc_0mA_with_bias	1.527685	PASS
36000000	* Intvcc_UVLO_Threshold RampDown	4.478650	PASS
40000001	** EN_Threshold RampUp	5.129394	PASS
40000002	* EN_Threshold Hysteresis	5.687005	PASS
41000003	* PG Lower Threshold Offset from VFB	8.699416	PASS
41000004	* PG Low Hysteresis	5.222225	PASS
42000003	* PG Upper Threshold Offset from VFB	5.741519	PASS
420000004	* PG Hi Hysteresis	4.649508	PASS
43000000	* SYNC_Threshold RampDown	2.429610	PASS
43000001	* SYNC_Threshold RampUp	1.023551	PASS
45000003	** Feedback Voltage Line Regulation	5.561093	PASS
480000000	* BIAS_pin_Current_Consumption	1.082953	PASS
50000000	** SS_Pin_Current	1.123075	PASS
510000000	** Datasheet_Osc_High [Rt=18.2K]	1.629319	PASS
520000000	** Datasheet_Osc_Low [Rt=60.4K]	1.924119	PASS
54000000	** Datasheet_Osc_Low [Rt=221K]	0.831821	PASS